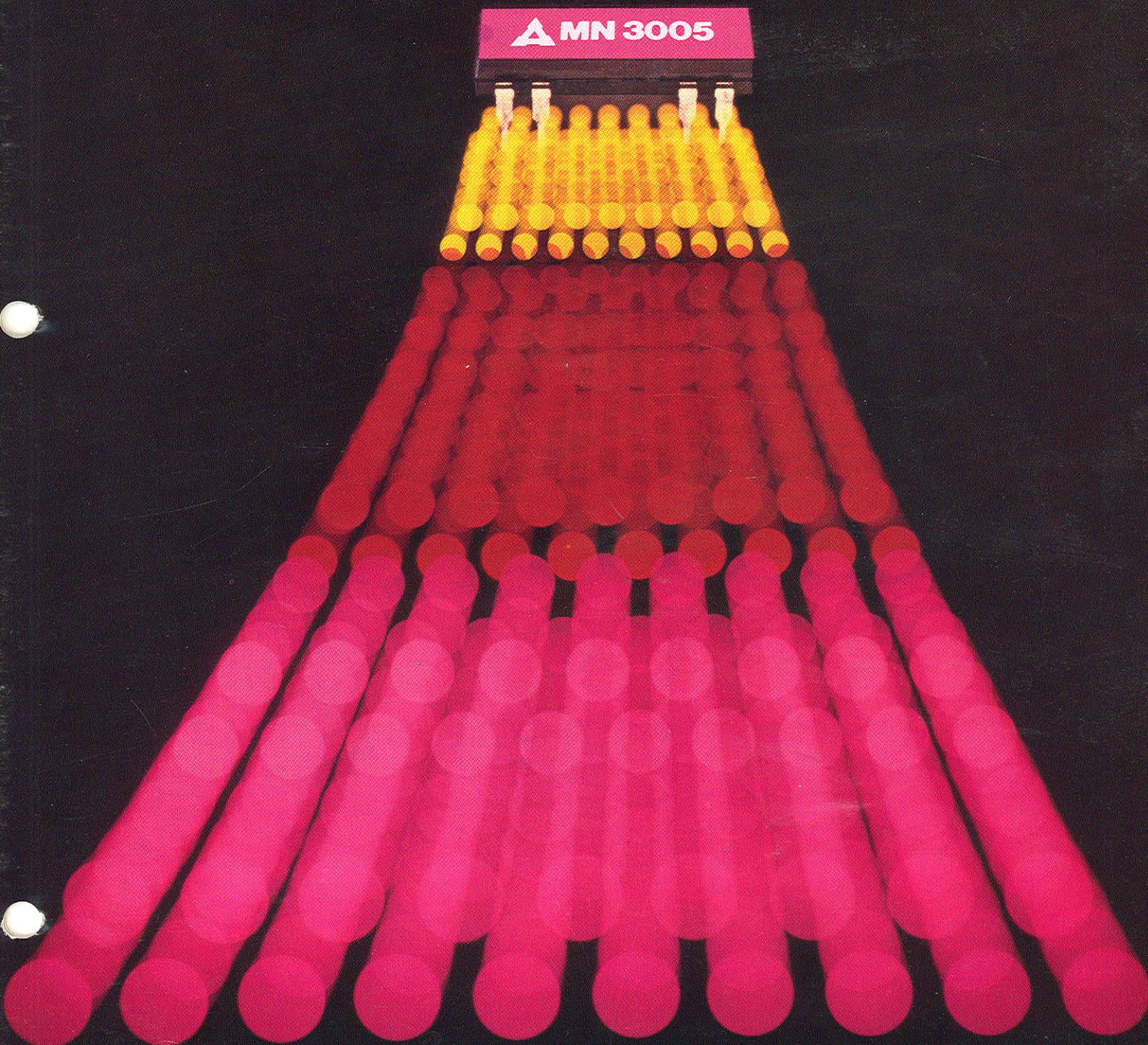


Panasonic®

BBD Bucket Brigade Devices



BBD SERIES

Bucket Brigade Devices

Panasonic holds a leadership position in the area of BBD's for audio signal delays. Since the first BBD (type MN3001) was developed, various new types have been introduced to meet the expanding market requirement. Now the product range has expanded to twelve types, ranging from 64-stage to the longest 4096-stage BBD.

This edition of our "BBD Series" catalog contains detailed information on the twelve types of products in this series already in production. If further information is required for your BBD application, please feel free to contact our sales offices, representatives or distributors. We always wish to offer you better service to satisfy your quality and performance requirements.

CONTENTS

INTRODUCTION	1
TYPICAL APPLICATIONS.....	1
CLOCK FREQUENCY and SIGNAL	
DELAY TIME	1
SELECTION GUIDE by STAGES	1
BBD QUICK REFERENCE TABLE.....	2
SPECIFICATIONS and CHARACTERISTICS	
MN3001, MN3002.....	3
MN3003.....	9
MN3004	13
MN3005	18
MN3006	23
MM3007	28
MN3008	32
MN3009	36
MN3010	40
MN3011	44
MN3012	50
MN3101	56

INTRODUCTION

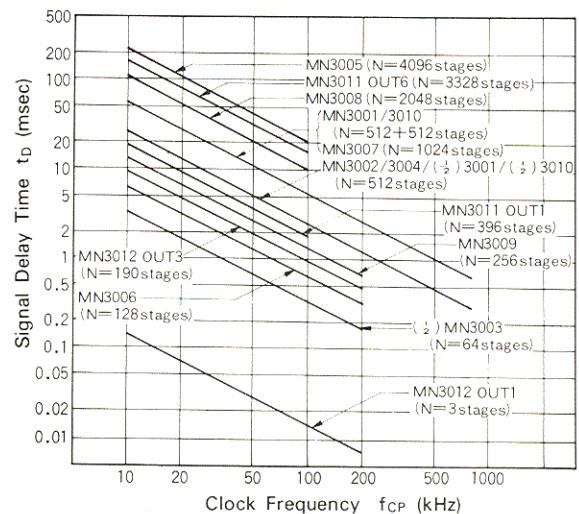
The Bucket Brigade Device is a P-channel silicon gate MOS LSI consists of a number of bucket brigade stages fabricated on a single chip. Each stage consists of a capacitor that stores the electrical charge and a tetrode transistor for switching purposes. Electrical charges corresponding to analog signals are transferred from one stage to another by a two phase clock drive. Thus the electric signals flow unidirectionally from the input to the output with a time delay which can be controlled by the clock frequency.

The Bucket Brigade Device has found a variety of applications in audio equipment as a useful variable or fixed delay line. The device can obtain chorus and tremolo effects in electronic musical instruments as well as reverberation effects in audio equipment, which completely replaces conventional mechanical systems. The device can also be used to restore the correct pitch of tape recordings played back faster or slower than the correct speed to accommodate the listener's rate of comprehension. In addition to these applications, the BBD facilitates the production of equipment incorporating new concepts with high marketability.

TYPICAL APPLICATIONS

- Variable speech control of playback and voice control of tape recorders.
- Reverberation effect of echo microphones and stereo equipment.
- Tremolo, vibrato and/or chorus effects in electronic musical instruments.
- Variable or fixed delay of analog signals.

CLOCK FREQUENCY AND SIGNAL DELAY TIME



SELECTION GUIDE by STAGES

Stage		Type No.	Noise	Application
64	Dual Type	MN3003	Low Noise Types	Reverberation Effect (Signal Delay under 10 msec.) Vibrato Effect *1 Chorus Effect *2 Phasor/Flanger Effect *3
128		MN3006		
3, 5, 190	Triple Type	MN3012		
256	Single Type	MN3009		
		MN3004		
512		MN3002	Standard Types	Echo Effect (Signal Delay over 10 msec.) Double Voicing Effect *4
	Dual Type	MN3001		
		MN3010		
1024	Single Type	MN3007	Low Noise Types	Reverberation Effect (Signal Delay over 100 msec.)
2048		MN3008		
4096		MN3005		
3328	Multi-Type	MN3011		Reverberation Effect (Six different delay outputs)

*1 Vibrato Effect: Several Hz modulation effect of the clock frequency for BBD.

*2 Chorus Effect: Mixing effect of the original signal and the attenuated delayed signal.

*3 Phasor/Flanger Effect: Effect of either the sum or difference of the original signal and the delayed signal.

*4 Double Voicing Effect: Mixing effect of the original signal and the delayed signal.

BBD QUICK REFERENCE TABLE

Item	Symbol	MN3001	MN3002	MN3003	MN3004	MN3005	MN3006	MN3007	MN3008	MN3009	MN3010	MN3011	MN3012	Unit
Number of BBD	N	Dual-512	512	Dual-64	512	4096	128	1024	2048	256	Dual-512	3328 6-Tap	190,3,5 3-Tap	Stage
Circuit Construction	Clock Generator		External	Built-in				External						Built-in
Output Terminal								Pair						6 Different Taps
Drain Supply Voltage	V _{DD}	-15	-9	-15	-15	-15	-15	-15	-15	-15	-15	-15	-15	v
Gate Supply Voltage	V _{GG}	-14	-8	-14	-14	-14	-14	-14	-14	-14	-14	-14	-	v
Operating Conditions	Back-Gate Bias Voltage	V _{BB}	+5											v
Clock Voltage "H" Level	V _{CPh}	0	0	0	0 ~ -1	0 ~ -1	0 ~ -1	0 ~ -1	0 ~ -1	0 ~ -1	0 ~ -1	0 ~ -1	0 ~ -0.4	v
Clock Voltage "L" Level	V _{CPL}	-15	-9	-15	-15	-15	-15	-15	-15	-15	-15	-15	-15	v
Input DC Bias	V _{Bias}	-3.3 ~ -4.9	-2.5 ~ -6	-5 ~ -10	-5 ~ -10	-5 ~ -10	-5 ~ -10	-5 ~ -10	-5 ~ -10	-5 ~ -10	-	-	-3 ~ -12	v
Input Signal Frequency	f _i		12	10	12	12	12	12	12	12	10	12	kHz (max.)	
Input Signal Swing	V _i	1.8	0.8	1.8	1.2	1.8	1.5	1.5	1.5	1.7	1.8	1.0	1.2	V _{rms} (max.)
Insertion Loss	L _i	8.5	3.5	1.5	0	0	0	0	0	0	0	0	0	dB (typ.)
Electrical Characteristics	Total Harmonic Distortion	THD	0.4	0.5	1	0.2	0.5	0.5	0.3	0.4	0.4	0.4	0.4	% (typ.)
	Noise Voltage	V _{no}	250 (typ.)	140	210	400	200	300	300	150	210	0.4	0.14	μV _{rms} (max.)
	Signal to Noise Ratio	S/N	70	75	85	75	90	80	78	88	85	76		dB (typ.)
	Signal Delay Time	t _D	51.2	25.6	6.4	25.6	204.8	6.4	51.2	1024	12.8	51.2	19.8,33.1 59.7,86.3,139.5 166.4	msec (max.)
Package (Molded Package)			14-Pin DIP		Large 8-Pin DIP	8-Pin DIP	Larger 8-Pin DIP	8-Pin DIP	14-Pin DIP	14-Pin DIP	14-Pin DIP			

MN3001/MN3002

DUAL 512-STAGE BBD (MN3001), 512-STAGE BBD (3002)

General Description

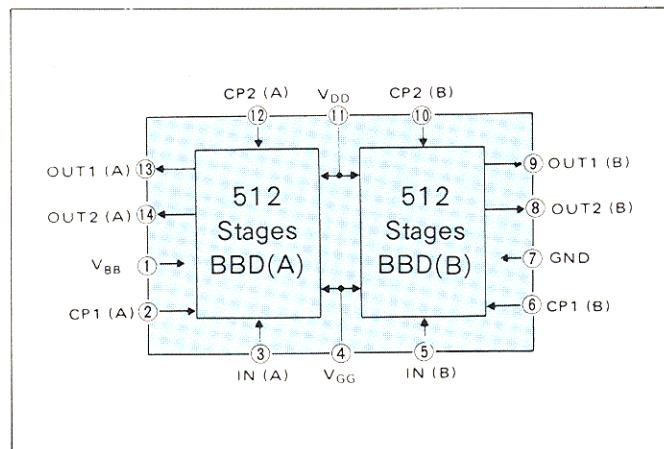
The MN3001 is a dual 512-stage BBD which contains two identical BBD's on a single chip with independent input, output and clock terminals as well as common power supply terminals. Each 512-stage BBD provides a signal delay of up to 25.6msec. The two identical BBD's integrated on the same chip offer uniform Characteristics and space saving advantage when they are used in parallel or series connection.

The MN3002 is a single 512-stage BBD that provides a signal delay of up to 25.6msec.

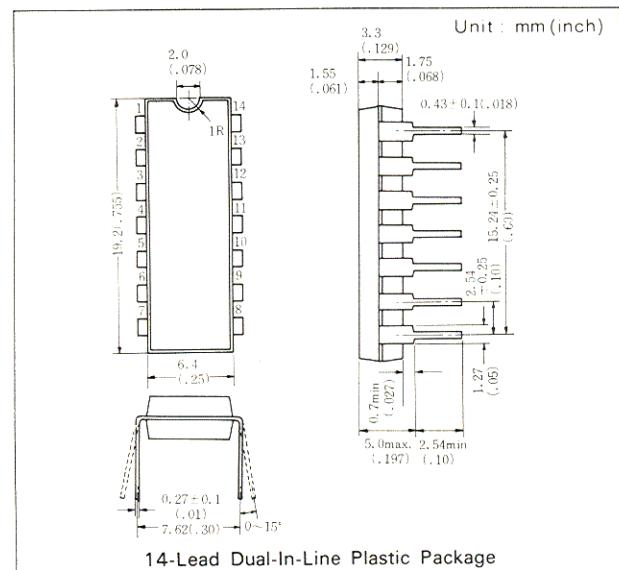
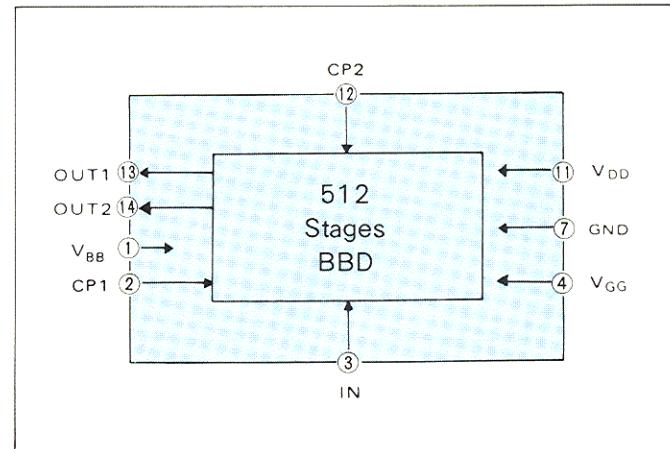
Features:

- Variable delay line in audio frequency range:
0.32~25.6msec. (512-stage)
0.64~51.2msec. (512×2-stage)
- Clock component cancellation capability.
- Wide dynamic range: S/N 70dB typ.
- Wide frequency response: $f_i \leq 0.3 \times f_{CP}$
- Low distortion: THD=0.4% typ.
- Wide clock frequency range: 10~800kHz
- Low noise: $V_{NO} = 0.25\text{mVrms}$ typ.
- Small DC level shift under wide clock frequency change: 40mV typ. ($f_{CP}=10\text{~}300\text{kHz}$)
- P-channel silicon gate, tetrode MOS transistors configuration.
- 14-lead dual-in-line plastic package.

Block Diagram (MN3001)



Block Diagram (MN3002)



Applications:

- Tremolo, vibrato and/or chorus effects in electronic musical instruments.
- Reverberation effect of stereo equipment.
- Variable or fixed delay of analog signals.

BBD SERIES MN3001,MN3002

Absolute Maximum Ratings (Ta=25°C)

Item	Symbol	Rating	Unit
Terminal Voltage	V _{DD} , V _{GG} , V _{CP} , V _I	-20~+0.3	V
Back-gate Bias Voltage	V _{BB}	-0.3~+10	V
Power Dissipation	P _D	50	mW
Operating Temperature	T _{opr}	-20~+60	°C
Storage Temperature	T _{stg}	-55~+125	°C

Operating Conditions (Ta=25°C)

Item	Symbol	Condition	Typical Value	Unit
Drain Supply Voltage	V _{DD}		-15	V
Gate Supply Voltage	V _{GG}		-14	V
Back-gate Bias Voltage	V _{BB}	V _{CPH} =0~-1V V _{BB} =+4~+6V	+5 *1	V
Clock Voltage "H" Level	V _{CPH}		0 *1	V
Clock Voltage "L" Level	V _{CPL}		-15	V
Clock Frequency	f _{CP}		40	kHz
Clock Pulse Width *3	t _{cpw}		0.5 T max. *2	
Clock Rise Time *3	t _{cpri}		0.05T max.	
Clock Fall Time *3	t _{cprf}		0.05T max.	
Clock Input Capacitance	C _{CP}		250	pF
Input DC Bias Voltage	V _{Bias}		-3.3~-4.9	V

Electrical Characteristics (Ta=25°C, V_{DD}=V_{CPL}=-15V, V_{GG}=-14V, V_{BB}=+5V, R_L=100kΩ)

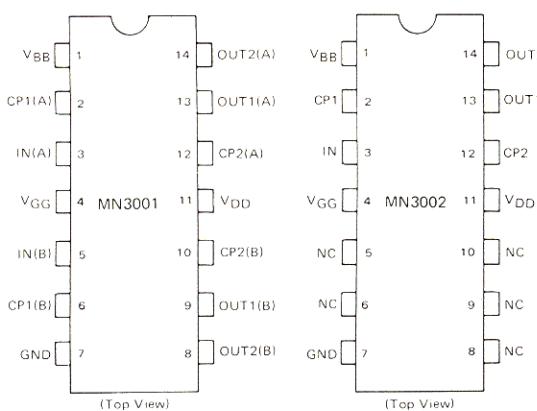
Item	Symbol	Condition	Min.	Typ.	Max.	Unit
Signal Delay Time	t _D		0.32		25.6	μsec
Input Signal Frequency	f _i	f _{CP} =40kHz, V _i =2Vrms, 3dB down (0 dB at f _i =1kHz)	0		0.3f _{CP}	kHz
Input Signal Swing	V _i	f _{CP} =40kHz, f _i =1kHz, THD ≤ 2.5%			1.8	Vrms
Insertion Loss	L _i	f _{CP} =40kHz, f _i =1kHz, V _i =2Vrms	8.5	11		dB
Total Harmonic Distortion	THD	f _{CP} =40kHz, f _i =1kHz, V _i =0.78Vrms	0.4	2.5		%
Noise Voltage	V _{no}	f _{CP} =80kHz, Weighted by "A" curve		0.25		mVrms
Signal to Noise Ratio	S/N		70			dB

*1 The device can be used at V_{BB}=0V when V_{CPH} is set at -3V.

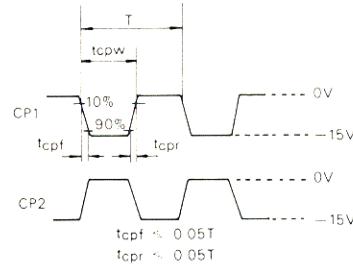
*2 T=1/f_{CP} (Clock Period)

*3 Clock Pulse Waveforms

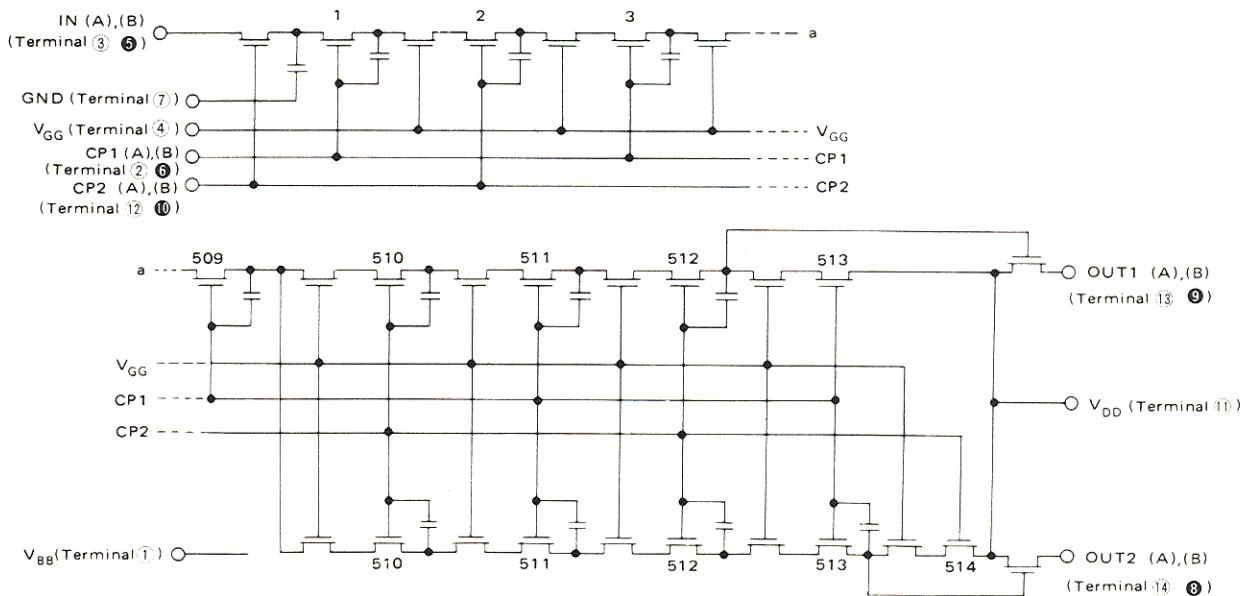
Terminal Assignments



Clock Pulse Waveforms

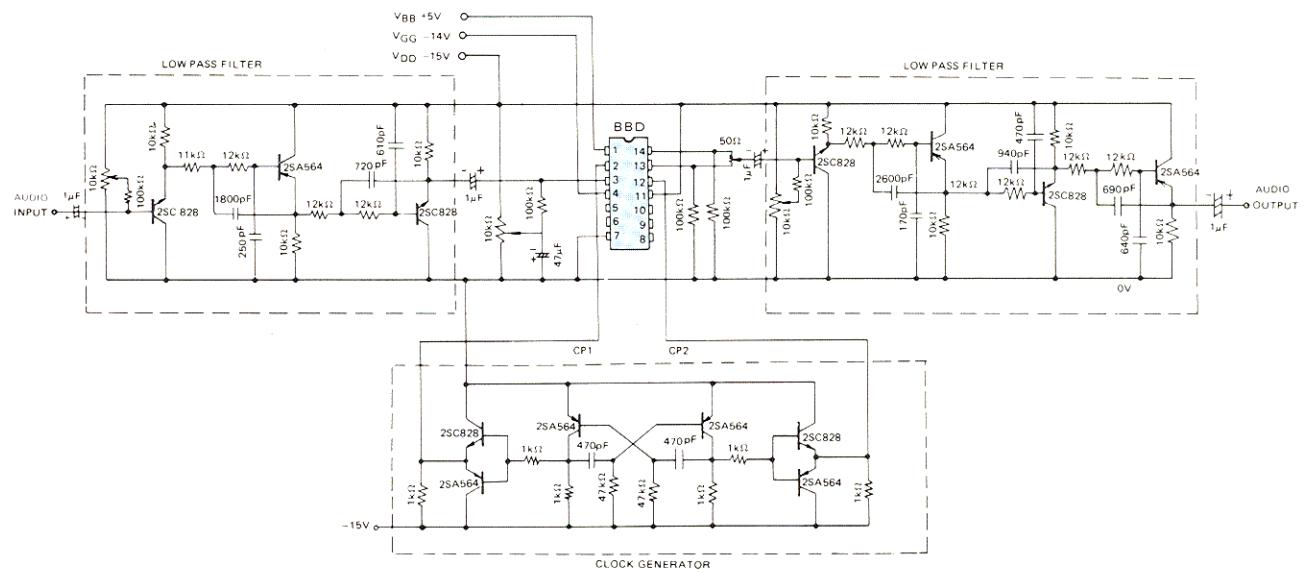


CIRCUIT DIAGRAM



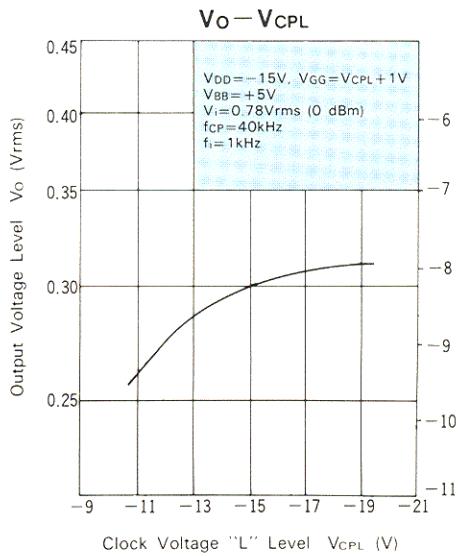
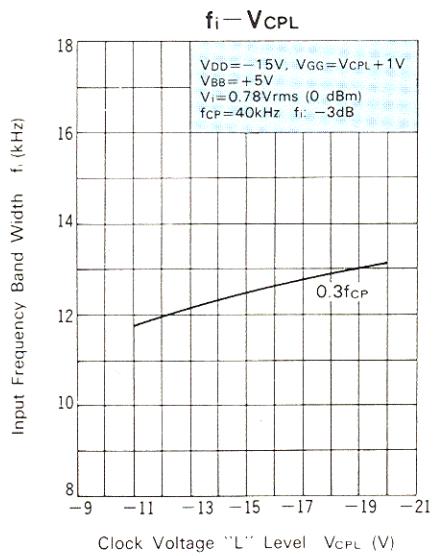
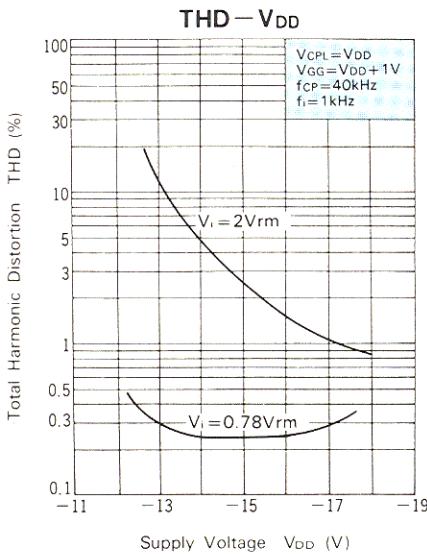
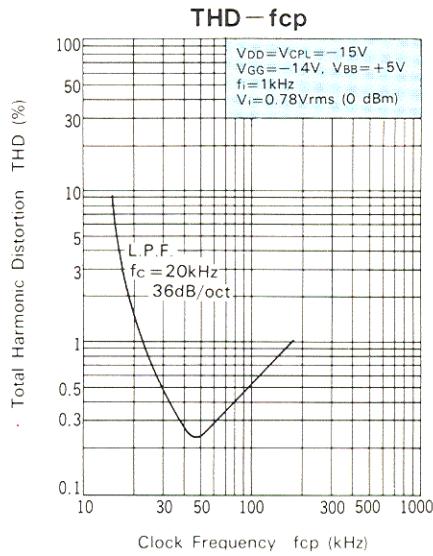
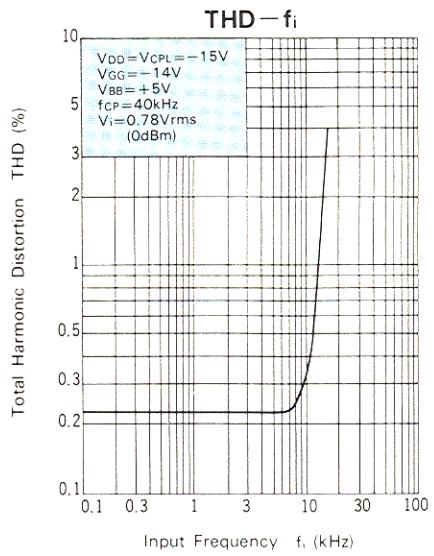
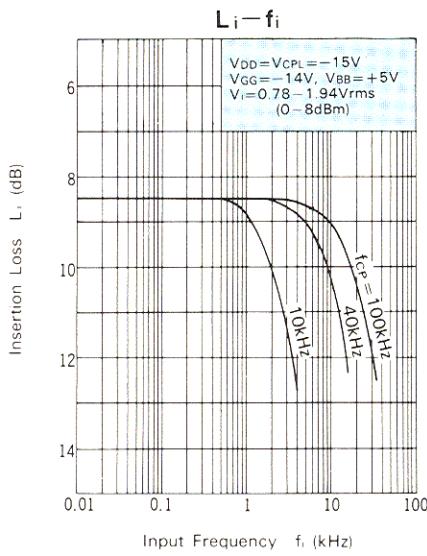
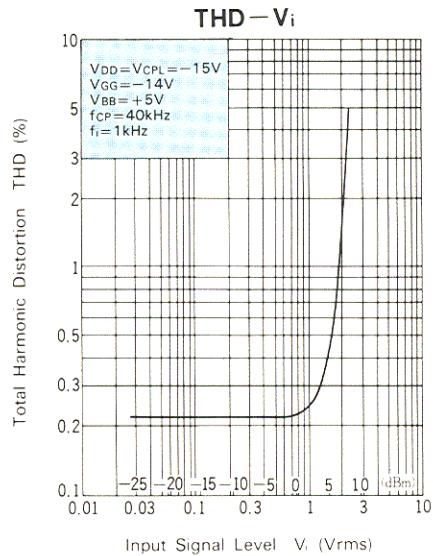
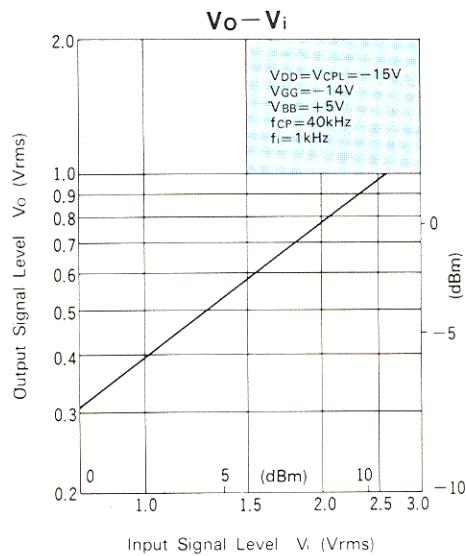
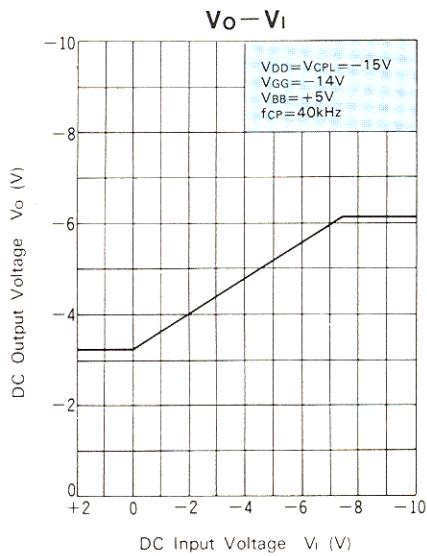
Note: Terminals CP1⑥, CP2⑩, IN⑤, OUT1⑨, OUT2⑧ are usable for the MN3001, and no-connection for the MN3002.

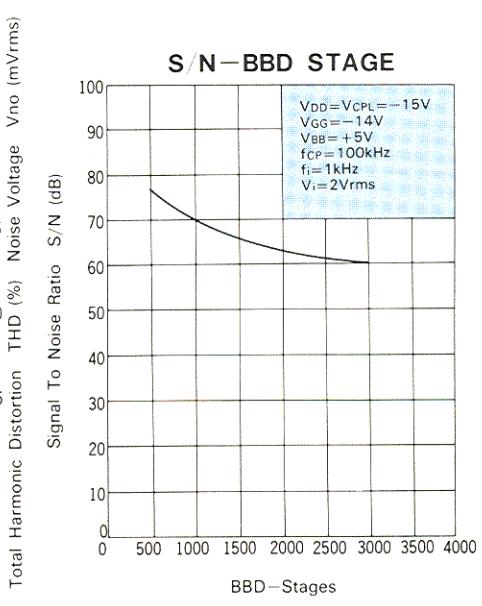
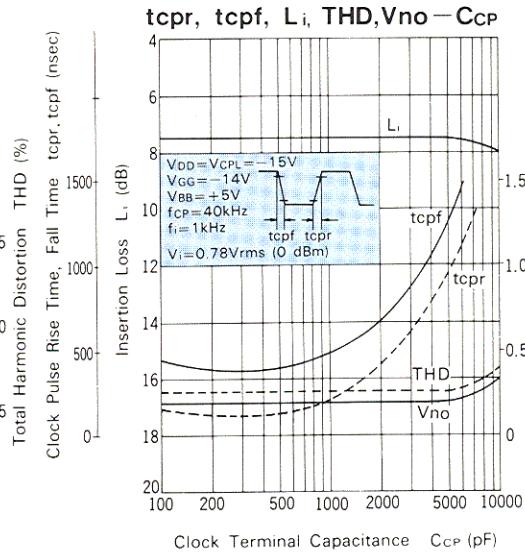
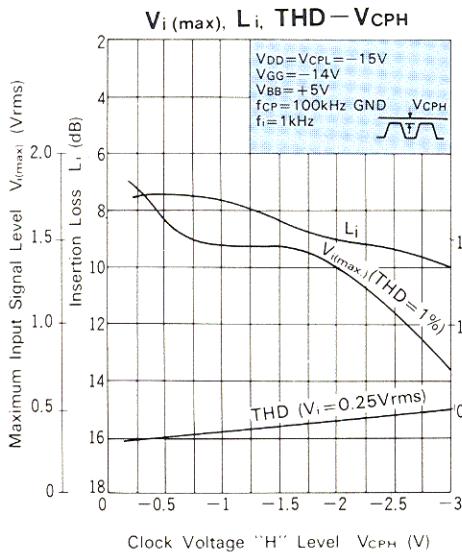
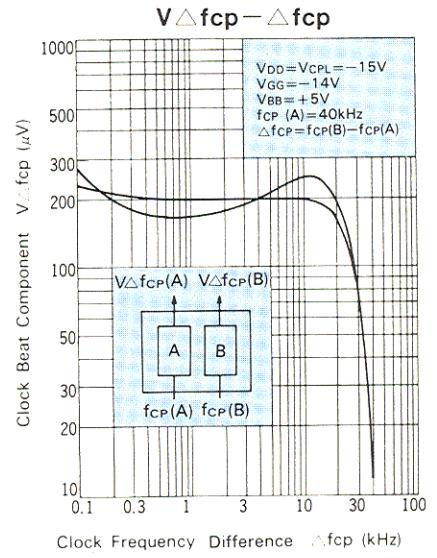
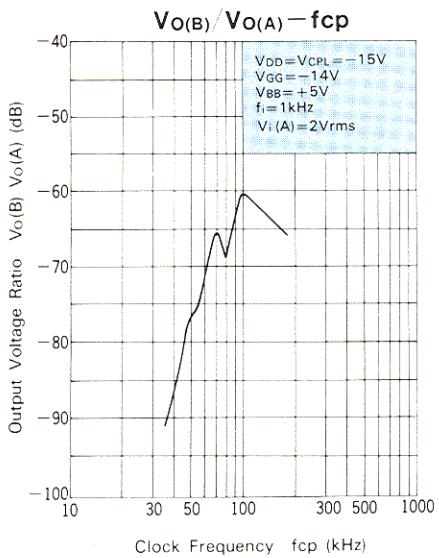
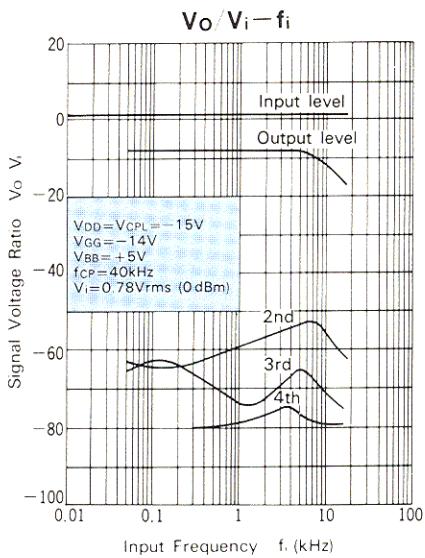
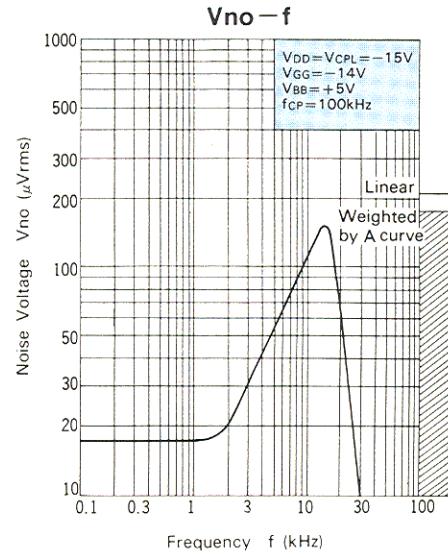
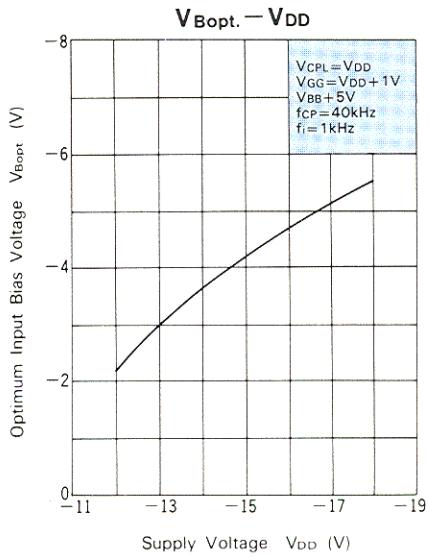
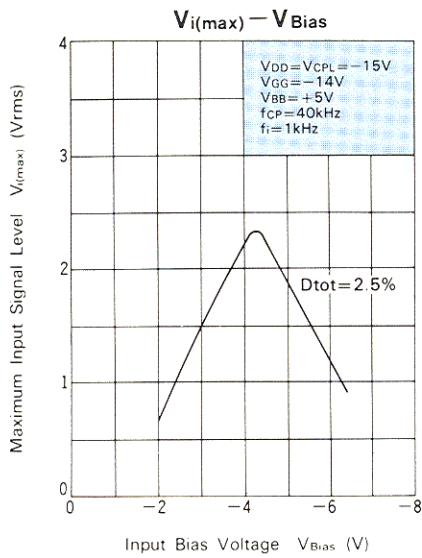
TEST CIRCUIT EXAMPLE



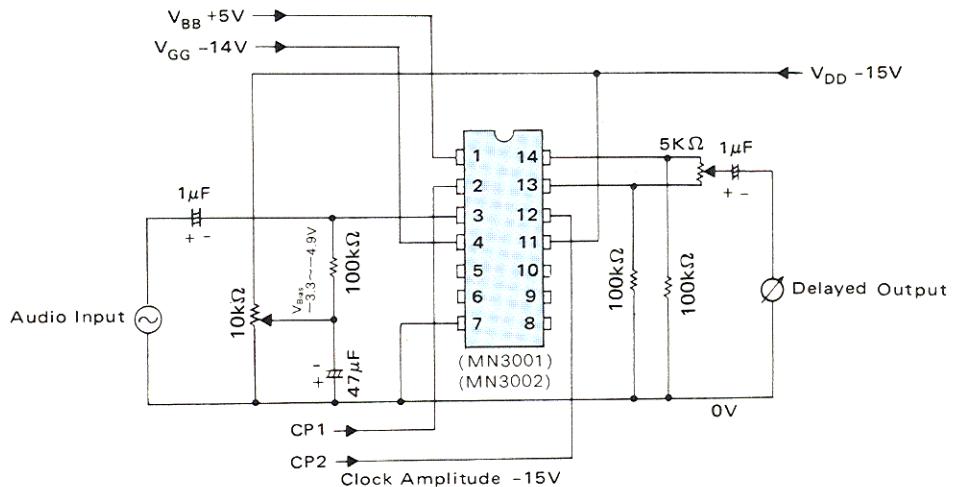
Insertion Loss Measuring Circuit.

Typical Electrical Characteristic Curves



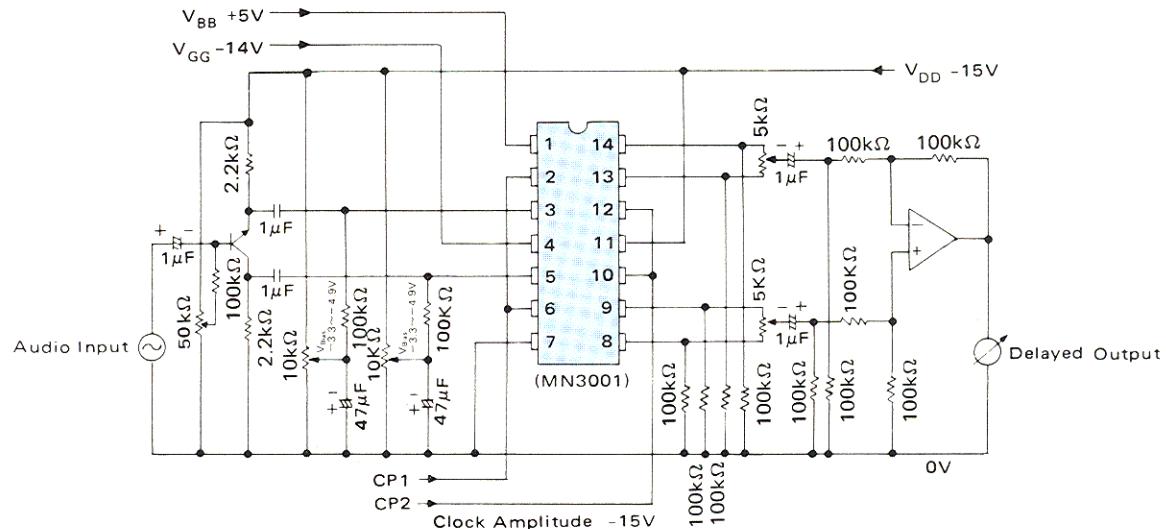


Application Circuit 1



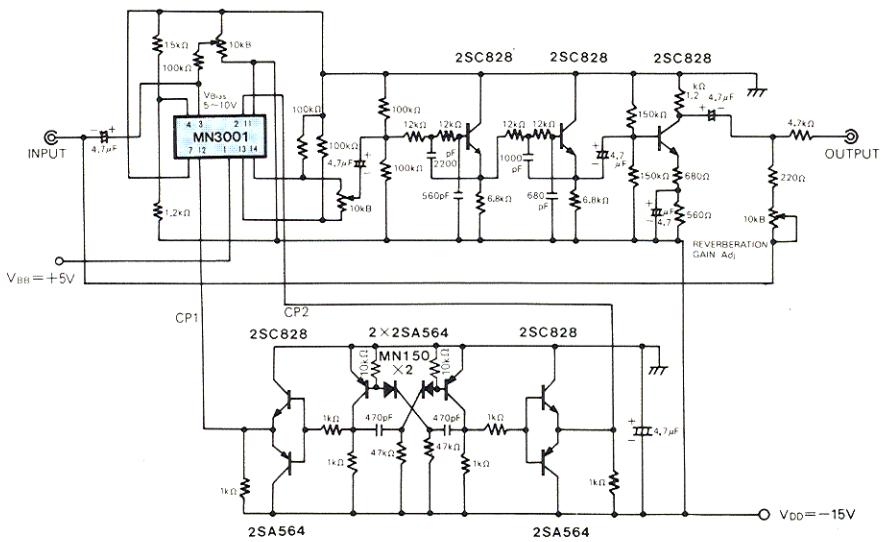
Basic Circuit With Clock Component Cancellation (Single Channel)

Application Circuit 2



Compensation Of DC Level Shift Due To Clock Frequency Change Using Two BBD's
(Dual Channels, Same Clock Phase)

Application Circuit 3



Echo Effect Generation Circuit (Signal Delay Over 10msec.)

MN3003

DUAL-64 STAGE BBD FOR LOW VOLTAGE OPERATION

General Description

The MN3003 is a dual 64-stage BBD for low voltage operation (-9V) incorporating a clock generator on a single chip. The 64-stage provides a signal delay of up to 3.2msec.

The dual type contains two identical BBD's on a single chip with independent input, output and common clock terminals, as well as common power supply terminals.

The two identical BBD's on the same chip offer uniform characteristics and space saving advantage when they are used in parallel or series connection.

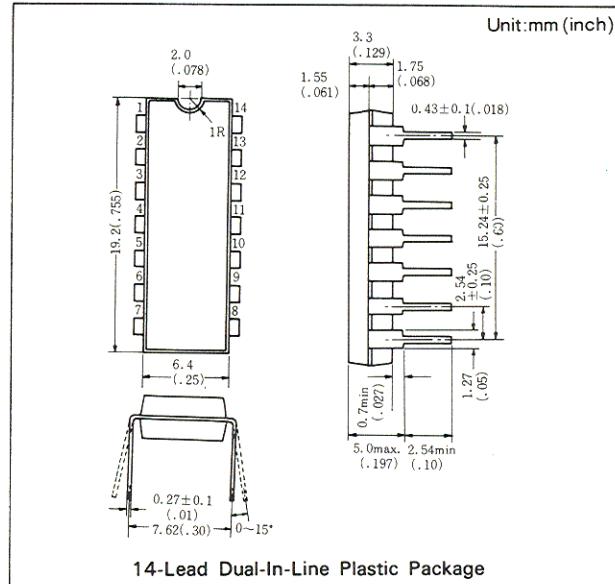
The clock oscillation frequency is controlled by the external resistor and capacitor connected to CG₁, CG₂ and CG₃ terminals.

Features:

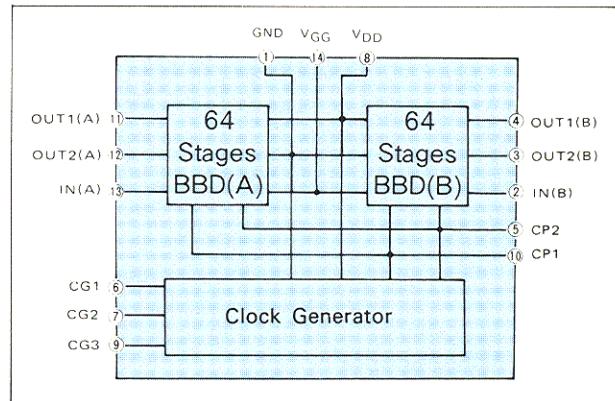
- Variable delay line in audio frequency range:
0.16~3.2msec. (64-stage)
0.32~6.4msec. (64×2-stage)
- Incorporating clock generator circuit.
- Wide frequency response: $f_i \leq 0.3 \times f_{cp}$
- Wide clock frequency range : 10~200kHz
- Wide dynamic range : S/N=75dB typ.
- Low insertion loss : Li=3.5dB typ.
- Low noise : Vno=0.14mVrms max.

Applications:

- Vibrato and/or chorus effects in electronic musical instruments.
- Reverberation effect of electronic musical instruments.
- Variable or fixed delay of analog signals.



Block Diagram



Quick Reference Data

Item	Symbol	Value	Unit
Supply Voltage	V _{DD} , V _{GG}	-9, V _{DD} +1	V
Signal Delay Time	t _D	0.16~6.4	msec
Total Harmonic Distortion	THD	0.5	%
Signal to Noise Ratio	S/N	68min	dB

BBD SERIES MN3003

Absolute Maximum Ratings ($T_a=25^\circ C$)

Item	Symbol	Rating	Unit
Terminal Voltage	V_{DD} , V_{GG} , V_{CP} , V_I	$-15 \sim +0.3$	V
Output Voltage	V_O	$-15 \sim +0.3$	V
Operating Temperature	T_{OPR}	$-20 \sim +60$	$^\circ C$
Storage Temperature	T_{STG}	$-55 \sim +125$	$^\circ C$

Operating Conditions ($T_a=25^\circ C$)

Item	Symbol	Condition	Min.	Typ.	Max.	Unit
Drain Supply Voltage	V_{DD}		-8.5	-9	-9.5	V
Gate Supply Voltage	V_{GG}			$V_{DD}+1$		V
Clock Voltage "H" Level	V_{CPH}		0		-0.4	V
Clock Voltage "L" Level	V_{CPL}			V_{DD}		V
Clock Frequency	f_{CP}		10		200	kHz
Input DC Bias	V_{BIAS}		-2.5		-6	V

($V_{DD}=-9V$, $V_{GG}=-8V$, $R_L=100K\Omega$, $R_2=R_3=22K\Omega$, $R_4=R_5=2.2K\Omega$)

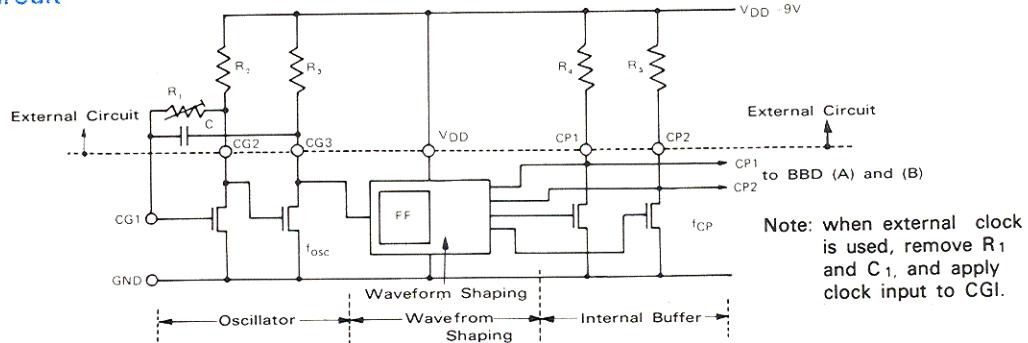
Electrical Characteristics

($C=100pF$, $f_{CP}=1/2f_{osc}$ (adjustable by R_1), $T_a=25^\circ C$)

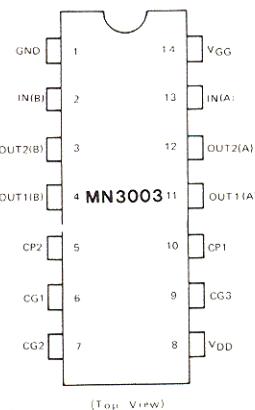
Item	Symbol	Condition	Min.	Typ.	Max.	Unit
Input Signal Frequency	f_i	$f_{CP}=40kHz$, $V_i=0.8Vrms$ 3dB down (0dB at $f_i=1kHz$)			12	kHz
Input Signal Swing	V_i	$f_{CP}=40kHz$, $f_i=1kHz$, THD=2.5%			0.8	Vrms
Insertion Loss	L_i	$f_{CP}=40kHz$, $f_i=1kHz$, $V_i=0.8Vrms$	3.5	7		dB
Total Harmonic Distortion	THD	$f_{CP}=40kHz$, $f_i=1kHz$, $V_i=0.5Vrms$	0.5			%
Noise Voltage	V_{NO}	$f_{CP}=90kHz$, Weighted by "A" curve			0.14	mVrms
Signal to Noise Ratio	S/N		68			dB

Note: Adjust input DC bias to the optimum value between -2.5 and -6 volts.

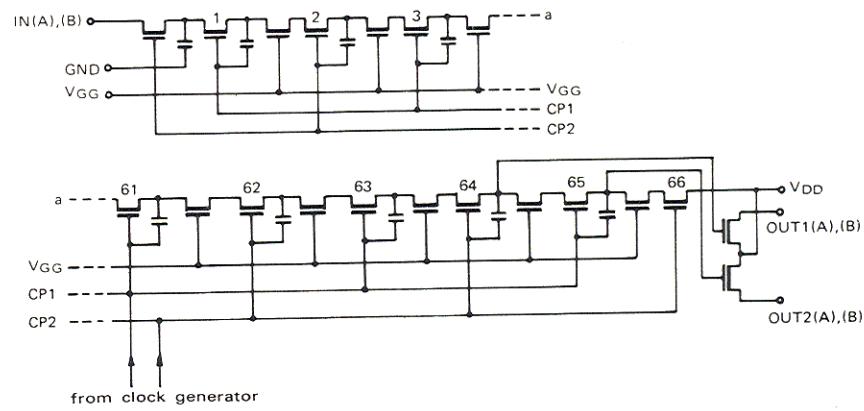
Clock Generator Circuit



Terminal Assignments

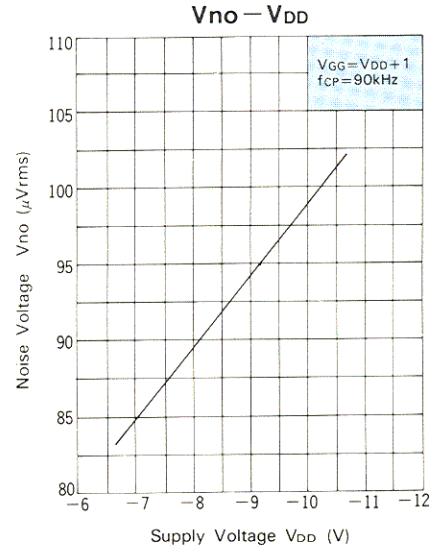
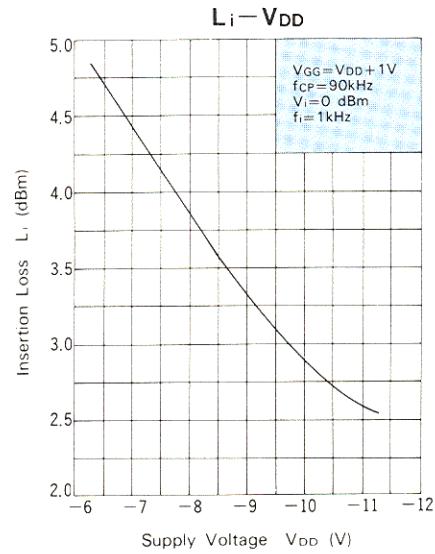
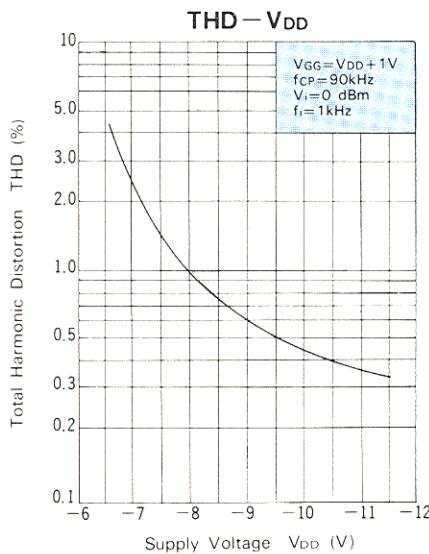
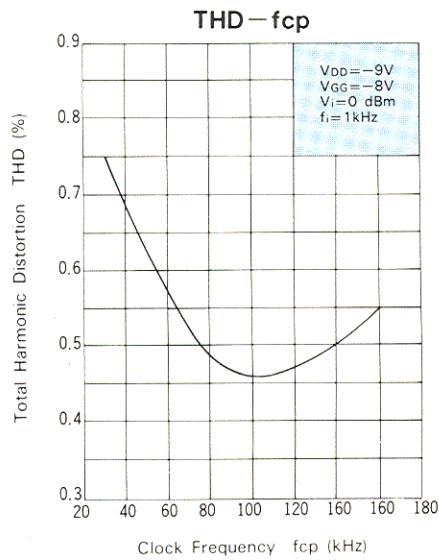
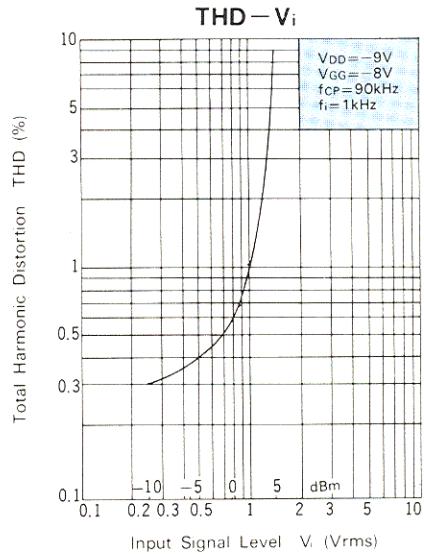
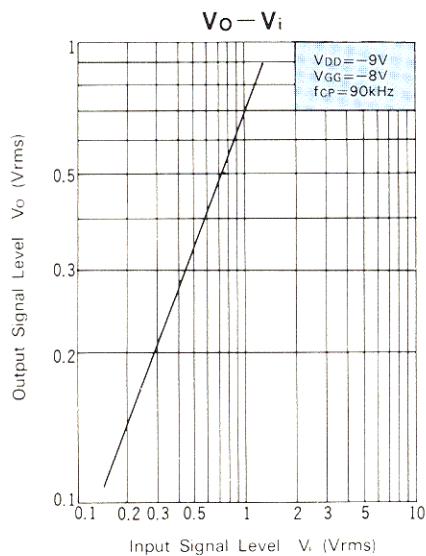
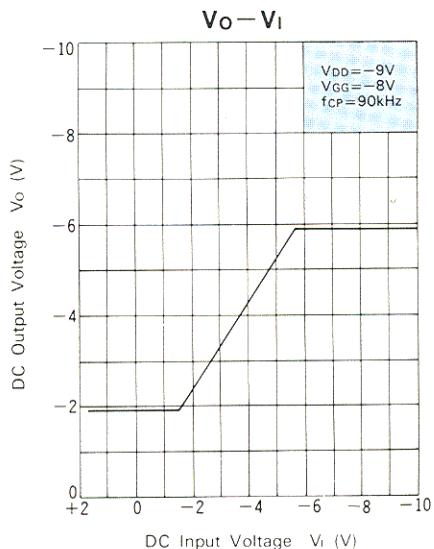
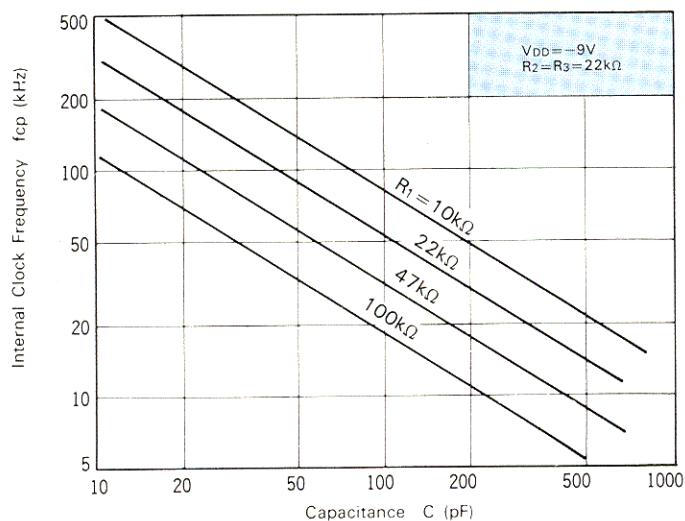


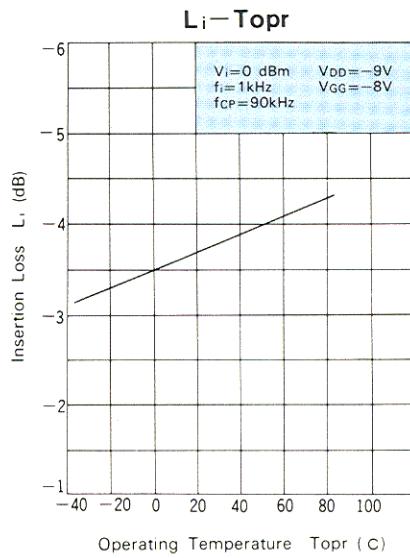
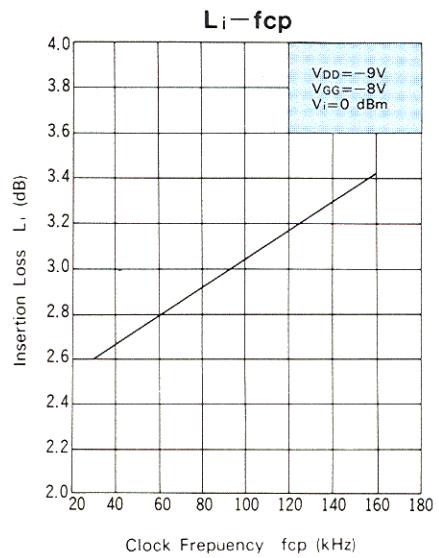
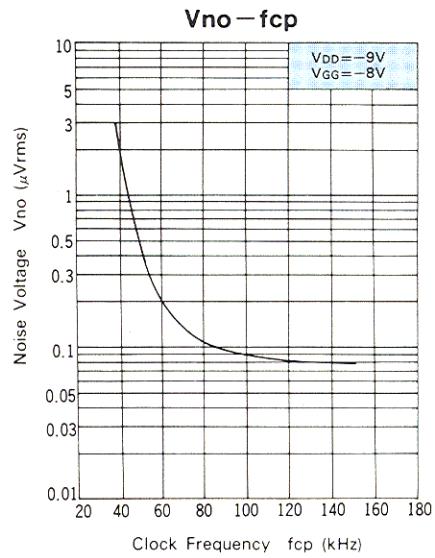
Circuit Diagram



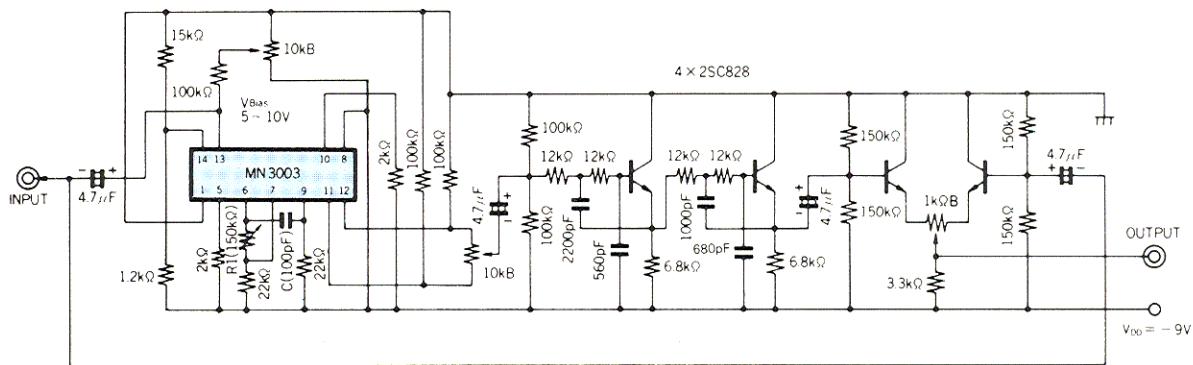
Typical Electrical Characteristic Curves

Clock Frequency Characteristics





Application Circuit



MN3004

512-STAGE LOW NOISE BBD

General Description

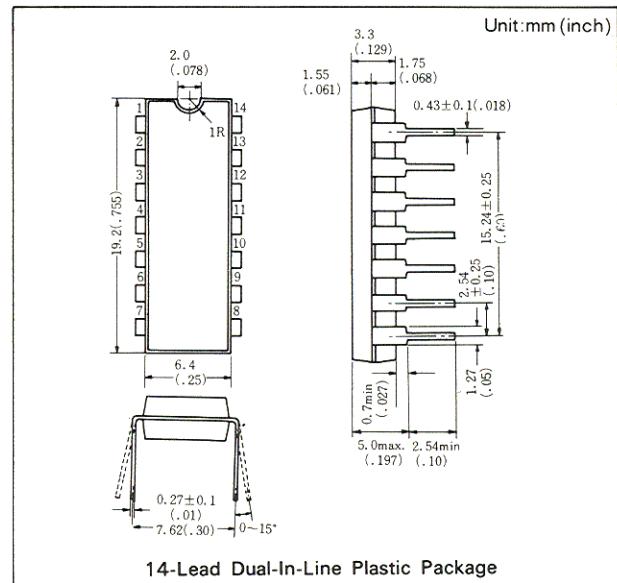
The MN3004 is a 512-stage low noise BBD (Bucket Brigade Device) that provides a signal delay of up to 25.6msec and is suitable for use as variable signal delay lines in audio frequency range.

Features:

- Wide range of variable delay time: 2.56~25.6msec.
- Clock component cancellation capability.
- Low insertion loss: $L_i \approx 1.5$ dB typ.
- Wide dynamic range: $S/N \approx 85$ dB typ.
- Wide frequency response: $f_i \leq 0.3 \times f_{CP}$
- Clock frequency range: 10~100kHz.
- Low noise: $V_{NO} = 0.21\text{mVrms}$ max.
- Total harmonic distortion: THD = 0.4% typ.
- P-channel silicon gate, tetrode MOS transistors configuration.
- 8-lead dual-in-line plastic package.

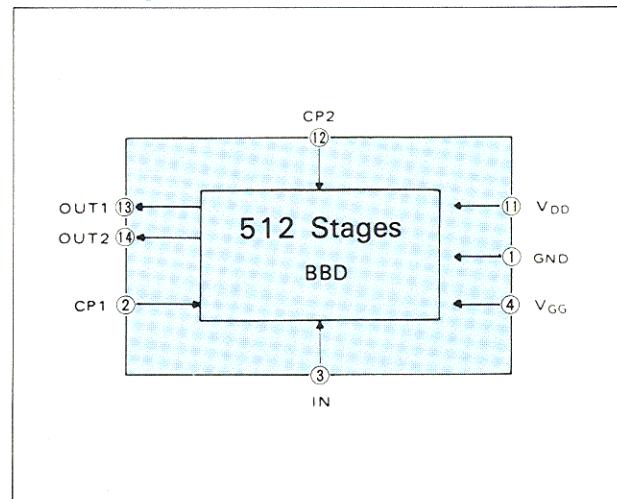
Applications:

- Reverberation effect of echo microphones and stereo equipment.
- Vibrato and/or chorus effects in electronic organs and musical instruments.
- Variable or fixed delay of analog signals.



14-Lead Dual-In-Line Plastic Package

Block Diagram



Quick Reference Data

Item	Symbol	Value	Unit
Supply Voltage	V_{DD}, V_{GG}	$-15, V_{DD} + 1$	V
Signal Delay Time	t_D	2.56~25.6	msec
Total Harmonic Distortion	THD	0.4	%
Signal to Noise Ratio	S/N	85	dB

BBD SERIES MN3004

Absolute Maximum Ratings (Ta=25°C)

Item	Symbol	Ratings	Unit
Terminal Voltage	V _{DD} , V _{GG} , V _{CP} , V _I	-18 ~ +0.3	V
Output Voltage	V _O	-18 ~ +0.3	V
Operating Temperature	T _{opr}	-20 ~ +60	°C
Storage Temperature	T _{stg}	-55 ~ +125	°C

Operating Conditions (Ta=25°C)

Item	Symbol	Condition	Min.	Typ.	Max.	Unit
Drain Supply Voltage	V _{DD}		-14	-15	-16	V
Gate Supply Voltage	V _{GG}			V _{DD} +1		V
Clock Voltage "H" Level	V _{CPH}	0		-1	V	
Clock Voltage "L" Level	V _{CPL}			V _{DD}		V
Clock Input Capacitance	C _{CP}			350	pF	
Clock Frequency	f _{CP}		10	100	kHz	
Clock Pulse Width *2	t _{cpw}				0.5T *1	
Clock Rise Time *2	t _{cpri}				500	nsec
Clock Fall Time *2	t _{cprf}				500	nsec
Input DC Bias	V _{Bias}		-5		-10	V

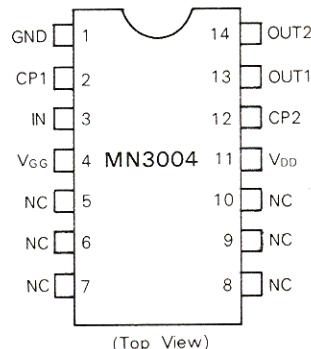
Electrical Characteristics (Ta=25°C, V_{DD}=V_{CPL}=-15V, V_{CPH}=0V, V_{GG}=-14V, R_L=KΩ)

Item	Symbol	Condition	Min.	Typ.	Max.	Unit
Signal Delay Time	t _D		2.56		25.6	msec
Input Signal Frequency	f _i	f _{CP} =40kHz, V _i =1.8VRms, 3dB down (0 dB at f _i =1kHz)			12	kHz
Input Signal Swing	V _i	f _{CP} =40kHz, f _i =1kHz, THD=2.5%			1.8	VRms
Insertion Loss	L _i	f _{CP} =40kHz, f _i =1kHz, V _i =1.8VRms		1.5	4.8	dB
Total Harmonic Distortion	THD	f _{CP} =40kHz, f _i =1kHz, V _i =1VRms		0.4		%
Noise Voltage	V _{no}	f _{CP} =100kHz Weighted by "A" curve			0.21	mVRms
Signal to Noise Ratio	S/N		75	85		dB

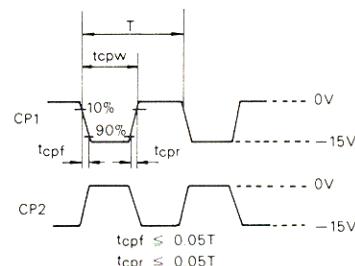
*1 T=1 f_{CP} (Clock Period)

*2 Clock Pulse Waveforms

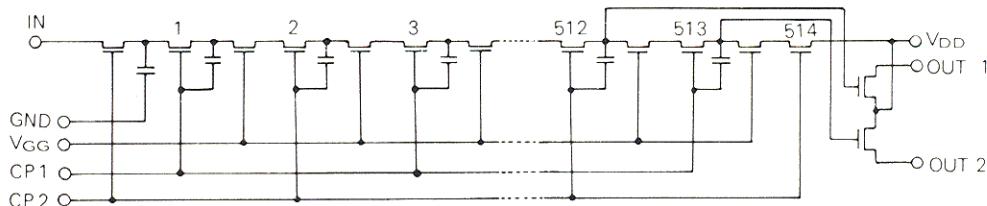
Terminal Assignments



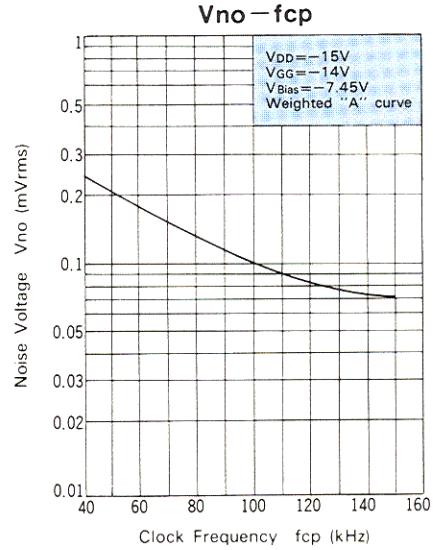
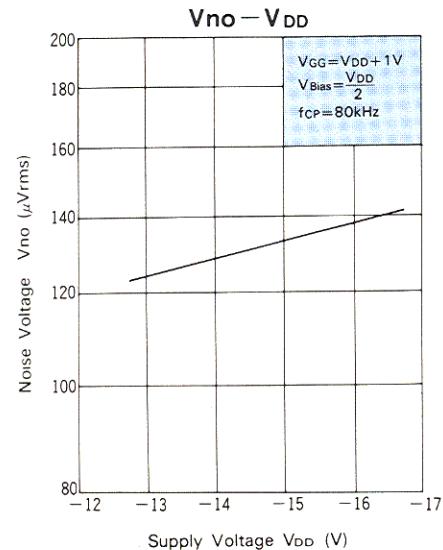
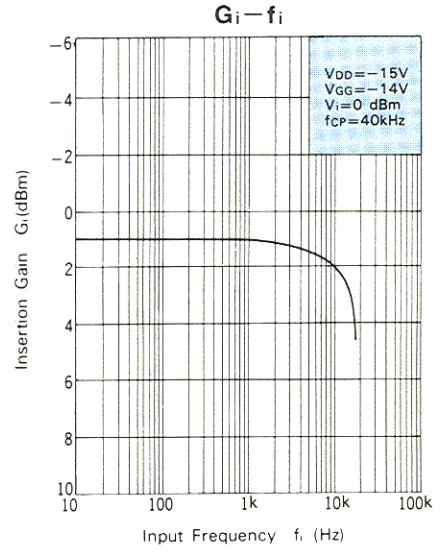
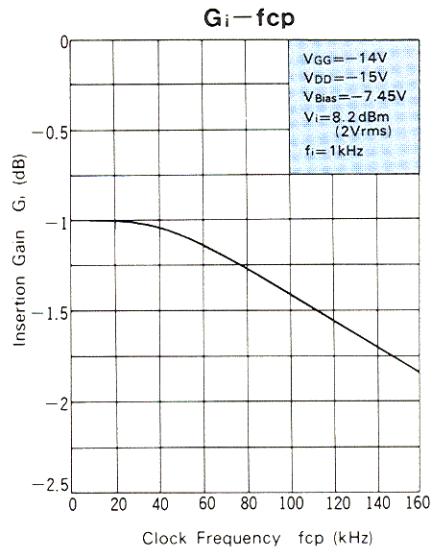
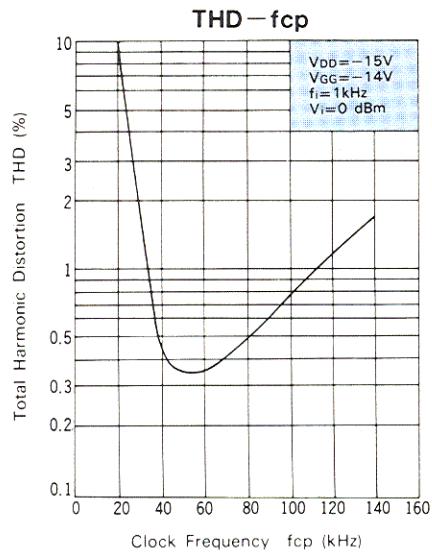
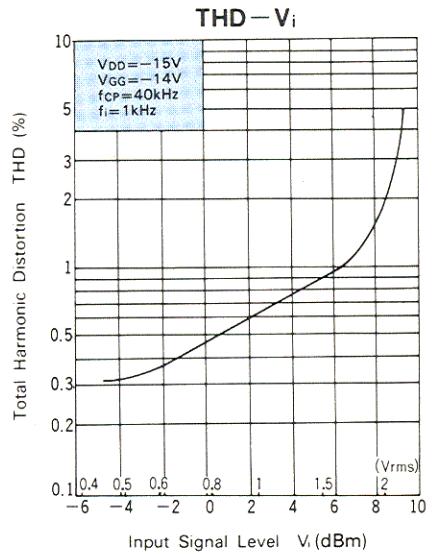
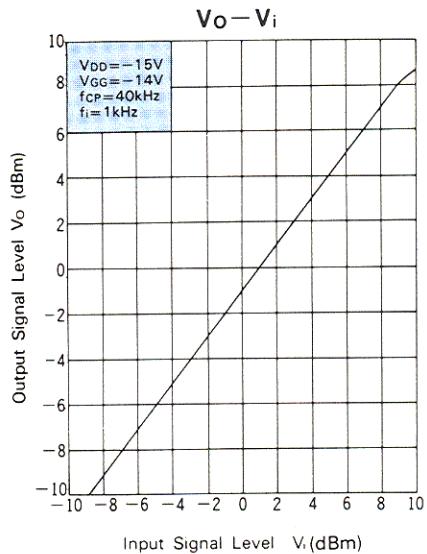
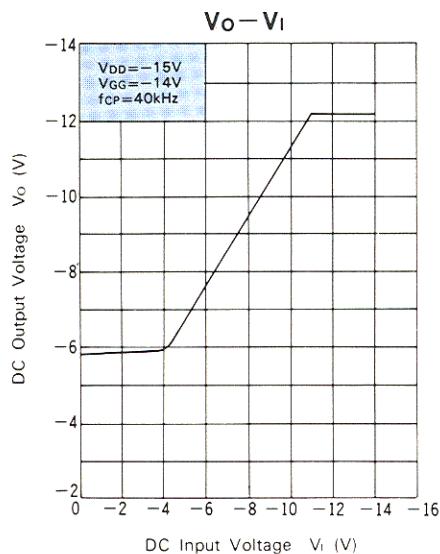
Clock Pulse Waveforms



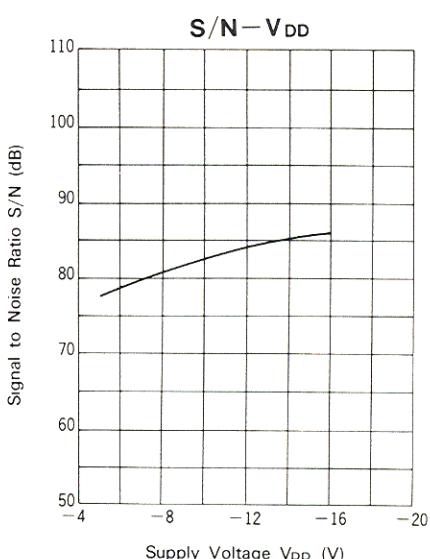
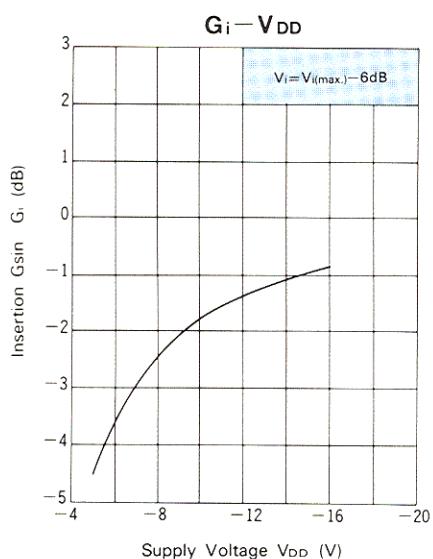
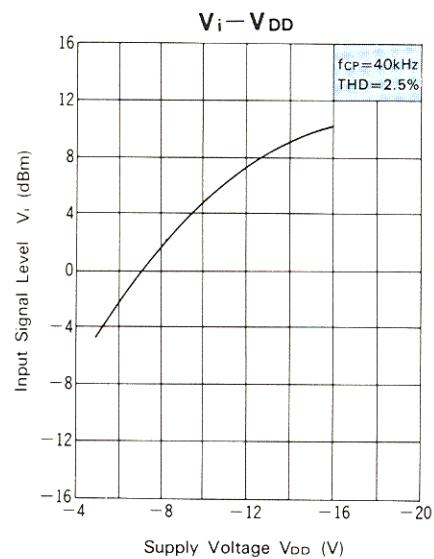
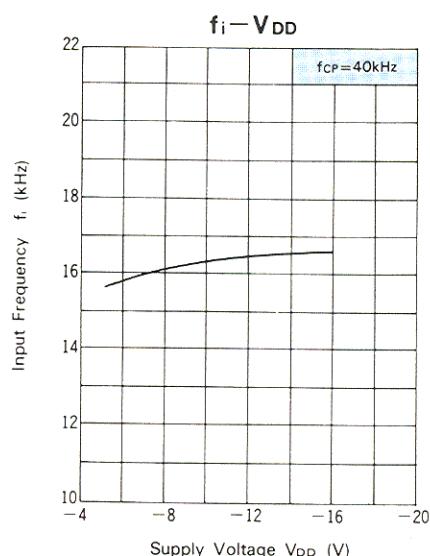
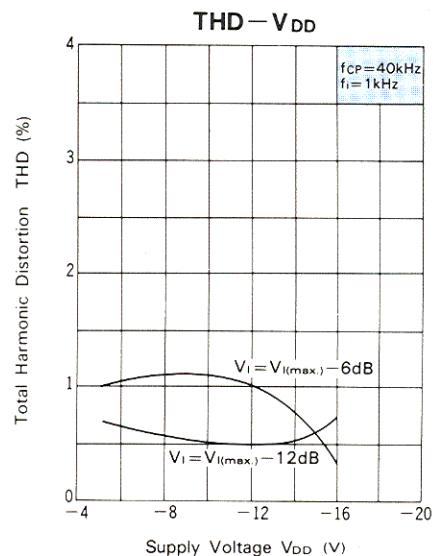
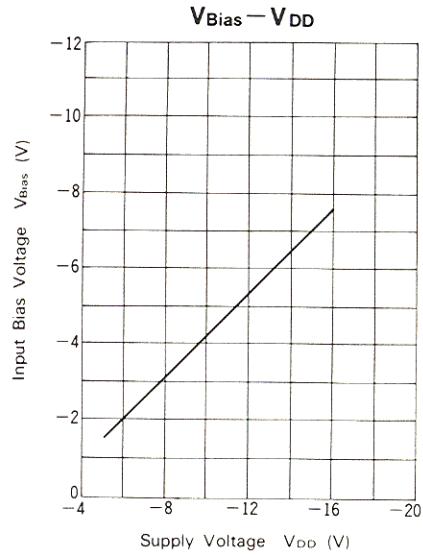
Circuit Diagram



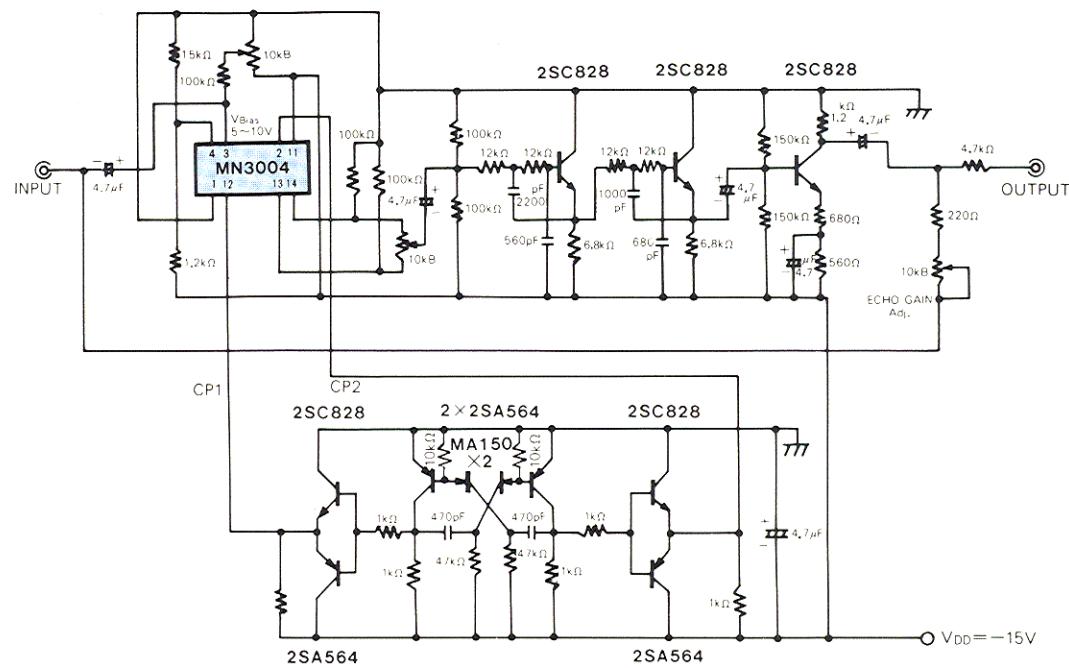
Typical Electrical Characteristic Curves



Supply Voltage Characteristics



Application Circuit



Echo Effect Generation Circuit (Signal Delay Over 10msec.)

4096-STAGE LOW NOISE BBD

General Description

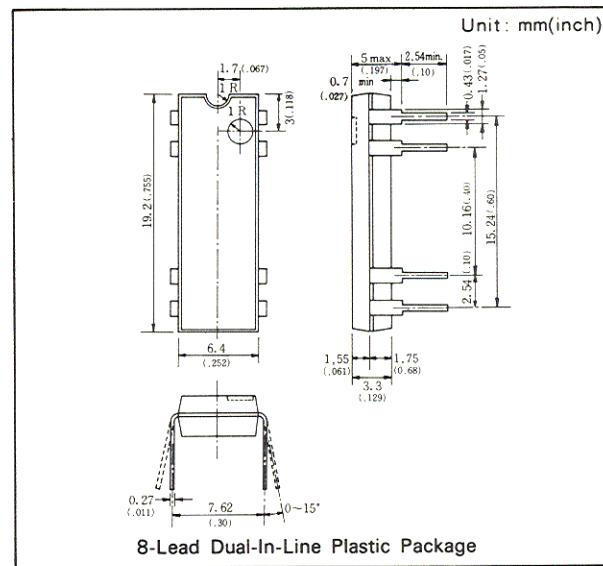
The MN3005 is a 4096-stage long delay BBD (Bucket Brigade Device) that provides a signal delay of up to 204.8 msec and is suitable for use as variable signal delay lines in audio frequency range.

Features:

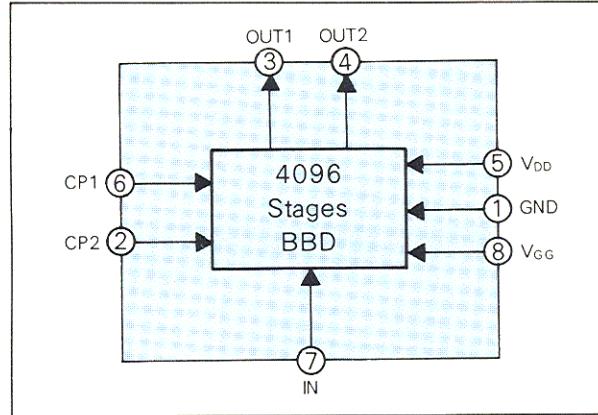
- Wide range of variable delay time : 20.48~204.8msec.
- Clock component cancellation capability.
- No insertion loss : $L_i \approx 0$ dB typ.
- Wide dynamic range : $S/N \approx 75$ dB typ.
- Wide frequency response : $f_i \leq 10$ kHz.
- Low distortion : THD=1% typ. ($V_i=0.78$ Vrms)
- Clock frequency range : 10~100kHz.
- P-channel silicon gate, tetrode MOS transistors configuration.
- 8-lead dual-in-line plastic package.

Applications:

- Reverberation effect of echo microphones and stereo equipment.
- Chorus effects in electronic musical instruments.
- Variable or fixed delay of analog signals.
- Telephone time compression and delay line for voice communication systems : etc.



Block Diagram



Quick Reference Data

Item	Symbol	Value	Unit
Supply Voltage	V_{DD}, V_{GG}	$-15, V_{DD}+1$	V
Signal Delay Time	t_D	20.48~204.8	msec
Total Harmonic Distortion	THD	1	%
Signal to Noise Ratio	S/N	75	dB

Absolute Maximum Ratings (Ta=25°C)

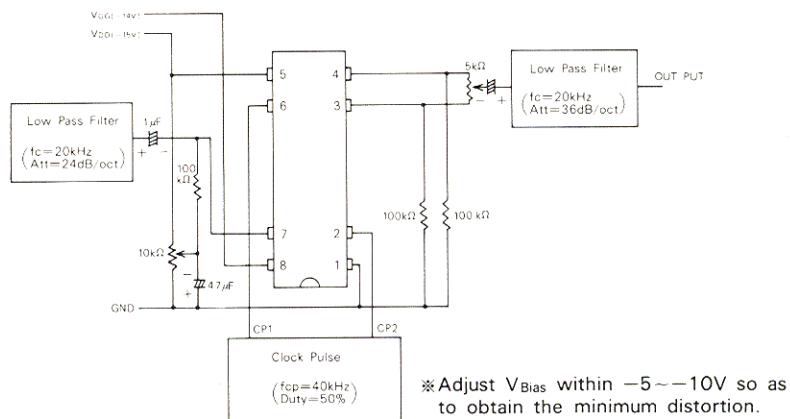
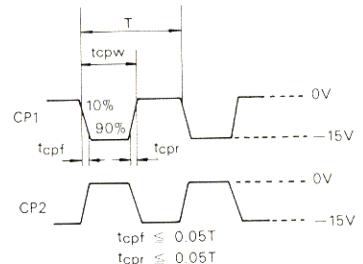
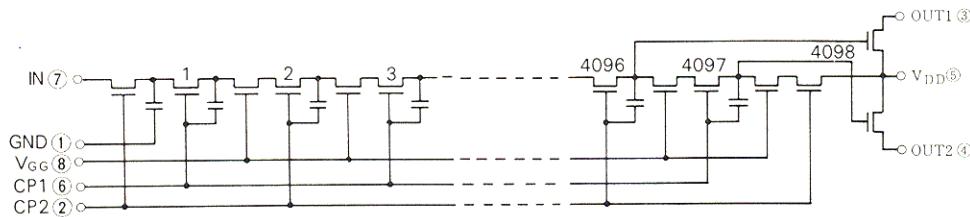
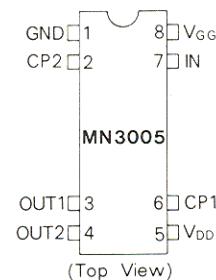
Item	Symbol	Ratings	Unit
Terminal Voltage	V _{DD} , V _{GG} , V _{CP} , V _I	-18~+0.3	V
Output Voltage	V _O	-18~+0.3	V
Operating Temperature	T _{opr}	-20~+ 60	°C
Storage Temperature	T _{stg}	-55~+125	°C

Operating Conditions (Ta=25°C)

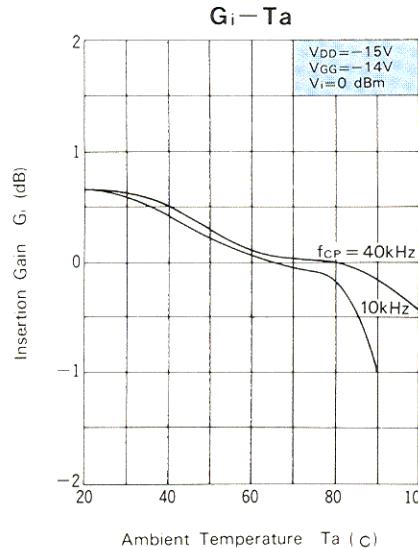
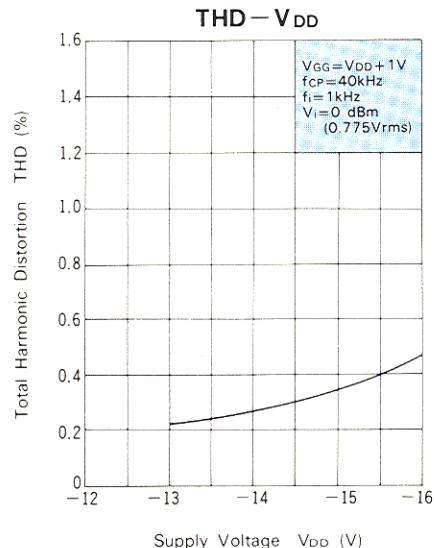
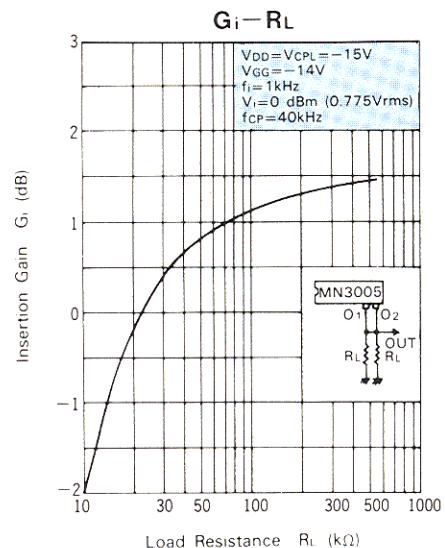
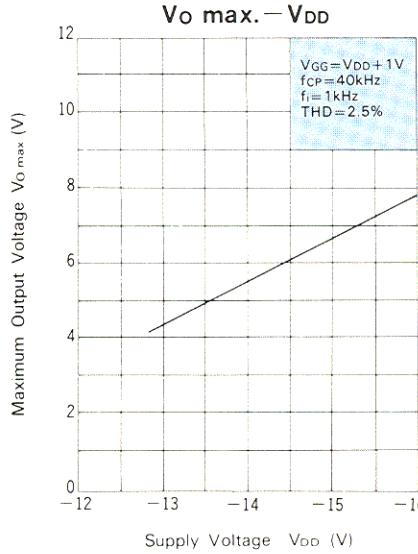
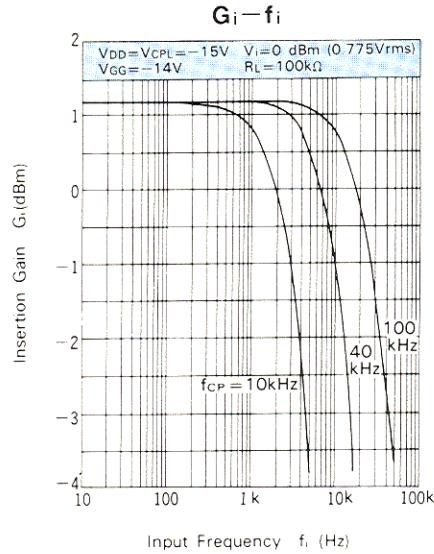
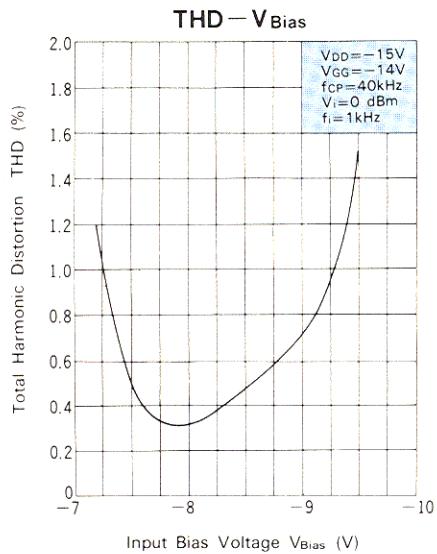
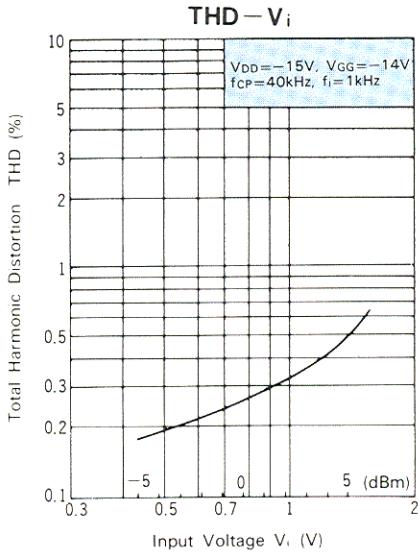
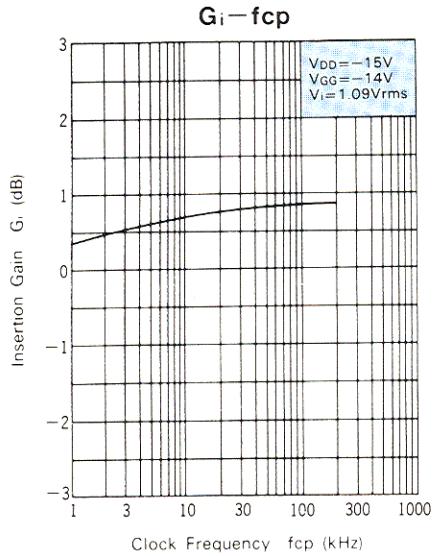
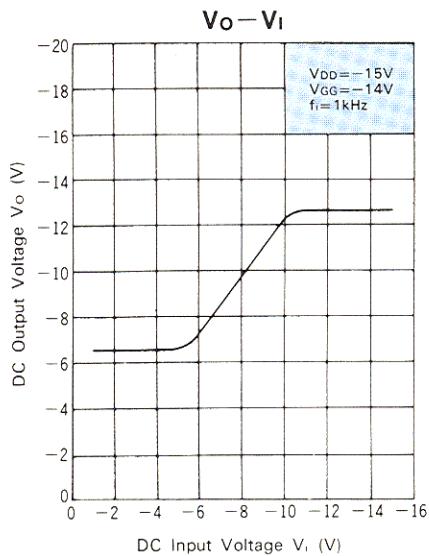
Item	Symbol	Condition	Min.	Typ.	Max.	Unit
Drain Supply Voltage	V _{DD}		-14	-15	-16	V
Gate Supply Voltage	V _{GG}			V _{DD} +1		V
Clock Voltage "H" Level	V _{CPH}		0		-1	V
Clock Voltage "L" Level	V _{CPL}			V _{DD}		V
Clock Input Capacitance	C _{CP}				2800	pF
Clock Frequency	f _{cp}		10		100	kHz
Clock Pulse Width *2	t _{cpw}	Test Circuit			0.5T*1	
Clock Rise Time *2	t _{cpri}	Test Circuit			500	nsec
Clock Fall Time *2	t _{cpf}	Test Circuit			500	nsec
Input DC Bias Voltage	V _{Bias}		-5		-10	V

*1 T=1/f_{cp} *2 Clock Pulse Waveforms**Electrical Characteristics (Ta=25°C, V_{DD}=V_{CPL}=-15V, V_{CPH}=0V, V_{GG}=-14V, R_L=100kΩ)**

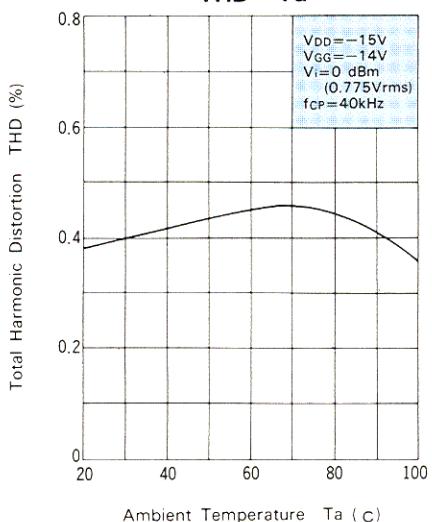
Item	Symbol	Condition	Min.	Typ.	Max.	Unit
Signal Delay Time	t _D		20.48		204.8	μsec
Input Signal Frequency	f _i	f _{cp} =40kHz, V _i =1.3Vrms, Output Attenuation ≤ 3dB(0dB at f _i =1kHz)			10	kHz
Input Signal Swing	V _i	f _{cp} =40kHz, f _i =1kHz, THD=2.5%			1.2	Vrms
Insertion Loss	L _i	f _{cp} =40kHz, f _i =1kHz, V _i =1.2Vrms	0	4		dB
Total Harmonic Distortion	THD	f _{cp} =40kHz, f _i =1kHz, V _i =0.78Vrms	1	2.5		%
Noise Voltage	V _{no}	f _{cp} =100kHz Weighted by "A" curve			0.4	mVrms
Signal to Noise Ratio	S/N		75			dB

Test Circuit**Clock Pulse Waveforms****Circuit Diagram****Terminal Assignments**

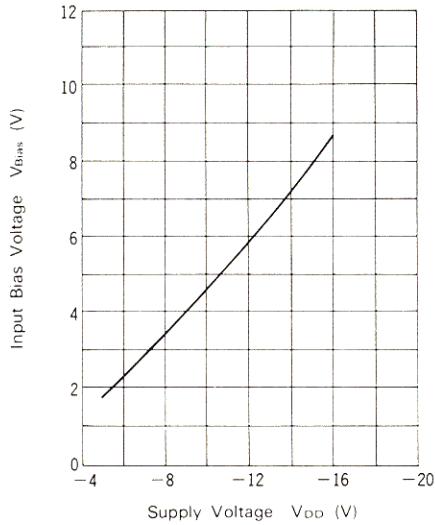
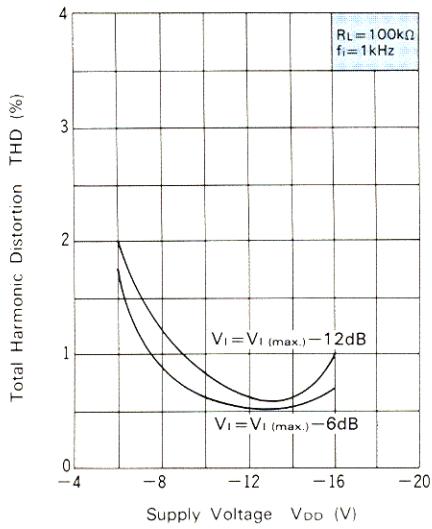
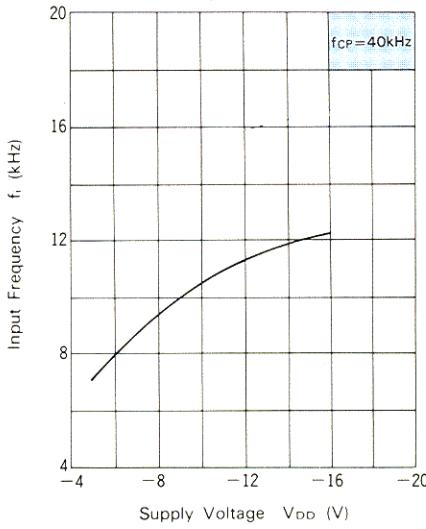
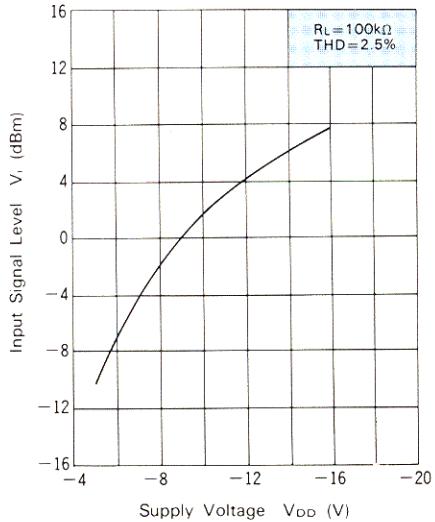
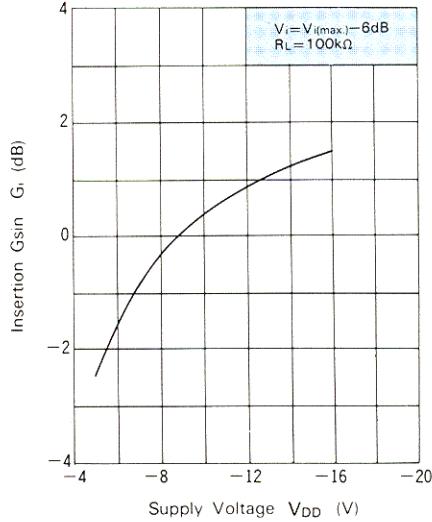
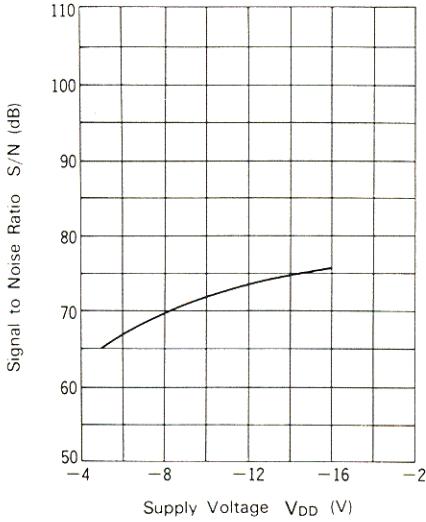
Typical Electrical Characteristic Curves



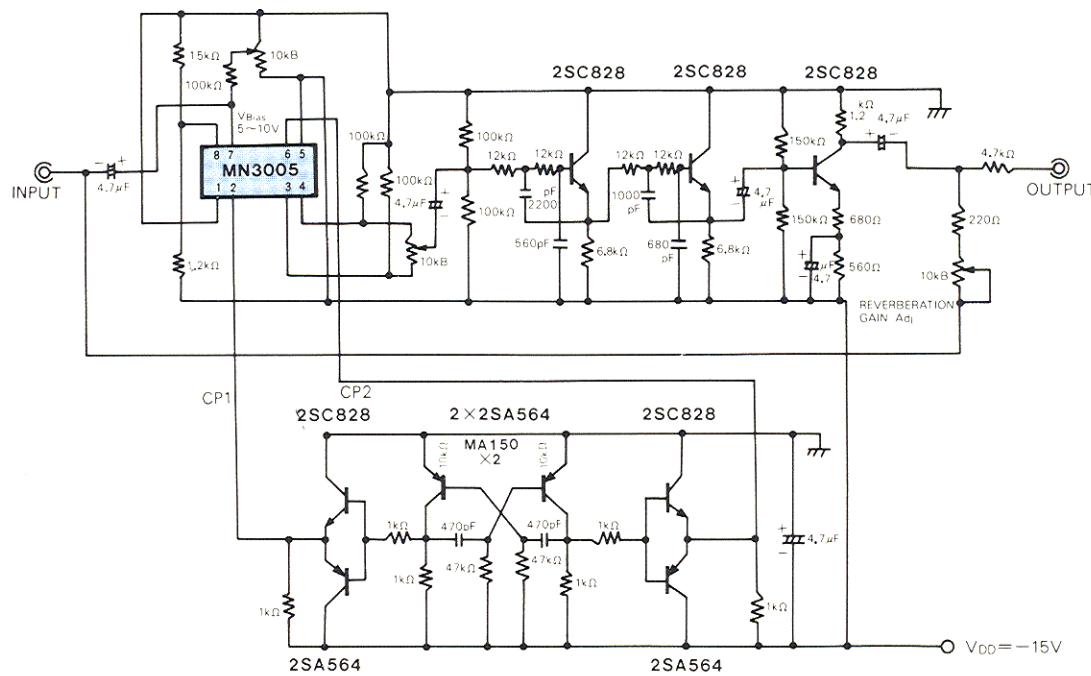
THD—Ta



Supply Voltage Characteristics

 $V_{Bias} - V_{DD}$ THD— V_{DD}  $f_i - V_{DD}$  $V_i - V_{DD}$  $G_i - V_{DD}$  $S/N - V_{DD}$ 

Application Circuit



Reverberation Effect Generation Circuit (Signal Delay Over 100msec.)

MN3006

128-STAGE LOW NOISE BBD

General Description

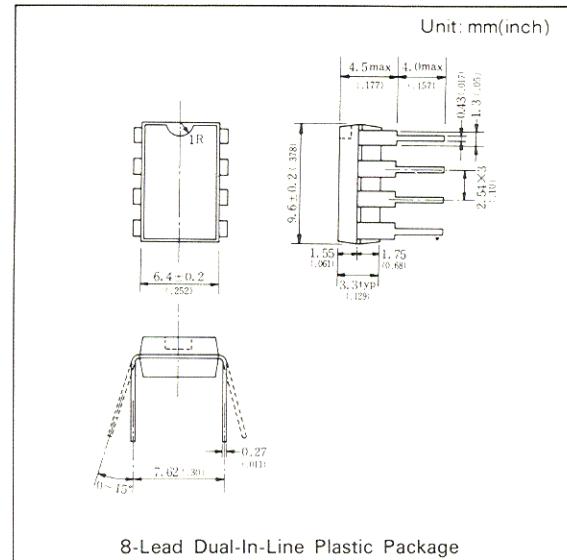
The MN3006 is a 128-stage Low Noise BBD (Bucket Brigade Device) that provides a signal delay of up to 6.4 msec. The typical applications are vibrato and chorus effects in electronic organs and musical instruments.

Features:

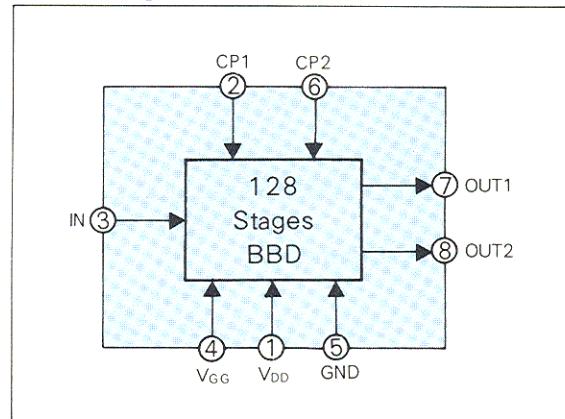
- Variable delay time : 0.32~6.4msec.
- Clock component cancellation capability.
- Low insertion loss : $L_i \approx 0$ dB typ.
- Wide dynamic range : S/N ≈ 90 dB typ.
- Wide frequency response : $f_i < 15$ kHz.
- Low Noise: $V_{no} = 0.2$ mVrms max.
- Total harmonic distortion : THD=0.2% typ. ($V_i=0.78$ Vrms)
- Clock frequency range : 10~200kHz.
- P-channel silicon gate, tetrode MOS transistors configuration.
- 8-lead dual-in-line plastic package.

Applications:

- Vibrato and / or chorus effects in electronic organs and musical instruments.
- Variable or fixed delay of analog signals.



Block Diagram



Quick Reference Data

Item	Symbol	Value	Unit
Supply Voltage	V_{DD} , V_{GG}	-15, $V_{DD} + 1$	V
Signal Delay Time	t_D	0.32~ 6.4	msec
Total Harmonic Distortion	THD	0.2	%
Signal to Noise Ratio	S/N	90	dB

BBD SERIES MN3006

Absolute Maximum Ratings (Ta=25°C)

Item	Symbol	Rating	Unit
Terminal Voltage	V _{DD} V _{GG} V _{CP} V _I	-18~+0.3	V
Output Voltage	V _O	-18~+0.3	V
Operating Temperature	T _{opr}	-20~+60	°C
Storage Temperature	T _{stg}	-55~+125	°C

Operating Conditions (Ta=25°C)

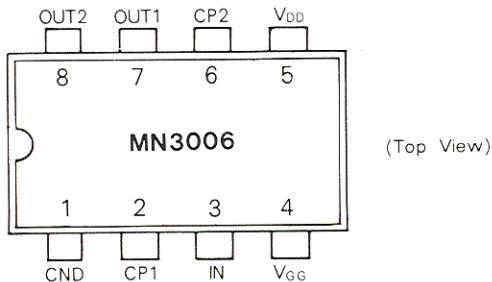
Item	Symbol	Min.	Typ.	Max.	Unit
Drain Supply Voltage	V _{DD}	-14	-15	-16	V
Gate Supply Voltage	V _{GG}		V _{DD} +1		V
Clock Voltage "H" Level	V _{CPH}	0		-1	V
Clock Voltage "L" Level	V _{CPL}		V _{DD}		V
Clock Input Capacitance	C _{CP}			100	pF
Clock Frequency	f _{CP}	10		200	kHz
Clock Pulse Width *2	t _{CPW}			0.5T *1	
Clock Rise Time *2	t _{CPR}			500	nsec
Clock Fall Time *2	t _{CPF}			500	nsec
Clock Cross Point	V _X	0		-3	V

*1 T=1/f_{CP} *2 Clock Pulse Waveforms

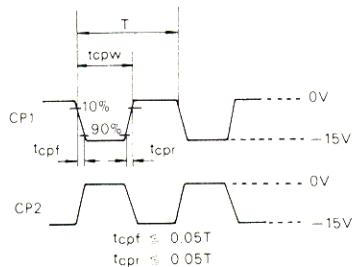
Electrical Characteristics (Ta=25°C, V_{DD}=V_{CPL}=-15V, V_{CPH}=0V, V_{GG}=-14V, R_L=100kΩ)

Item	Symbol	Condition	Min.	Typ.	Max.	Unit
Signal Delay Time	t _D		0.32		6.4	msec
Input Signal Frequency	f _i	f _{CP} =40kHz, V _i =1.8Vrms, 3dB down (0dB at f _i =1kHz)			12	kHz
Input Signal Swing	V _i	f _{CP} =40kHz, f _i =1kHz, THD=2.5%			1.8	Vrms
Insertion Loss	L _i	f _{CP} =40kHz, f _i =1kHz, V _i =1.8Vrms	-4	0	4	dB
Total Harmonic Distortion	THD	f _{CP} =40kHz, f _i =1kHz, V _i =0.78Vrms		0.2	2.5	%
Noise Voltage	V _{no}	f _{CP} =100kHz, Weighted by "A" curve		0.08	0.2	mVrms
Signal to Noise Ratio	S/N	Maximum output voltage to noise voltage		90		dB

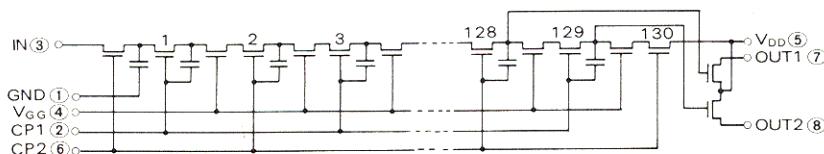
Terminal Assignments



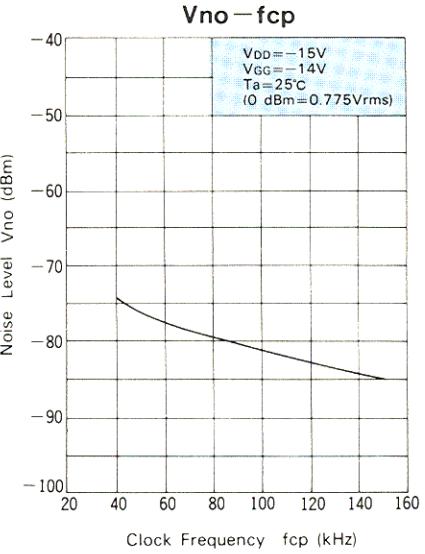
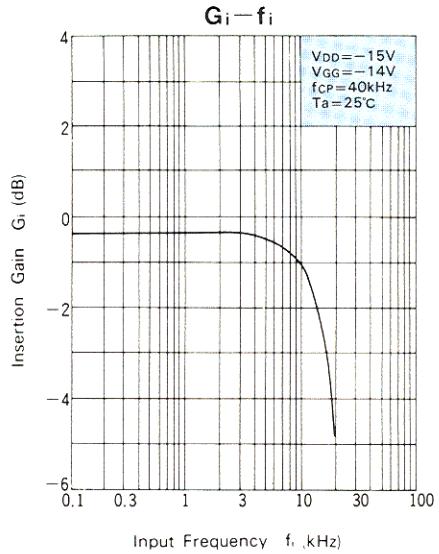
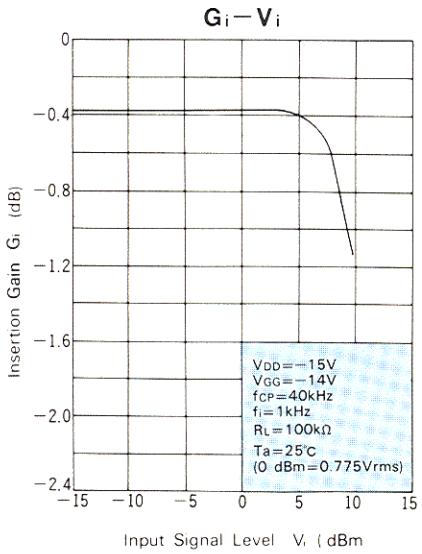
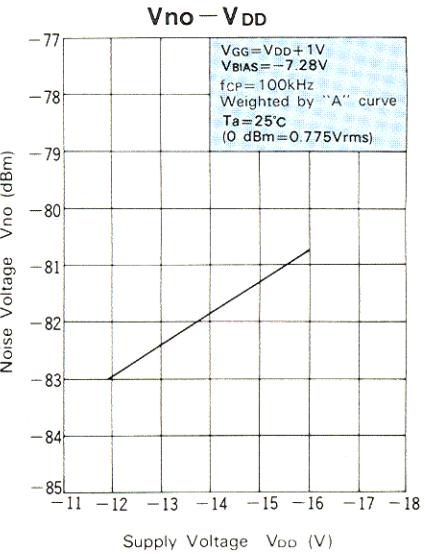
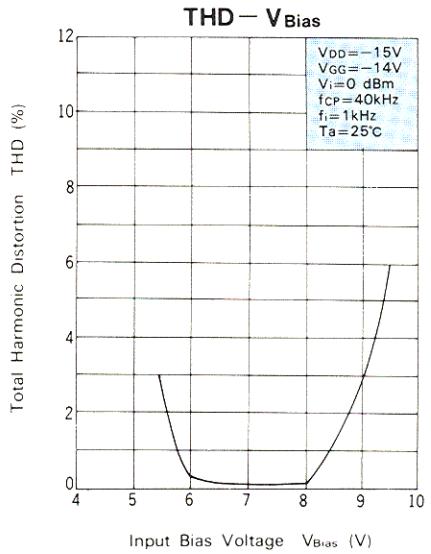
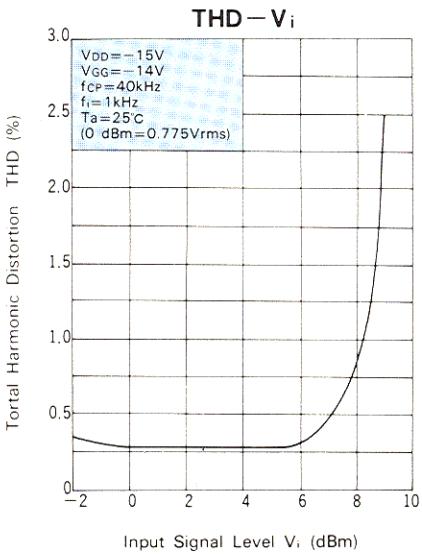
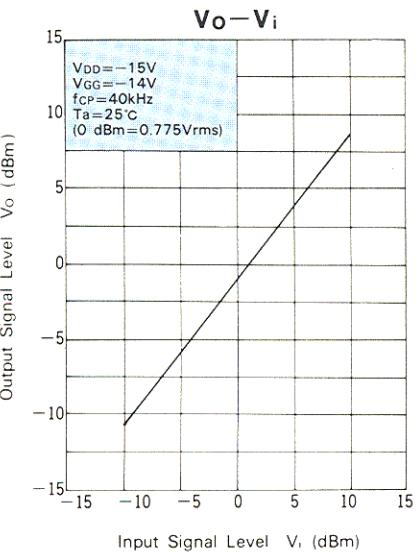
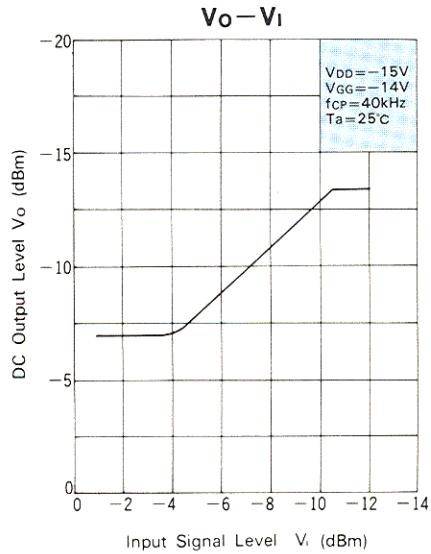
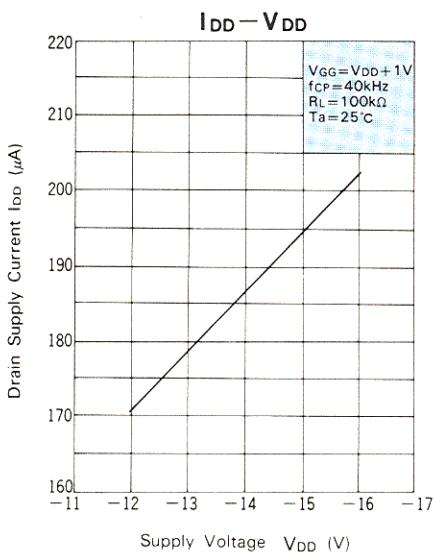
Clock Pulse Waveforms



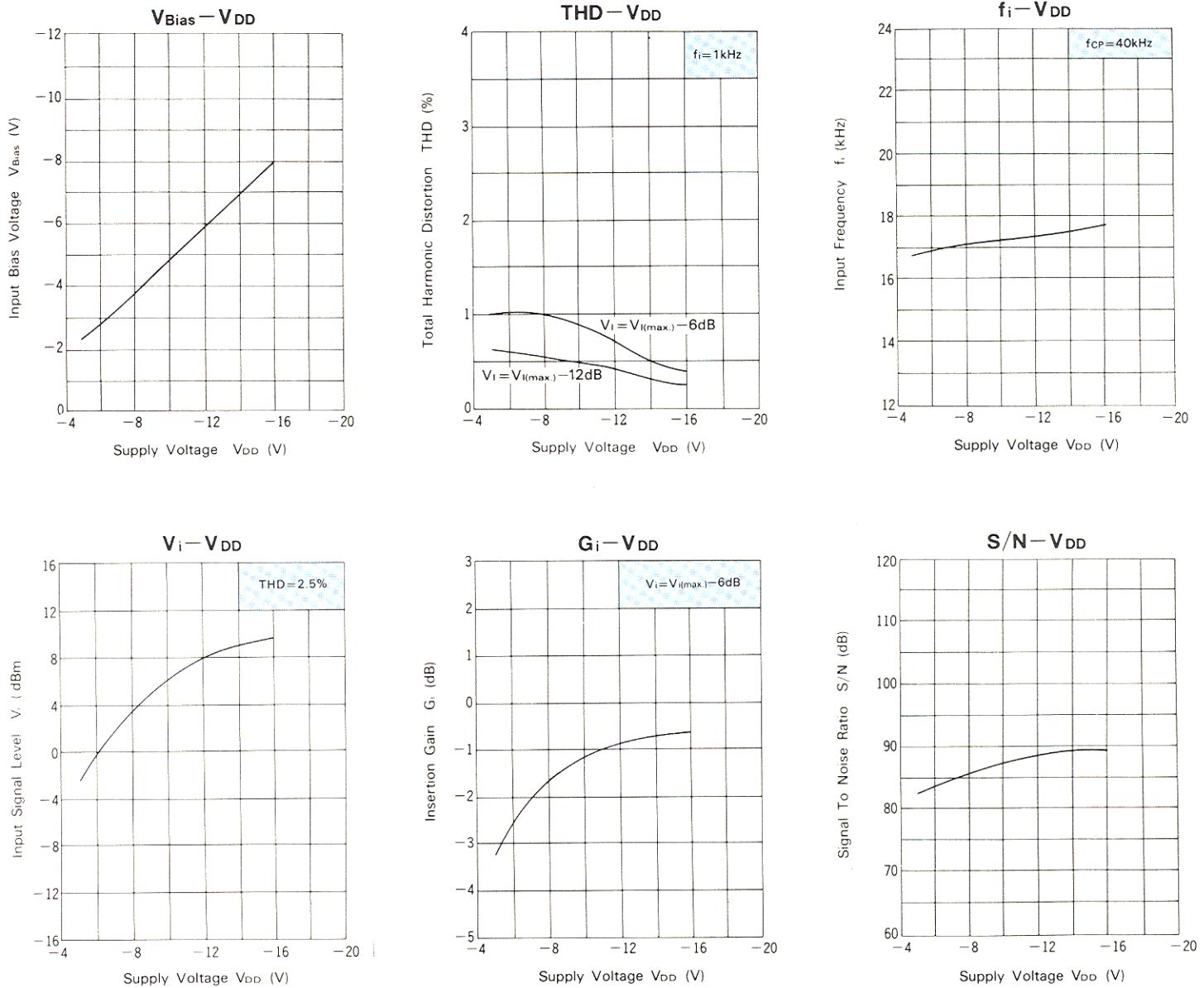
Circuit Diagram



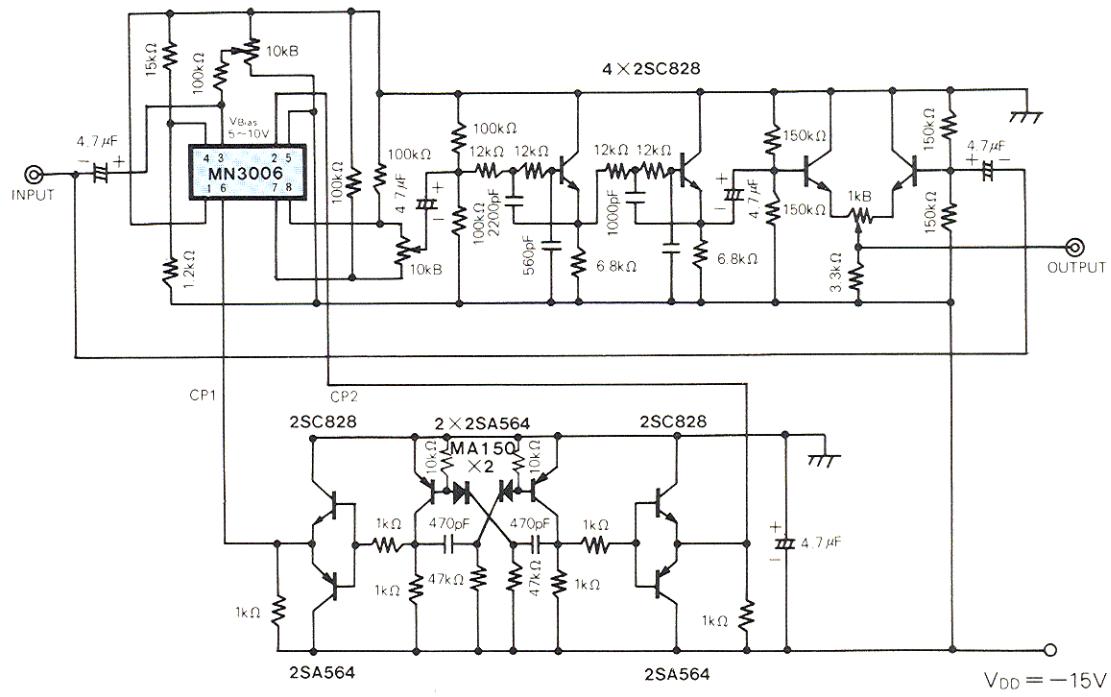
Typical Electrical Characteristic Curves



Supply Voltage Characteristics



Application Circuit



Chorus Effect Generation Circuit

1024-STAGE LOW NOISE BBD

General Description

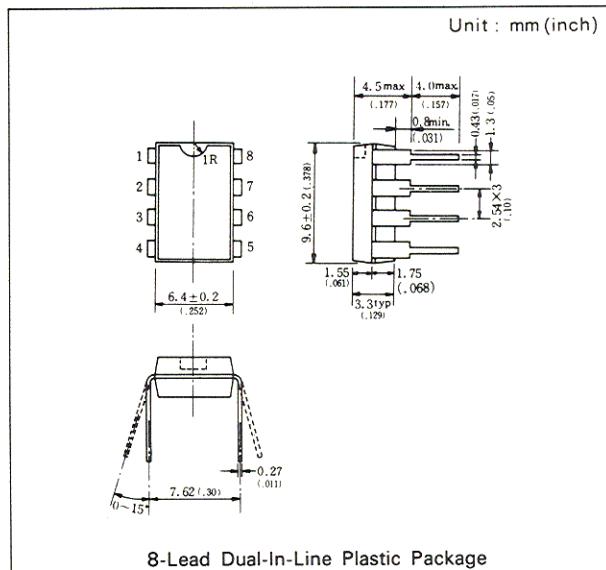
The MN3007 is a 1024-stage long delay BBD (Bucket Brigade Device) that provides a signal delay of up to 51.2msec. The MN3007 is particularly suitable for use as variable signal delay lines in audio frequency range.

Features:

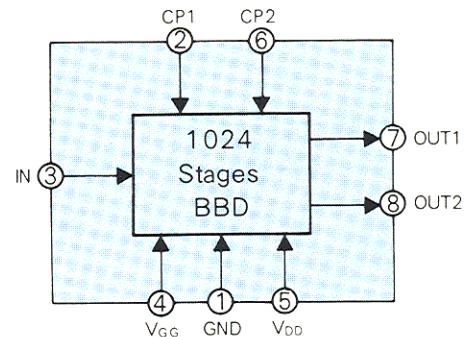
- Wide range of variable delay time: 5.12~51.2msec.
- Clock component cancellation capability.
- No insertion loss: $L_i \simeq 0$ dB typ.
- Wide dynamic range: $S/N \simeq 80$ dB typ.
- Wide frequency response: $f_i < 12$ kHz.
- Total harmonic distortion: THD=0.5% typ. ($V_i=0.78$ Vrms)
- Clock frequency range: 10~100kHz.
- P-channel silicon gate, tetrode MOS transistors configuration
- 8-lead dual-in-line plastic package.

Applications:

- Reverberation effect of echo microphones and stereo equipment.
- Chorus effects in electronic musical instruments.
- Variable or fixed delay of analog signals.



Block Diagram



Quick Reference Data

Item	Symbol	Value	Unit
Supply Voltage	V_{DD} , V_{GG}	-15, $V_{DD}+1$	V
Signal Delay Time	t_D	5.12~51.2	msec
Total Harmonic Distortion	THD	0.5	%
Signal to Noise Ratio	S/N	80	dB

Absolute Maximum Ratings (Ta=25°C)

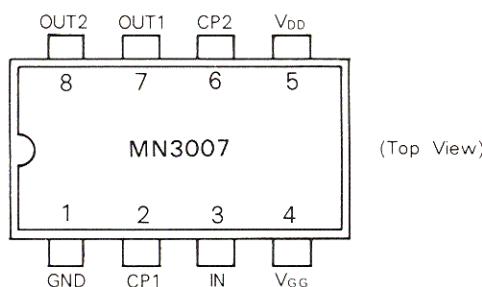
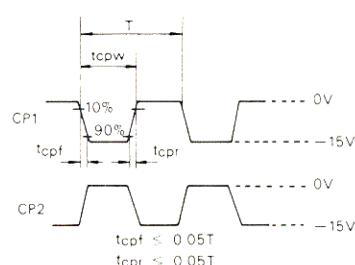
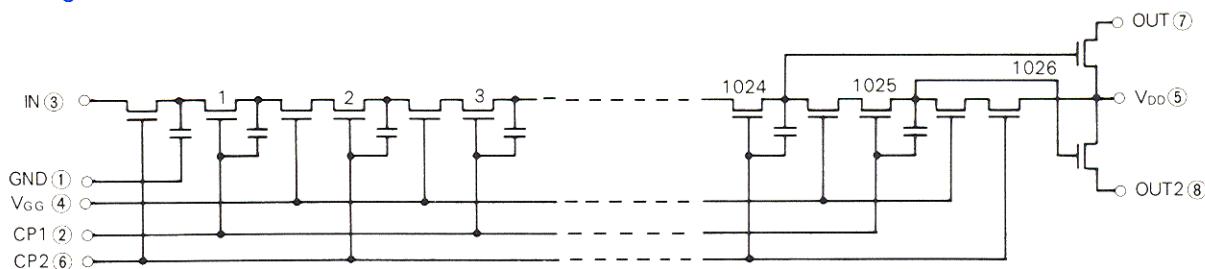
Item	Symbol	Ratings	Unit
Terminal Voltage	V _{DD} , V _{GG} , V _{CP} , V _I	-18~+0.3	V
Output Voltage	V _O	-18~+0.3	V
Operating Temperature	T _{opr}	-20~+60	°C
Storage Temperature	T _{stg}	-55~+125	°C

Operating Conditions (Ta=25°C)

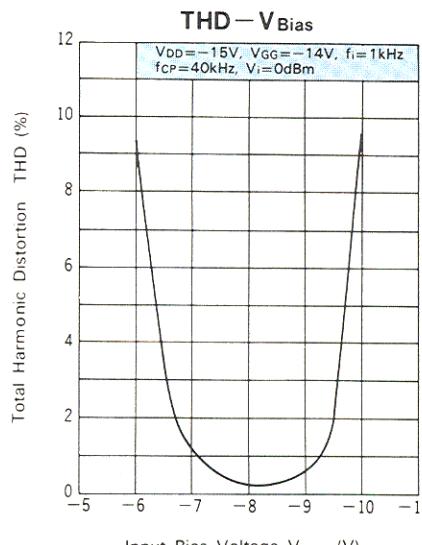
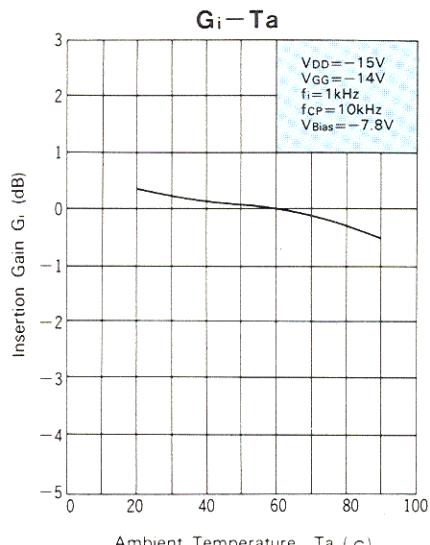
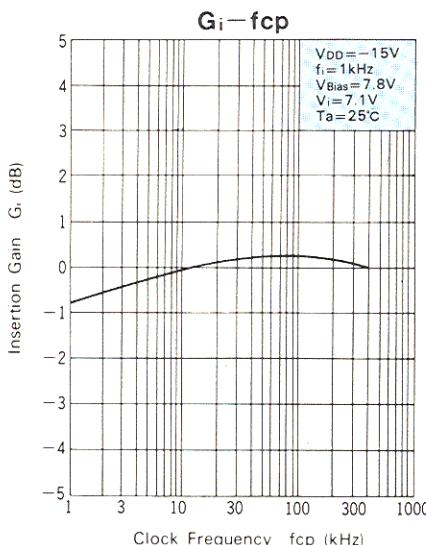
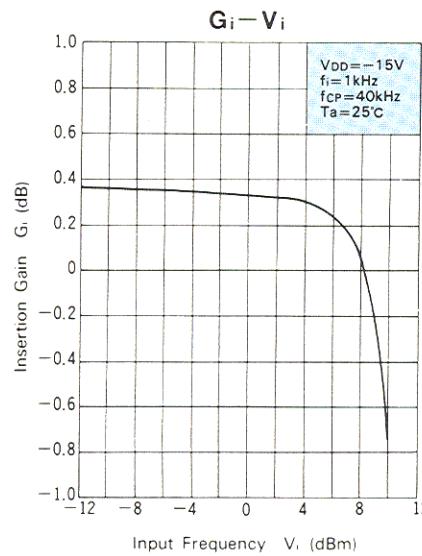
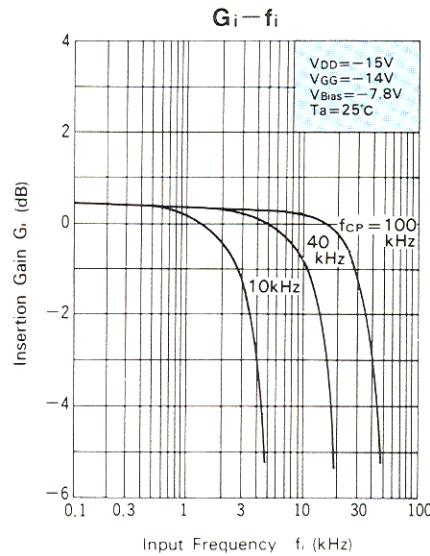
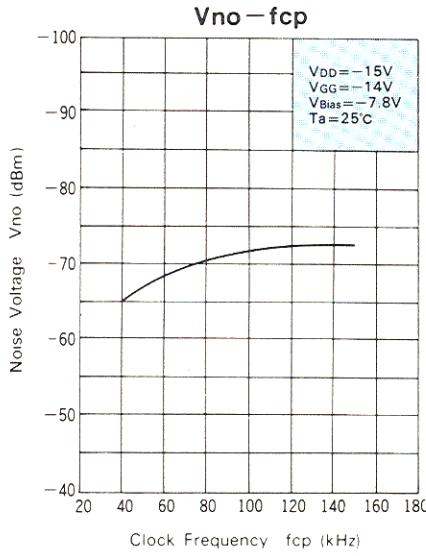
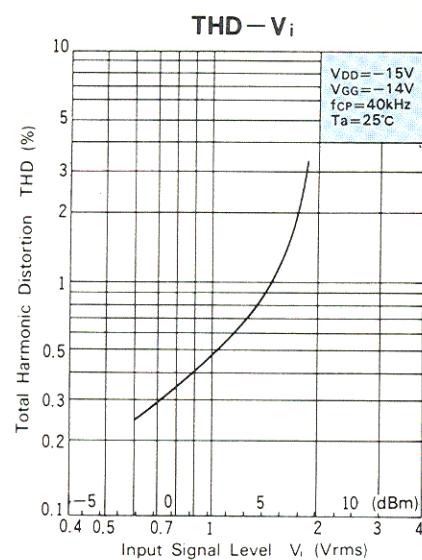
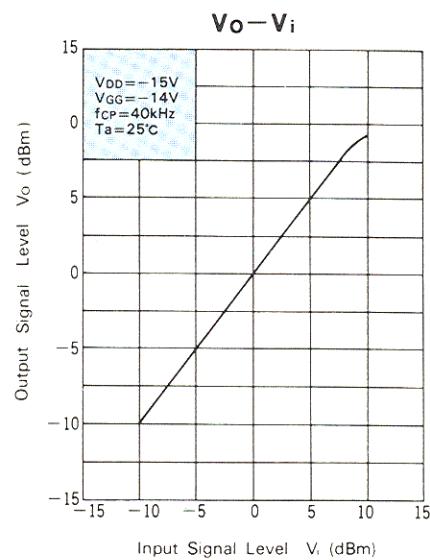
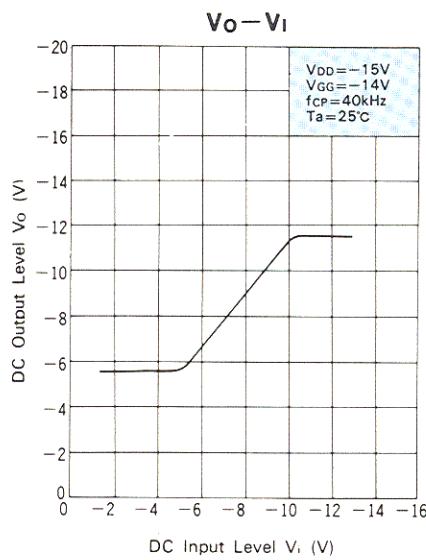
Item	Symbol	Min.	Typ.	Max.	Unit
Drain Supply Voltage	V _{DD}	-14	-15	-16	V
Gate Supply Voltage	V _{GG}		V _{DD} +1		V
Clock Voltage "H" Level	V _{CPH}	0		-1	V
Clock Voltage "L" Level	V _{CPL}		V _{DD}		V
Clock Input Capacitance	C _{CP}			700	pF
Clock Frequency	f _{CP}	10		100	kHz
Clock Pulse Width *2	t _{cpw}			0.5T *1	
Clock Rise Time *2	t _{cpri}			500	nsec
Clock Fall Time *2	t _{cpcf}			500	nsec
Clock Cross Point	V _x	0		-3	V

*1 T=1/f_{CP} *2 Clock Pulse Waveforms**Electrical Characteristics (Ta=25°C, V_{DD}=V_{CPL}=-15V, V_{CPH}=0V, V_{GG}=-14V, R_L=100kΩ)**

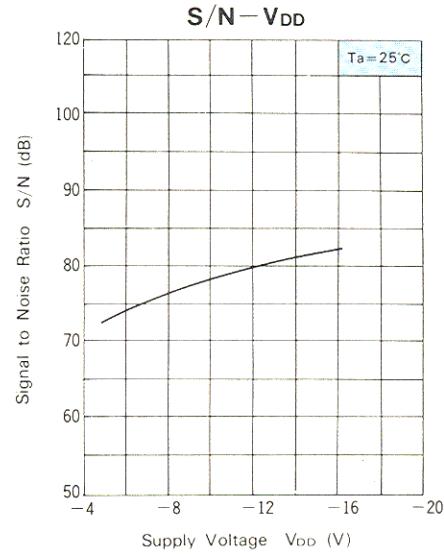
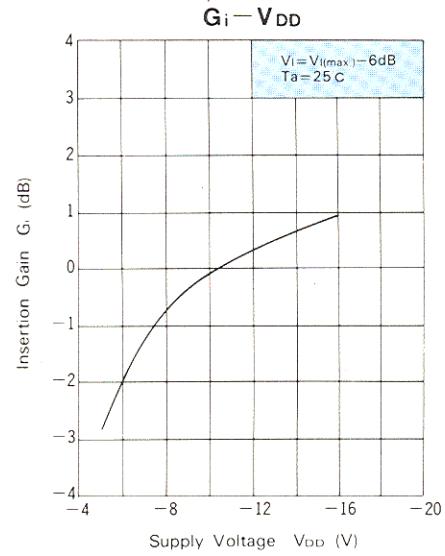
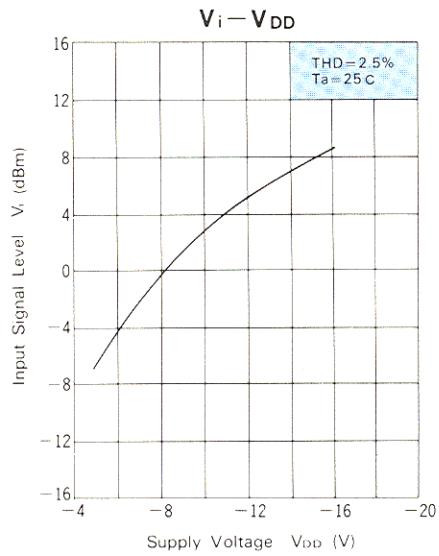
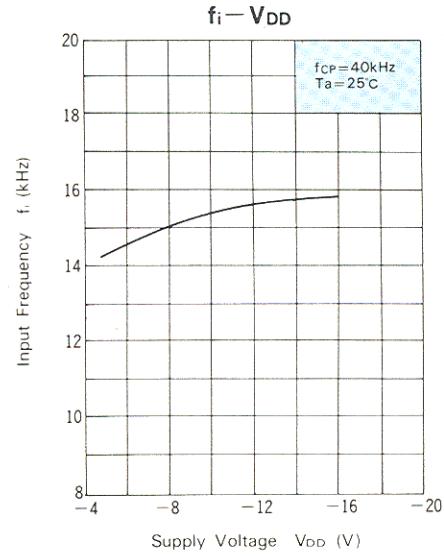
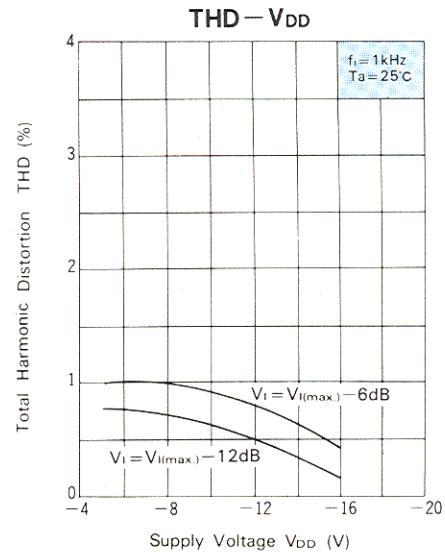
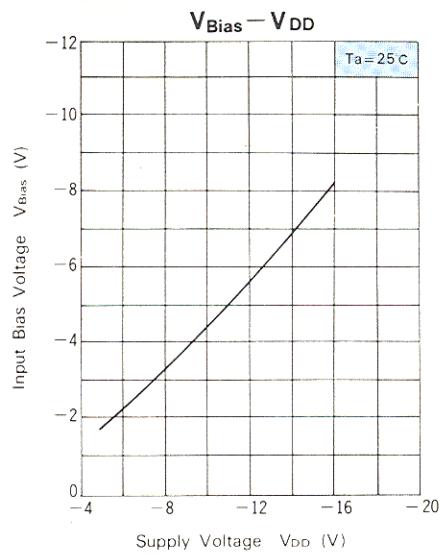
Item	Symbol	Condition	Min.	Typ.	Max.	Unit
Signal Delay Time	t _D		5.12		51.2	msec
Input Signal Frequency	f _i	f _{CP} =40kHz, V _i =1.5VRms, 3dB down (0dB at f _i =1kHz)			12	kHz
Input Signal Swing	V _i	f _{CP} =40kHz, f _i =1kHz, THD=2.5%			1.5	VRms
Insertion Loss	L _i	f _{CP} =40kHz, f _i =1kHz, V _i =1.5VRms	-4	0	4	dB
Total Harmonic Distortion	THD	f _{CP} =40kHz, f _i =1kHz, V _i =0.78VRms		0.5	2.5	%
Noise Voltage	V _{no}	f _{CP} =100kHz Weighted by "A" curve			0.30	mVRms
Signal to Noise Ratio	S/N			80		dB

Terminal Assignments**Clock Pulse Waveforms****Circuit Diagram**

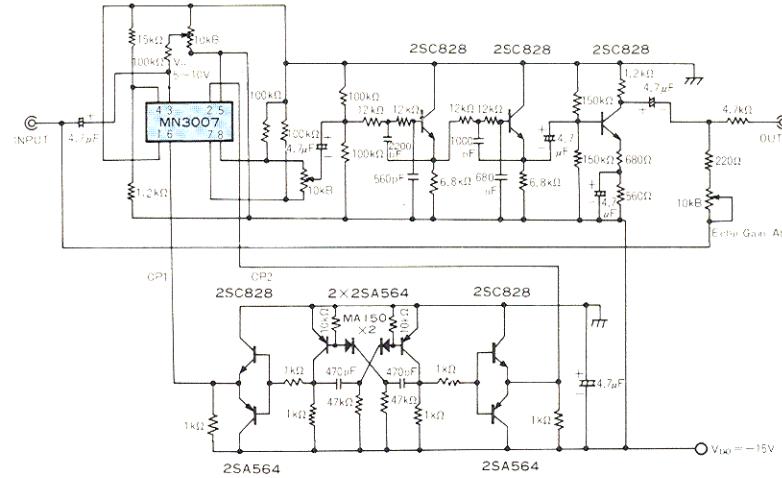
Typical Electrical Characteristic Curves



Supply Voltage Characteristics



Application Circuit



Echo Effect Generation Circuit (Signal Delay Over 10msec.)

2048-STAGE LOW NOISE BBD

General Description

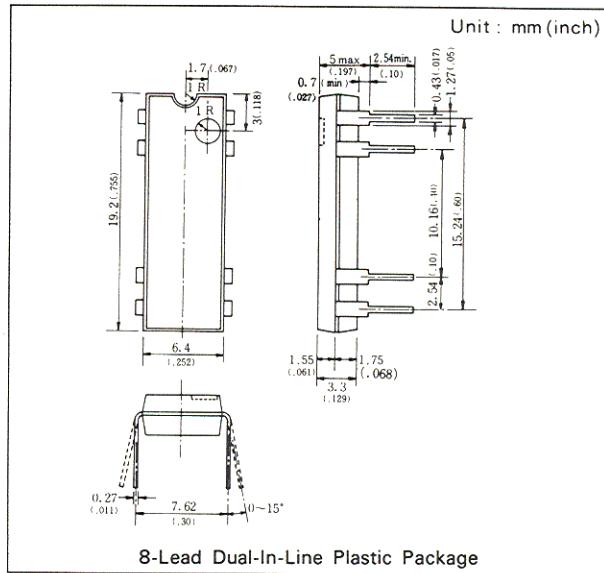
The MN3008 is a 2048-stage long delay BBD (Bucket Brigade Device) that provides a signal delay of up to 102.4msec. The MN3008 is particularly suitable for use as variable signal delay lines in audio frequency range.

Features:

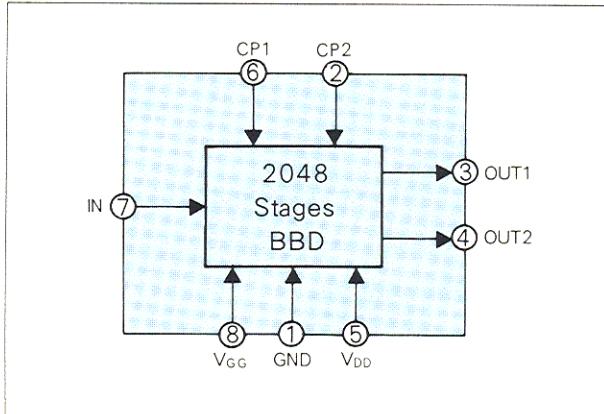
- Wide range of variable delay time: 10.24~102.4msec.
- Clock component cancellation capability.
- No insertion loss: $L_i \simeq 0$ dB typ.
- Wide dynamic range: S/N $\simeq 78$ dB typ.
- Wide frequency response: $f_i < 12$ kHz.
- Total harmonic distortion: THD=0.5% typ. ($V_i=0.78$ Vrms)
- Clock frequency range: 10~100kHz.
- P-channel silicon gate, tetrode MOS transistors configuration.
- 8-lead dual-in-line plastic package.

Applications:

- Reverberation effect of echo microphones and stereo equipment.
- Chorus effects in electronic musical instruments.
- Variable or fixed delay of analog signals.



Block Diagram



Quick Reference Data

Item	Symbol	Value	Unit
Supply Voltage	V_{DD} , V_{GG}	-15, $V_{DD}+1$	V
Signal Delay Time	t_D	10.24~102.4	msec
Total Harmonic Distortion	THD	0.5	%
Signal to Noise Ratio	S/N	78	dB

Absolute Maximum Ratings (Ta=25°C)

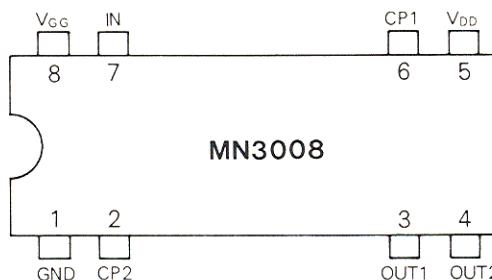
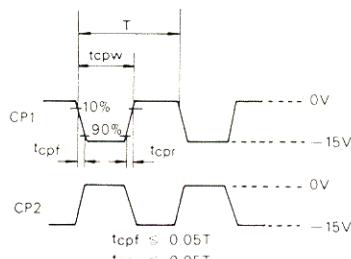
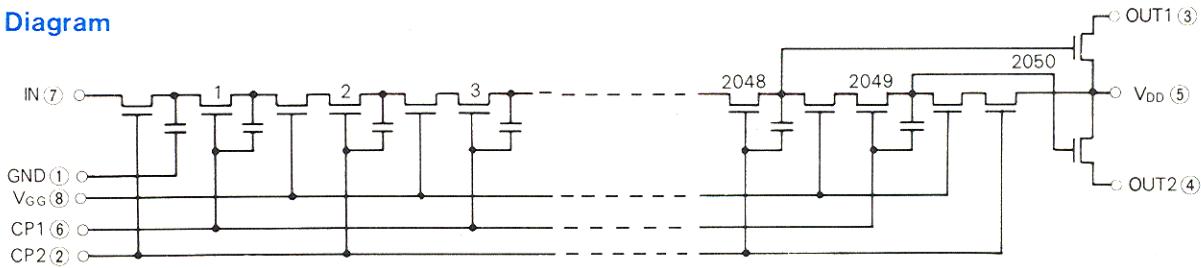
Item	Symbol	Ratings	Unit
Terminal Voltage	V _{DD} , V _{GG} , V _{CPL} , V _I	-18~+0.3	V
Output Voltage	V _O	-18~+0.3	V
Operating Temperature	T _{opr}	-20~+60	°C
Storage Temperature	T _{stg}	-55~+125	°C

Operating Conditions (Ta=25°C)

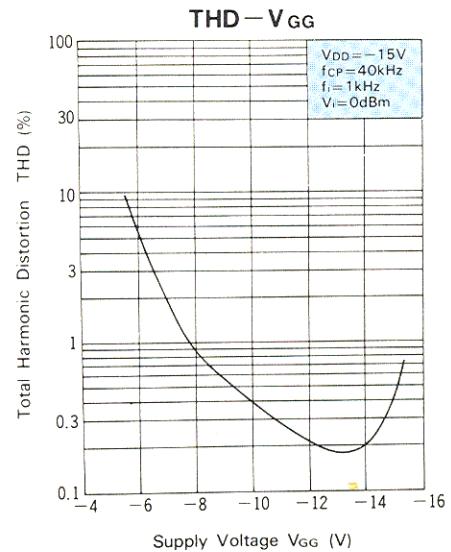
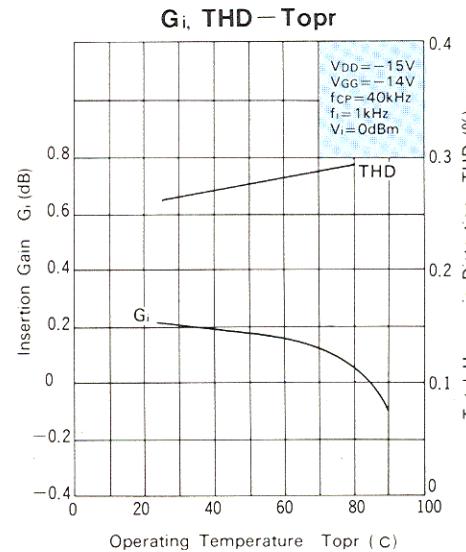
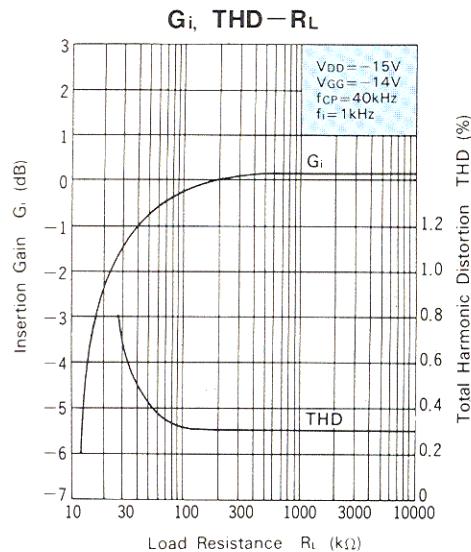
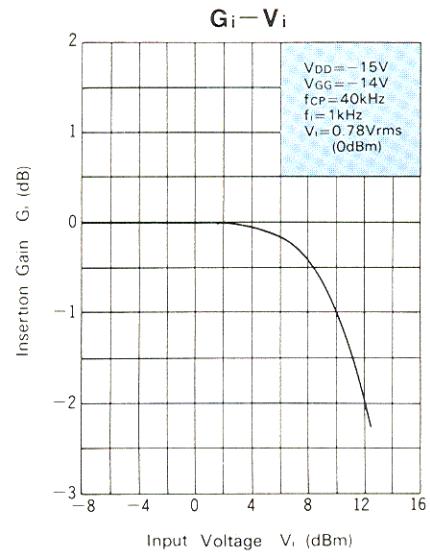
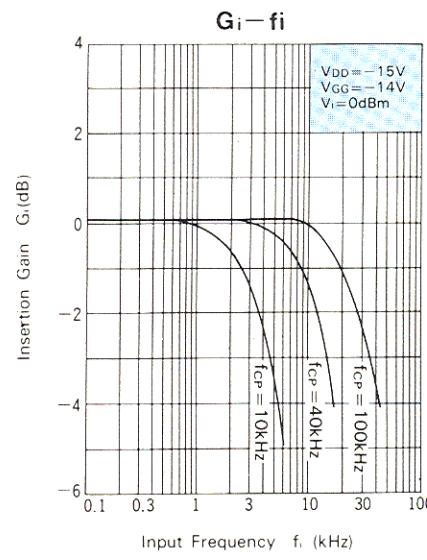
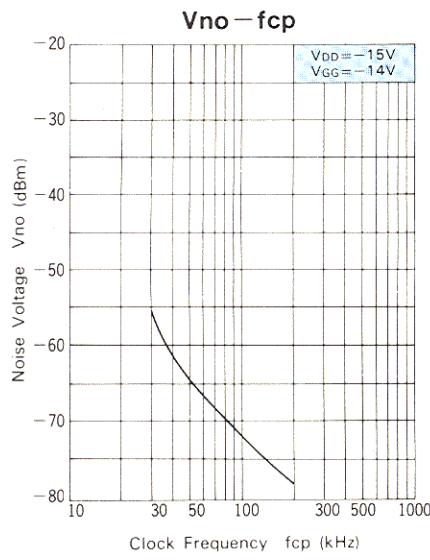
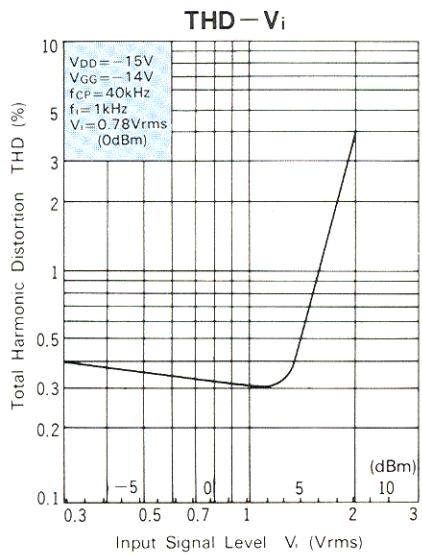
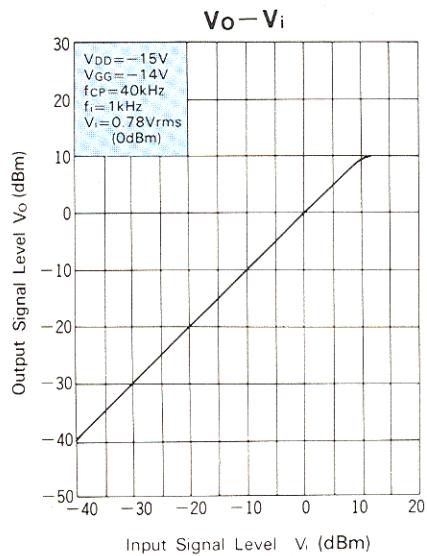
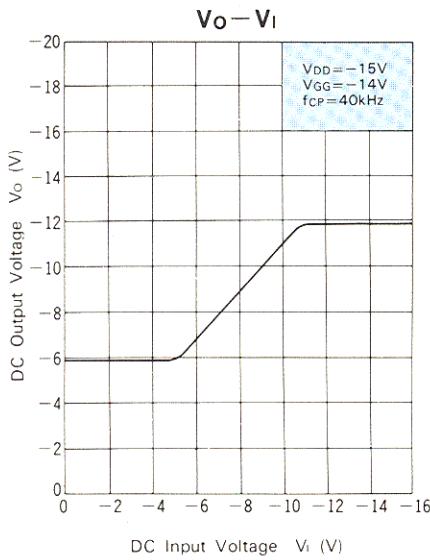
Item	Symbol	Min.	Typ.	Max.	Unit
Drain Supply Voltage	V _{DD}	-14	-15	-16	V
Gate Supply Voltage	V _{GG}		V _{DD} +1		V
Clock Voltage "H" Level	V _{CPH}	0		-1	V
Clock Voltage "L" Level	V _{CPL}		V _{DD}		V
Clock Input Capacitance	C _{CP}			1400	pF
Clock Frequency	f _{CP}	10		100	kHz
Clock Pulse Width *2	t _{cpw}			0.5T *1	
Clock Rise Time *2	t _{cpri}			500	nsec
Clock Fall Time *2	t _{cpcf}			500	nsec
Clock Cross Point	V _x	0		-3	V

*1 T=1/f_{CP} *2 Clock Pulse Waveforms**Electrical Characteristics (Ta=25°C, V_{DD}=V_{CPL}=-15V, V_{CPH}=0V, V_{GG}=-14V, R_L=100kΩ)**

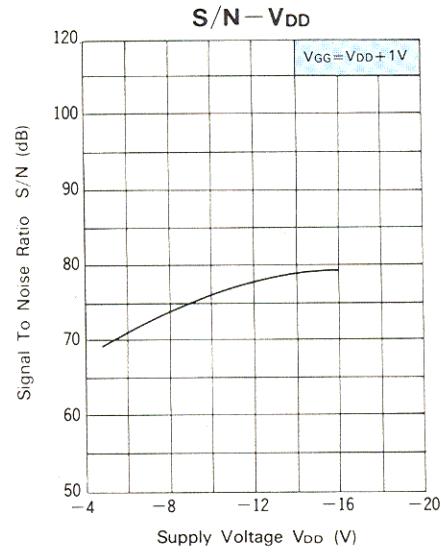
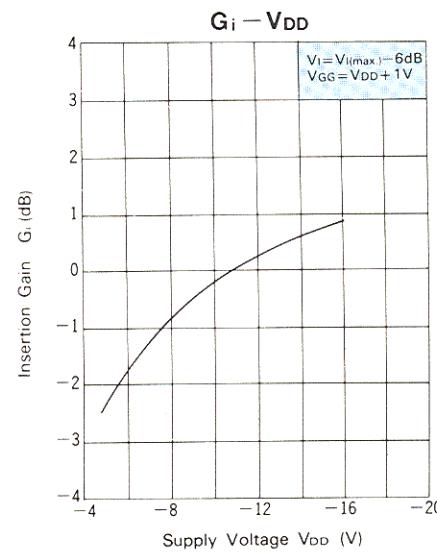
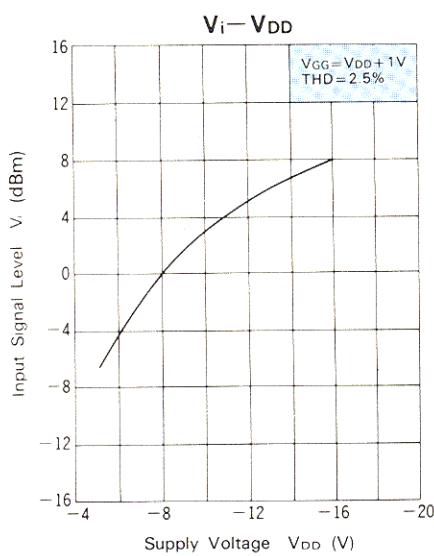
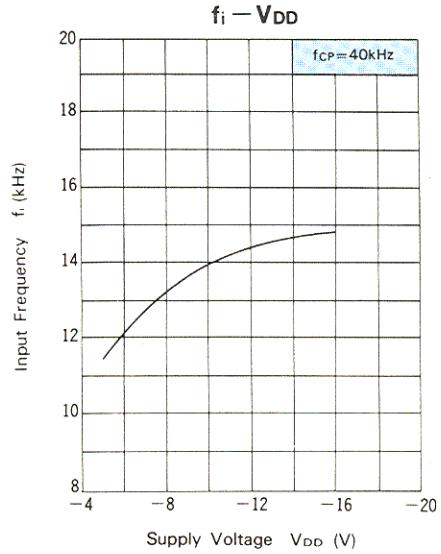
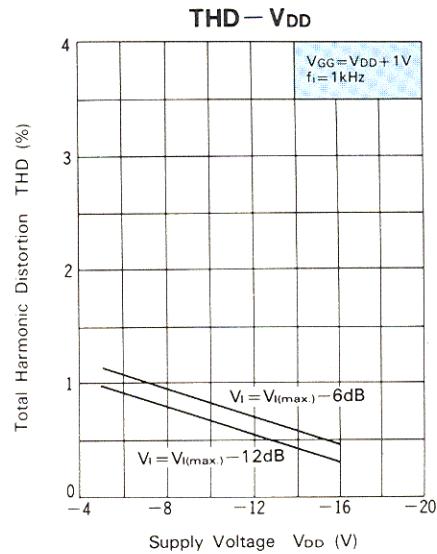
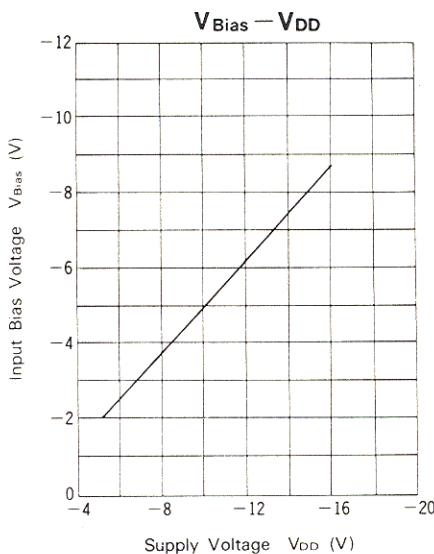
Item	Symbol	Condition	Min.	Typ.	Max.	Unit
Signal Delay Time	t _D		10.24		102.4	msec
Input Signal Frequency	f _i	f _{cp} =40kHz, V _i =1.3Vrms. 3dB down (0dB at f _i =1kHz)			12	kHz
Input Signal Swing	V _i	f _{cp} =40kHz, f _i =1kHz, THD=2.5%			1.5	Vrms
Insertion Loss	L _i	f _{cp} =40kHz, f _i =1kHz, V _i =1.3Vrms	0			dB
Total Harmonic Distortion	THD	f _{cp} =40kHz, f _i =1kHz, V _i =0.78Vrms	0.5			%
Noise	V _{no}	f _{cp} =100kHz Weighted by "A" curve			0.30	mVrms
Signal to Noise Ratio	S/N		78			dB

Terminal Assignments**Clock Pulse Waveforms****Circuit Diagram**

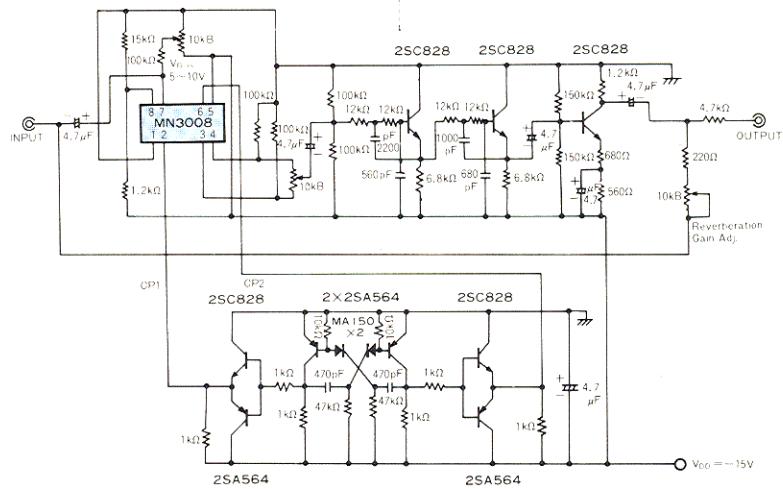
Typical Electrical Characteristic Curves



Supply Voltage Characteristics



Application Circuit



Reverberation Effect Generation Circuit (Signal Delay Over 100msec.)

256-STAGE LOW NOISE BBD

General Description

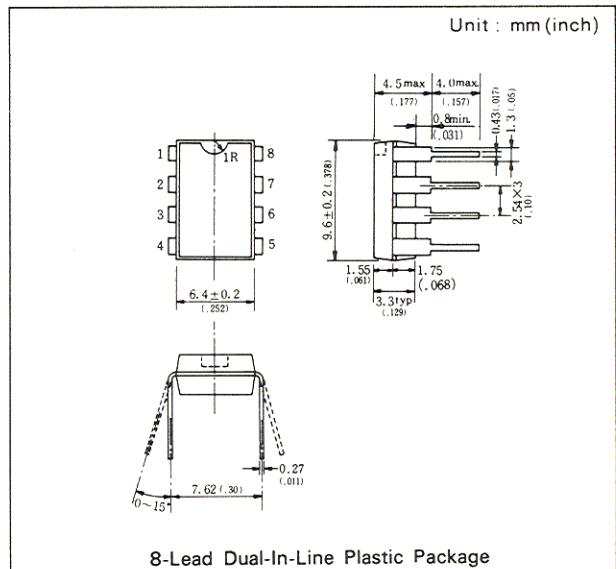
The 3009 is a 256-stage BBD (Bucket Brigade Device) having a wide dynamic range and low distortion characteristics. The 3009 provides a signal delay of up to 12.8msec and is particularly suitable as a device for generation of vibrato and / or chorus effects in electronic musical instruments.

Features:

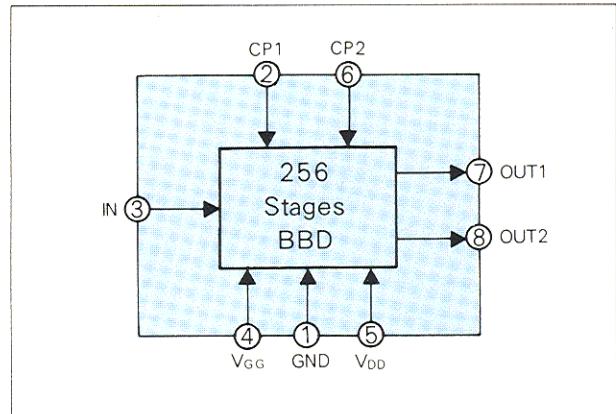
- Variable delay time: 0.64~12.8msec.
- Clock component cancellation capability.
- Low insertion loss: $L_i \approx 0$ dB typ.
- Wide dynamic range: $S/N \approx 88$ dB typ.
- Wide frequency response: $f_i < 14$ kHz.
- Total harmonic distortion: THD=0.3% typ. ($V_i=0.78$ Vrms)
- Clock frequency range: 10~200kHz.
- P-channel silicon gate, tetrode MOS transistors configuration.
- 8-lead dual-in-line plastic package.

Applications:

- Vibrato and / or chorus effects in electronic organs and musical instruments.
- Variable or fixed delay of analog signals.



Block Diagram



Quick Reference Data

Item	Symbol	Value	Unit
Supply Voltage	V _{DD} , V _{GG}	-15, V _{DD} +1	V
Signal Delay Time	t _D	0.64~12.8	msec
Total Harmonic Distortion	THD	0.3	%
Signal to Noise Ratio	S/N	88	dB

Absolute Maximum Ratings (Ta=25°C)

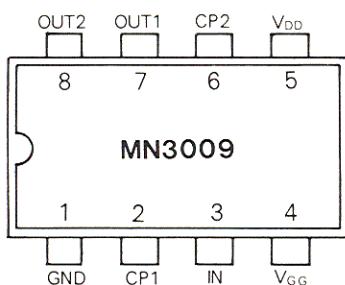
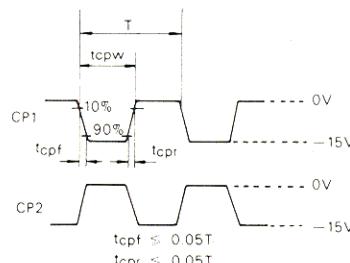
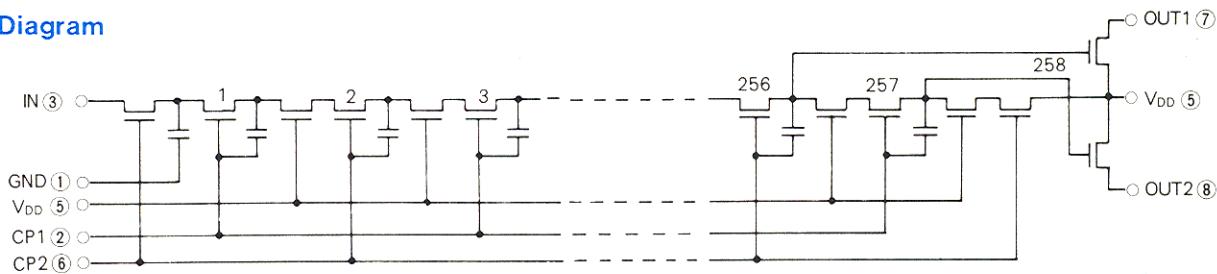
Item	Symbol	Ratings	Unit
Terminal Voltage	V _{DD} , V _{GG} , V _{CP} , V _I	-18 ~ +0.3	V
Output Voltage	V _O	-18 ~ +0.3	V
Operating Temperature	T _{opr}	-20 ~ +60	°C
Storage	T _{stg}	-55 ~ +125	°C

Operating Conditions (Ta=25°C)

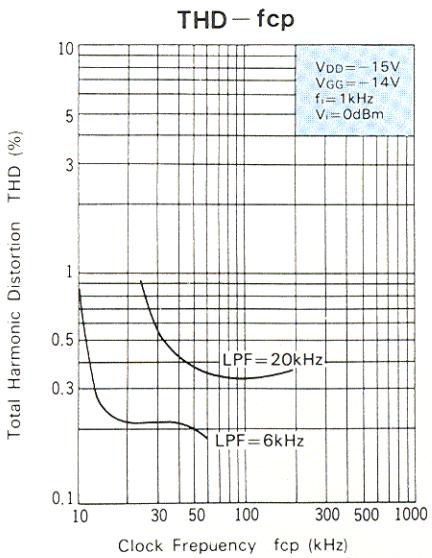
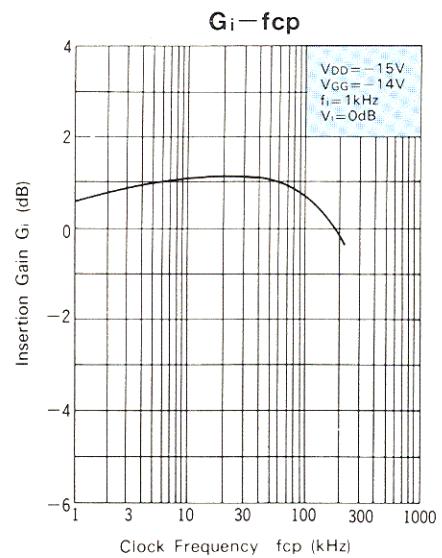
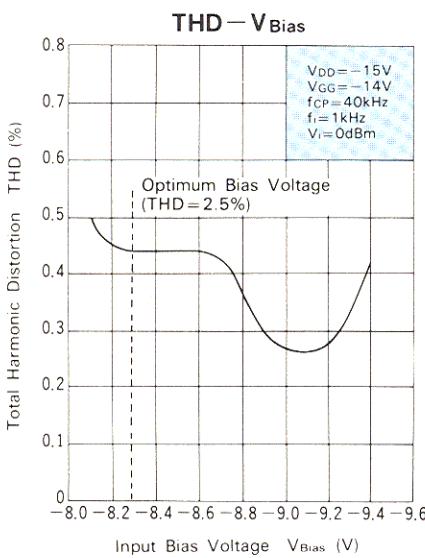
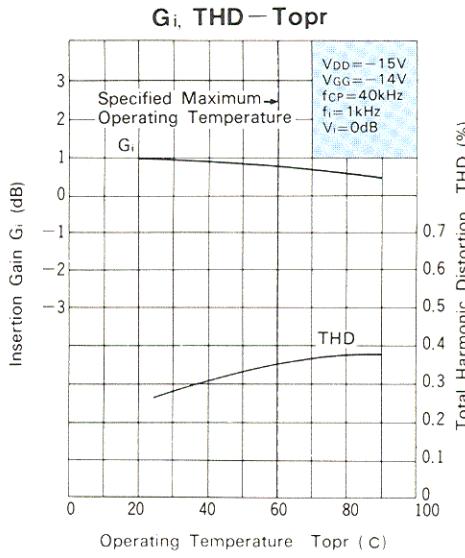
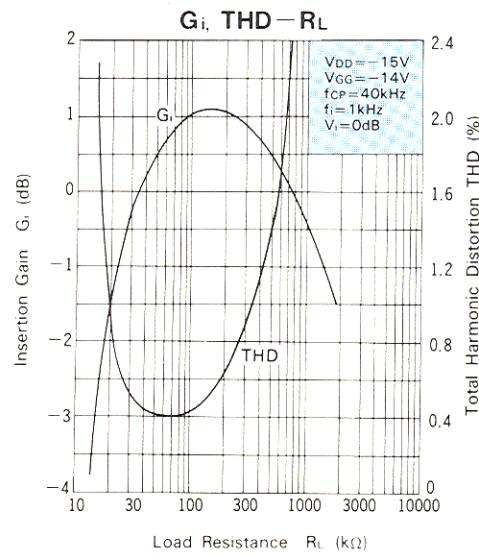
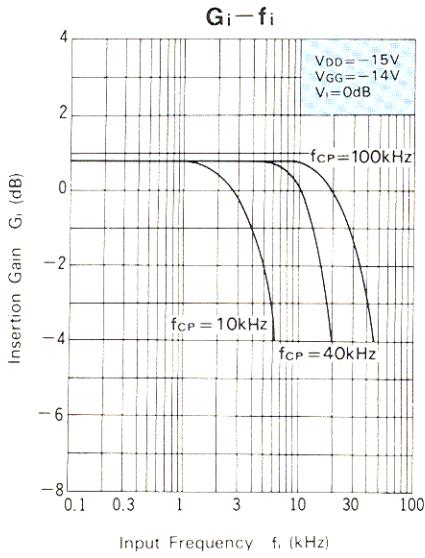
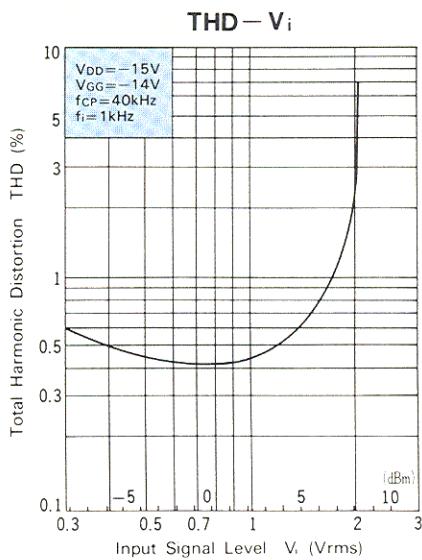
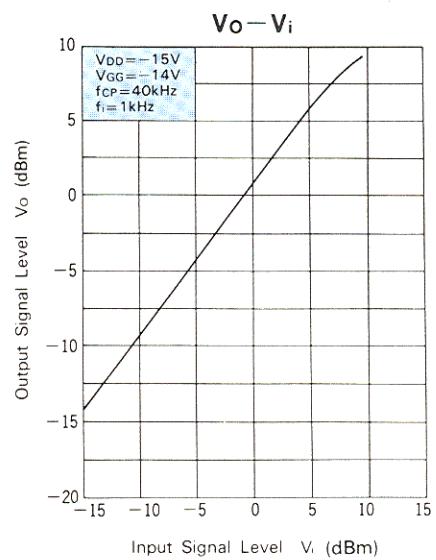
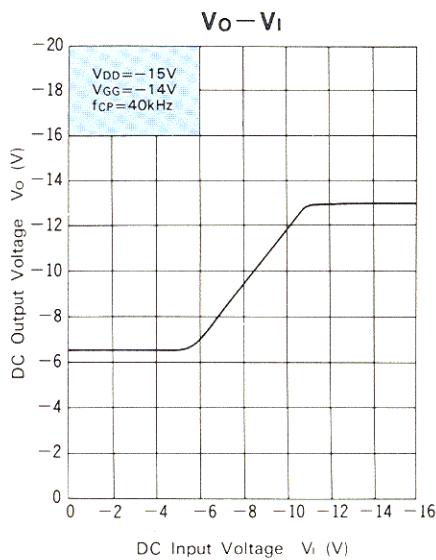
Item	Symbol	Min.	Typ.	Max.	Unit
Drain Supply Voltage	V _{DD}	-14	-15	-16	V
Gate Supply Voltage	V _{GG}		V _{DD} +1		V
Clock Voltage "H" Level	V _{CPH}	0		-1	V
Clock Voltage "L" Level	V _{CPL}		V _{DD}		V
Clock Input Capacitance	C _{CP}			200	pF
Clock Frequency	f _{CP}	10		200	kHz
Clock Pulse Width *2	t _{cpw}			0.5T *1	
Clock Rise Time *2	t _{cpri}			500	nsec
Clock Fall Time *2	t _{cpf}			500	nsec
Clock Cross Point	V _x	0		-3	V

*1 T=1/f_{CP} *2 Clock Pulse Waveforms**Electrical Characteristics (Ta=25°C, V_{DD}=V_{CPL}=-15V, V_{CPH}=0V, V_{GG}=-14V, R_L=100kΩ)**

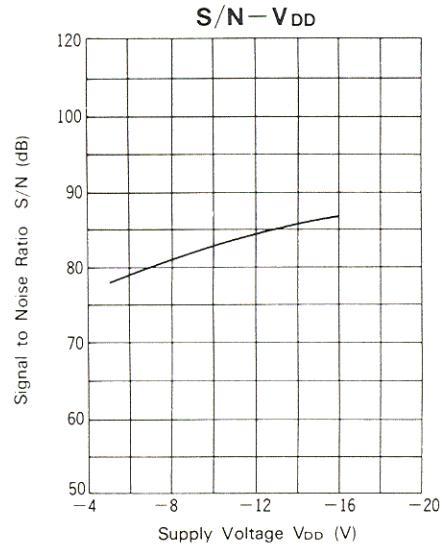
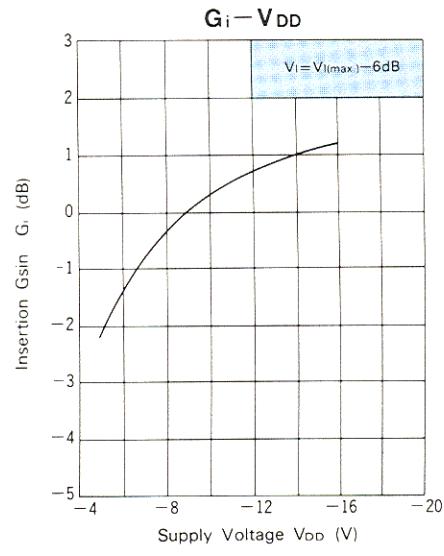
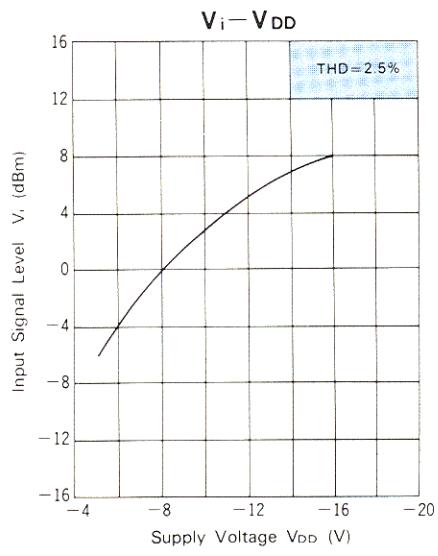
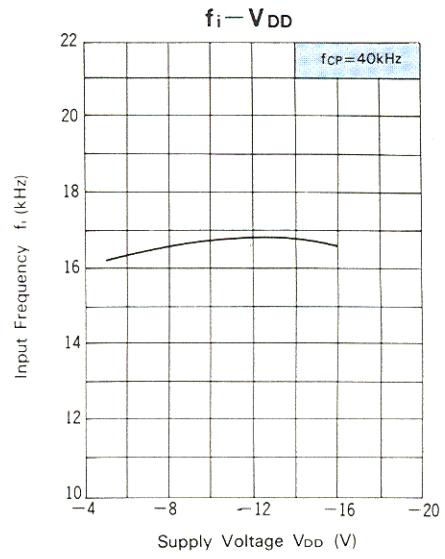
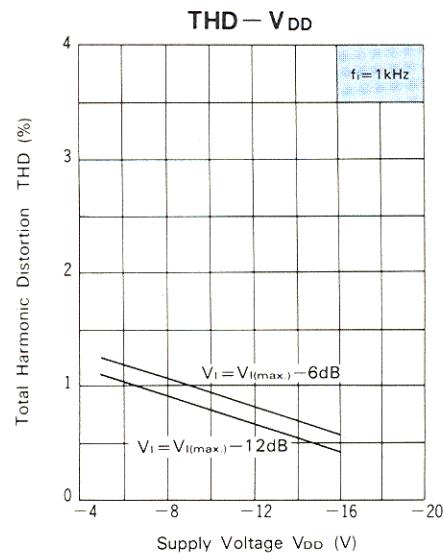
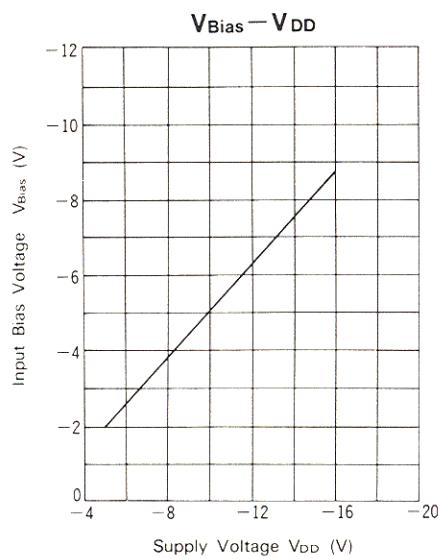
Item	Symbol	Condition	Min.	Typ.	Max.	Unit
Signal Delay Time	t _D		0.64		12.8	msec
Input Signal Frequency	f _i	f _{CP} =40kHz, V _i =1.8VRms 3dB down (0dB at f _i =1kHz)			14	kHz
Input Signal Swing	V _i	f _{CP} =40kHz, f _i =1kHz, THD=2.5%			1.7	VRms
Insertion Loss	L _i	f _{CP} =40kHz, f _i =1kHz, V _i =1.8VRms	0			dB
Total Harmonic Distortion	THD	f _{CP} =40kHz, f _i =1kHz, V _i =0.78VRms	0.3			%
Noise	V _{no}	f _{CP} =100kHz Weighted by "A" curve			150	μVRms
Signal to Noise Ratio	S/N	Maximum output voltage to noise voltage	88			dB

Terminal Assignments**Clock Pulse Waveforms****Circuit Diagram**

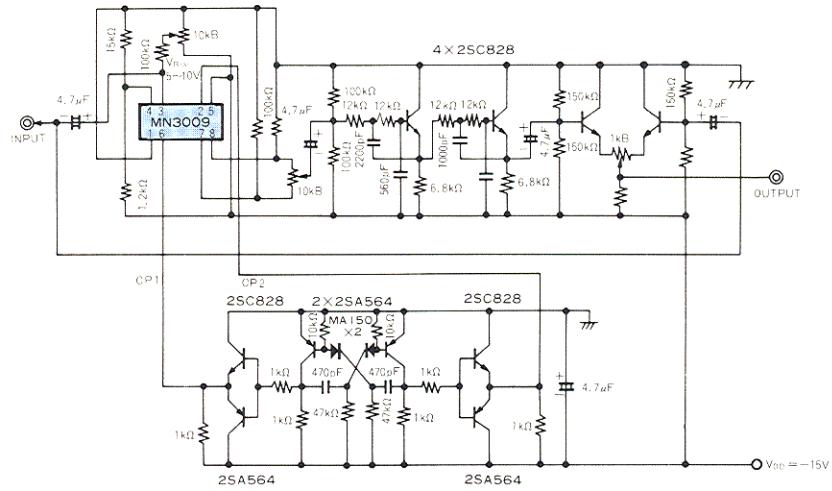
Typical Electrical Characteristic Curves



Supply Voltage Characteristics



Application Circuit



Chorus Effect Generation Circuit

DUAL 512-STAGE LOW NOISE BBD

General Description

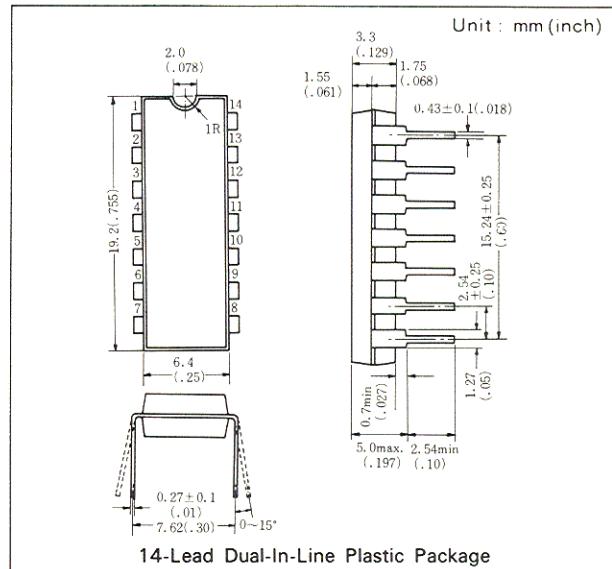
The MN3010 is a dual 512-stage low noise BBD having a wide dynamic range and low distortion characteristics. The device contains two identical BBD's on a single chip with independent input, output and clock terminals as well as common power supply terminals. Each 512-stage BBD provides a signal delay of up to 25.6msec. The two identical BBD's on a same chip offer uniform characteristics and space saving advantage when they are used in parallel or series connection.

Features:

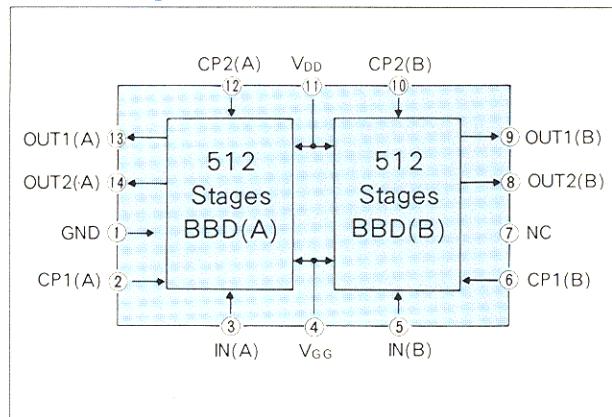
- Wide range of variable delay time:
2.56~25.6msec. (512-stage)
5.12~51.2msec. (512×2-stage)
- Clock component cancellation capability.
- No insertion loss: $L_i \approx 0$ dB typ.
- Wide dynamic range: $S/N \approx 85$ dB typ.
- Wide frequency response: $f_i < 12$ kHz.
- Total harmonic distortion: THD=0.4% typ. ($V_i=0.78$ Vrms)
- Clock frequency range: 10~100kHz.
- Dual 512-stage configuration: 1024-stage in series connection, and twice as large output in parallel connection.
- P-channel silicon gate, tetrode MOS transistors configuration.
- 14-lead dual-in-line package.

Applications:

- Vibrato and/or chorus effects in electronic organs and musical instruments.
- Reverberation effect of electronic musical instruments.
- Variable or fixed delay of analog signals.



Block Diagram



Quick Reference Data

Item	Symbol	Value	Unit
Supply Voltage	V_{DD} V_{GG}	-15, $V_{DD}+1$	V
Signal Delay Time	t_D	2.56~51.2	msec
Total Harmonic Distortion	THD	0.4	%
Signal to Noise Ratio	S/N	85	dB

Absolute Maximum Ratings (Ta=25°C)

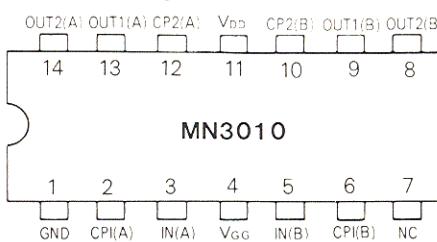
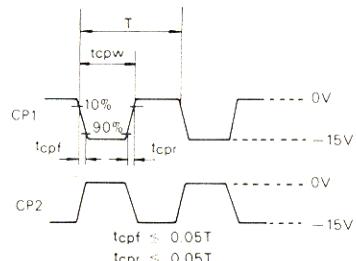
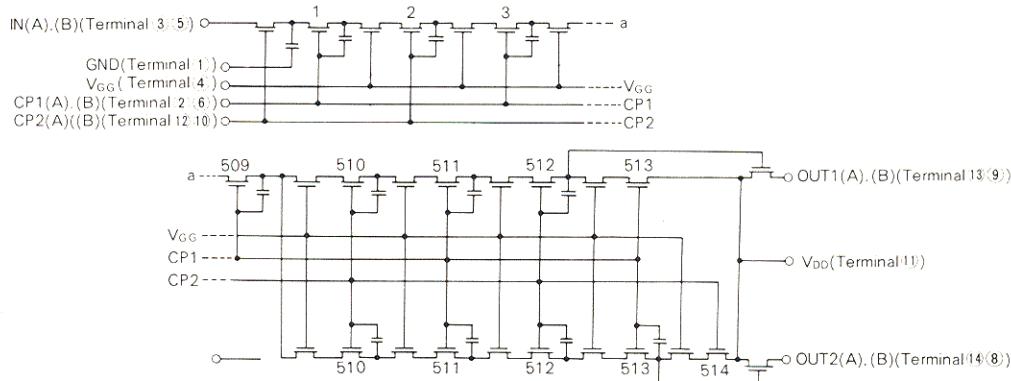
Item	Symbol	Ratings	Unit
Terminal Voltage	V _{DD} , V _{GG} , V _{CP} , V _I	-18 ~ +0.3	V
Output Voltage	V _O	-18 ~ +0.3	V
Operating Temperature	T _{OPR}	-20 ~ +60	°C
Storage Temperature	T _{STG}	-55 ~ +125	°C

Operating Conditions (Ta=25°C)

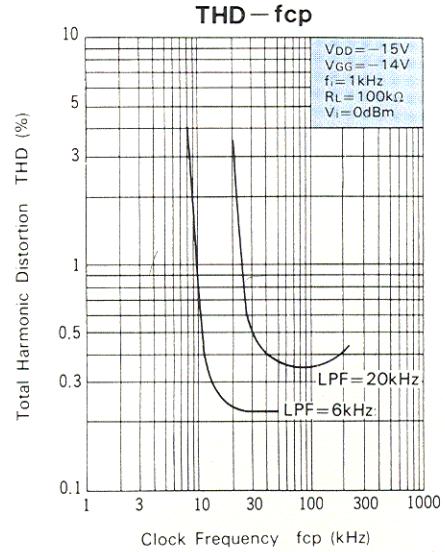
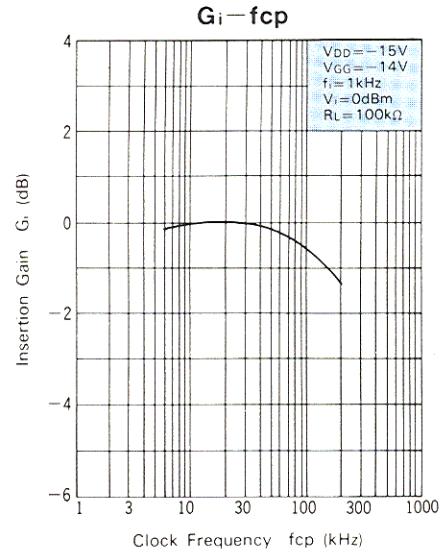
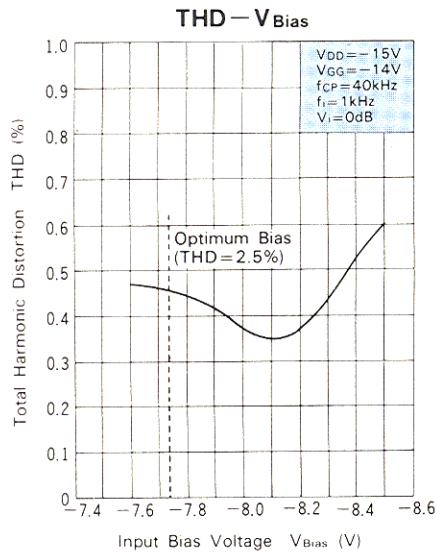
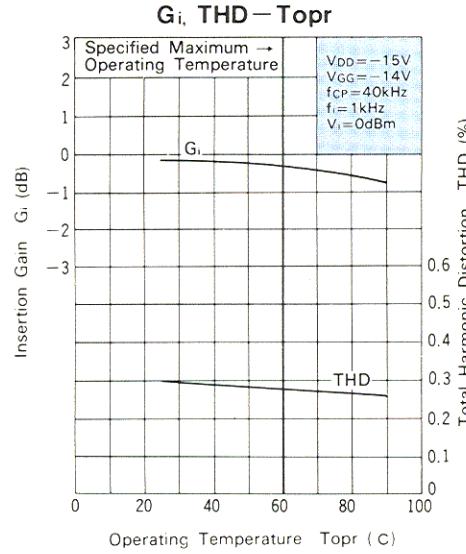
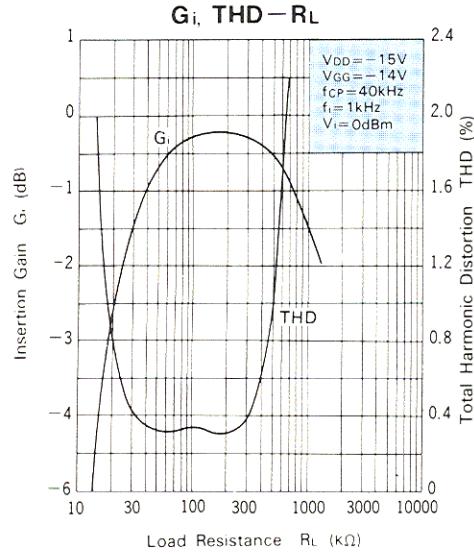
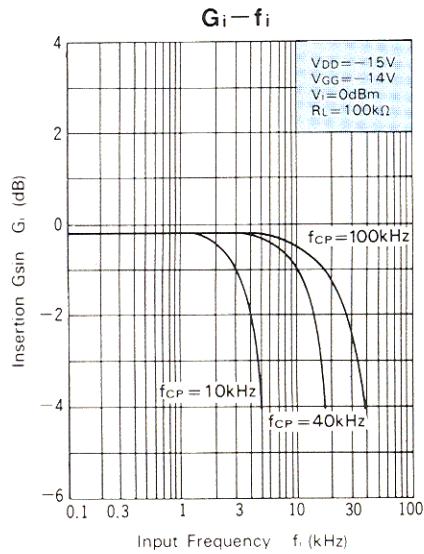
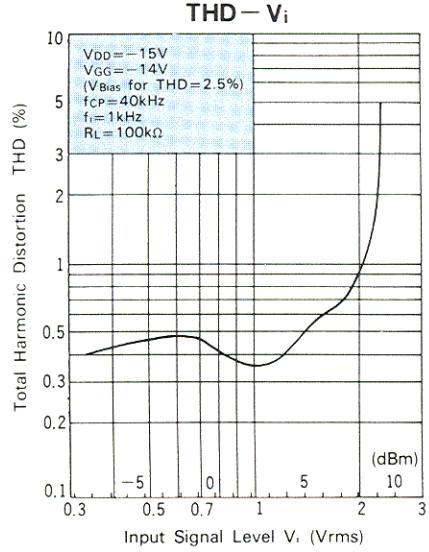
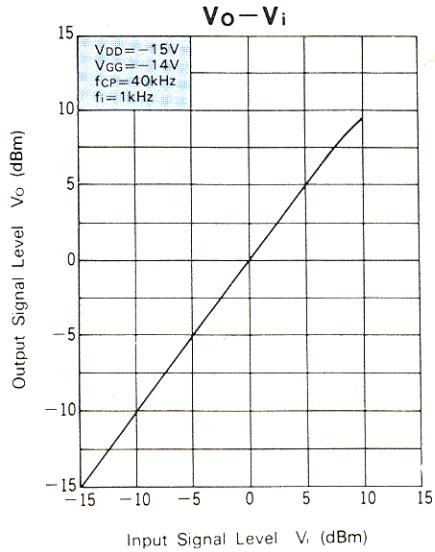
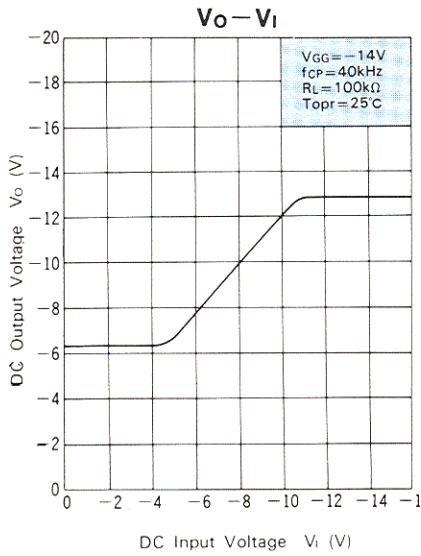
Item	Symbol	Min.	Typ.	Max.	Unit
Drain Supply Voltage	V _{DD}	-14	-15	-16	V
Gate Supply Voltage	V _{GG}		V _{DD} +1		V
Clock Voltage "H" Level	V _{CPH}	0		-1	V
Clock Voltage "L" Level	V _{CPL}		V _{DD}		V
Clock Input Capacitance	C _{CP}			350	pF
Clock Frequency	f _{CP}	10		100	kHz
Clock Pulse Width *2	t _{CPW}			0.5T *1	
Clock Rise Time *2	t _{CPR}			500	nsec
Clock Fall Time *2	t _{CPF}			500	nsec
Clock Cross Point	V _X	0		-3	V

*1 T=1/f_{CP} *2 Clock Pulse Waveforms**Electrical Characteristics (Ta=25°C, V_{DD}=V_{CPL}=-15V, V_{CPH}=0V, V_{GG}=-14V, R_L=100kΩ)**

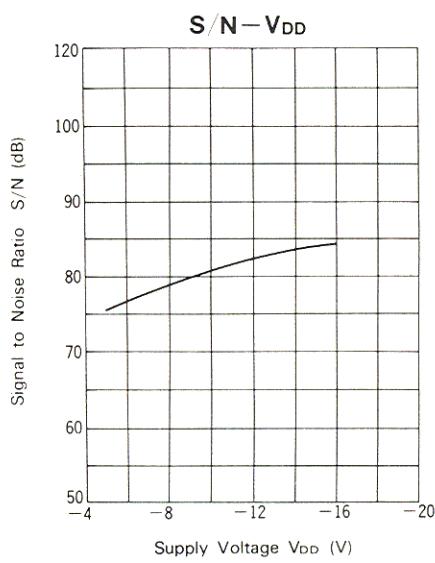
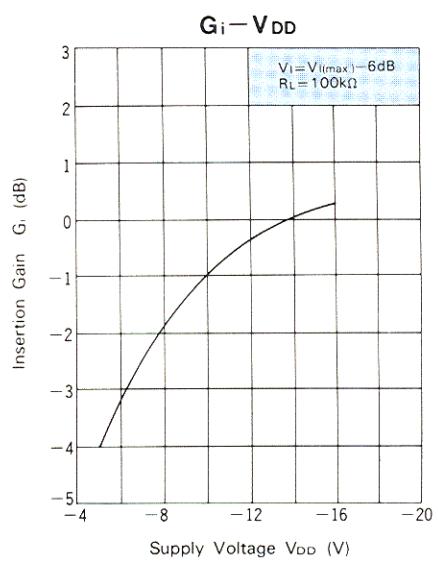
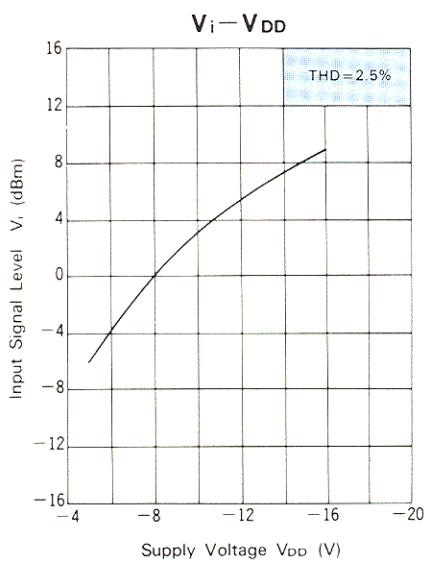
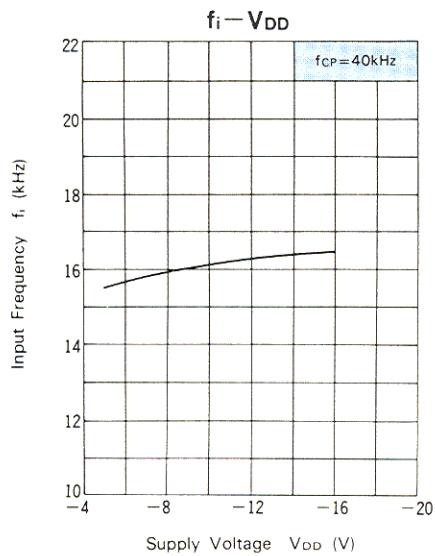
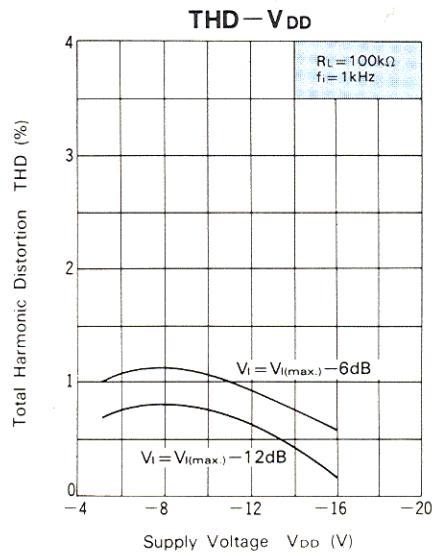
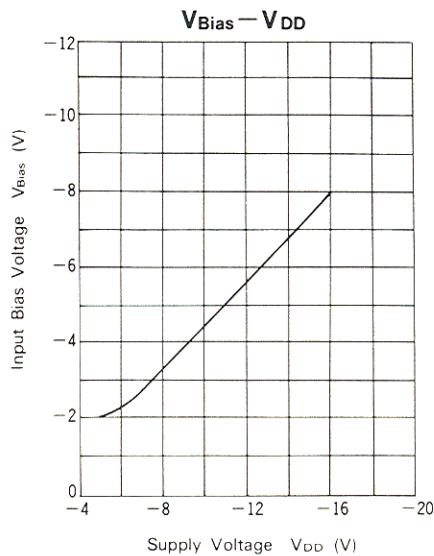
Item	Symbol	Condition	Min.	Typ.	Max.	Unit
Signal Delay Time	t _D		2.56		25.6	msec
Input Signal Frequency	f _I	f _{CP} =40kHz, V _I =1.8Vrms, 3dB down (0dB at f _I =1kHz)			12	kHz
Input Signal Swing	V _I	f _{CP} =40kHz, f _I =1kHz, THD=2.5%			1.8	Vrms
Insertion Loss	L _I	f _{CP} =40kHz, f _I =1kHz, V _I =1.8Vrms	-	0		dB
Total Harmonic Distortion	THD	f _{CP} =40kHz, f _I =1kHz, V _I =0.78Vrms		0.4		%
Noise Voltage	V _{NO}	f _{CP} =100kHz Weighted by "A" curve			0.21	mVrms
Signal to Noise Ratio	S/N	Maximum output voltage to noise voltage		85		dB

Terminal Assignments**Clock Pulse Waveforms****Circuit Diagram**

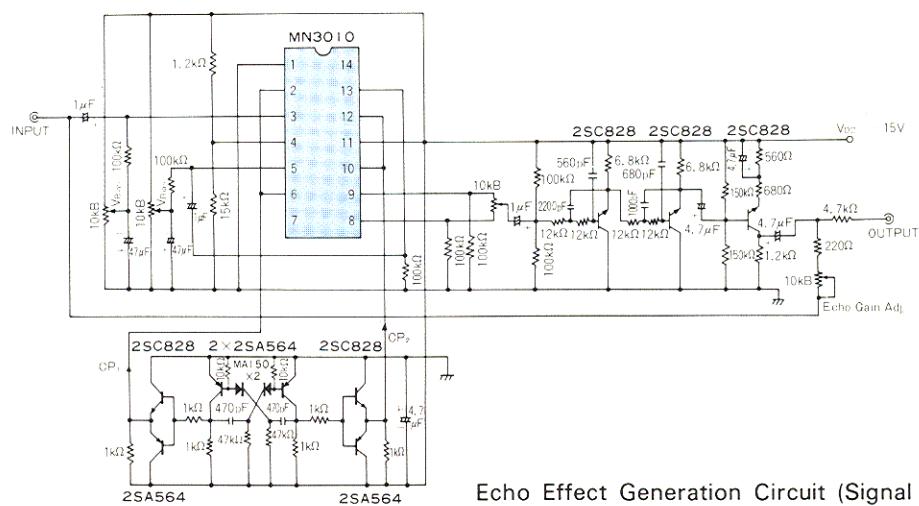
Typical Electrical Characteristic Curves



Supply Voltage Characteristics



Application Circuit



Echo Effect Generation Circuit (Signal Delay Over 10msec.)

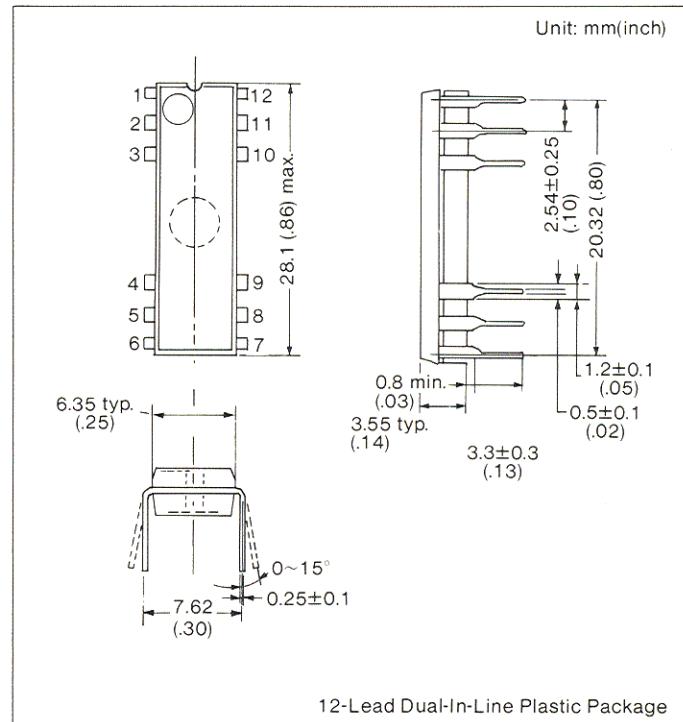
3328 - Stage Multi-Tap BBD (MN3011) for Audio Signal Delays

General Description

The MN3011 is a 3328-stage low noise BBD (Bucket Brigade Device) designed to provide simultaneously six different delay outputs with respect to a signal input. A proper mixing of the six differently delayed signals generates highly effective reverberation. The delay times can be varied by the clock frequency control.

Features

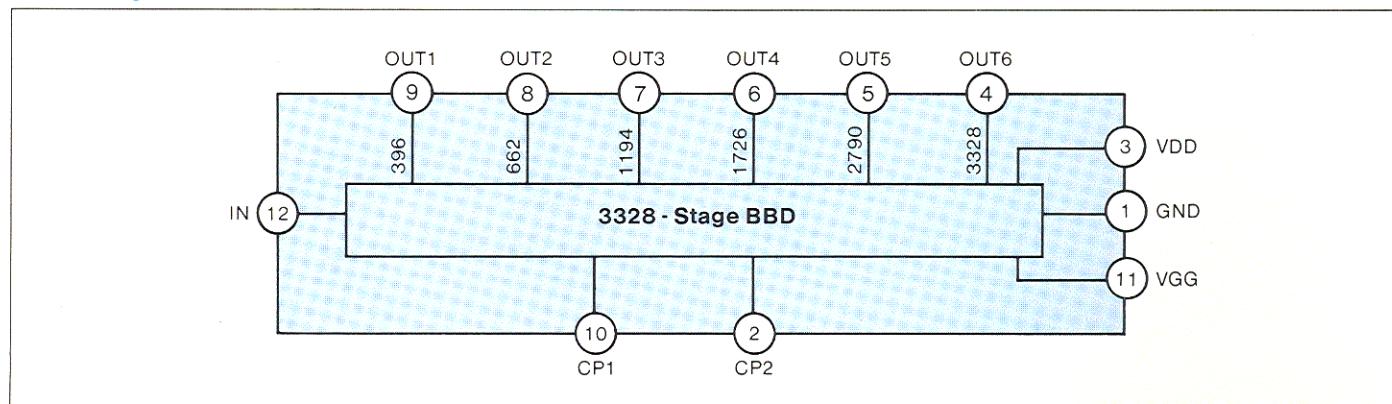
- 3328-stage with 6 different output stages
- 6 stages not in multiple proportion with each other so that a proper mixing of the six differently delayed output signals generates a highly effective reverberation.
- Clock component cancellation capability.
- Wide dynamic range: S/N \geq 76 dB typ.
- No insertion loss: Li = 0 dB typ.
- Total harmonic distortion: THD = 0.4% typ.
- P-channel silicon gate, tetrode MOS transistors configuration



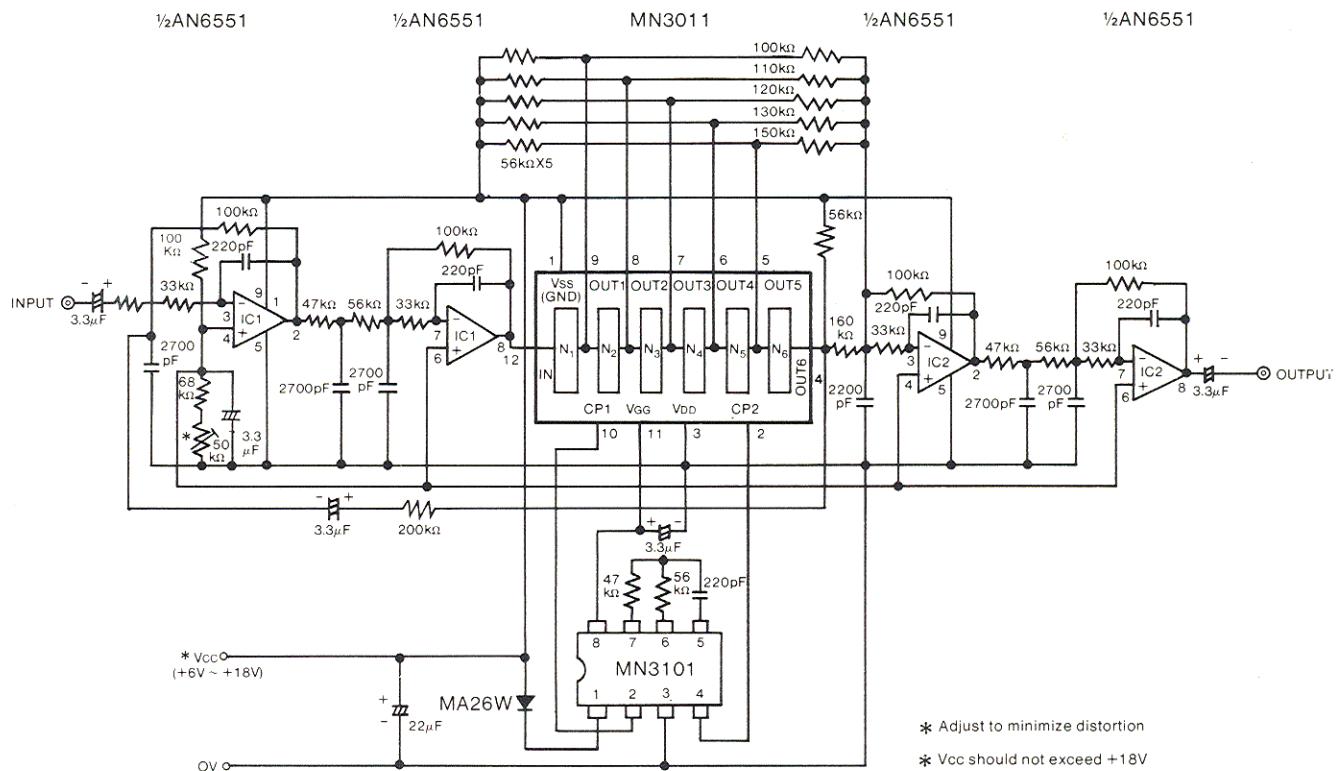
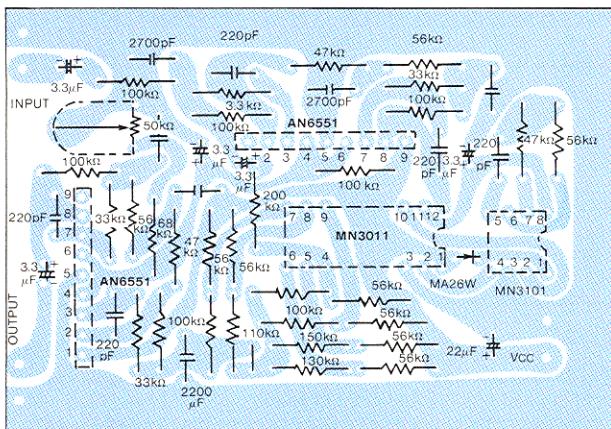
Maximum Delay Times for 6 Different Output Stages

Tapped Output Terminals	OUT1	OUT2	OUT3	OUT4	OUT5	OUT6	Remark
BBD stages (stages)	396	662	1194	1726	2790	3328	
Maximum Delay Time (msec.)	19.8	33.1	59.7	86.3	139.5	166.4	Clock 10KHz

Block Diagram



Application Circuit – Reverberation Effect Generation Circuit

Printed Circuit Board Layout
(Actual Size)Electrical Characteristics of The Application Circuit
(Vcc = +15V, Ta = 25°C)

Item	Symbol	Condition	min.	typ.	max.	Unit
Supply Current	Icc			11(8)	15(10)	mA
Total Power Dissipation	Ptot			165 (70)		mW
Signal Delay Time	tD	OUT6: $f_{CP} = 15 \sim 20\text{kHz}$	83	98	111	msec
Cutoff Frequency	f _{CO}			3		kHz
Input Signal Swing	V _i	THD = 2.5%			1.1(0.5)	Vrms
Insertion Loss	L _i	OUT3: f _i = 1kHz V _i = 300mV	0	2	4	dB
Total Harmonic Distortion	THD	f _i = 1kHz V _i (max) - 6dB		0.4 (0.5)		%
Output Noise Voltage	Vno	OUT3: V _i = 0V		0.4 (0.4)		mVrms
Signal to Noise Ratio	S/N	V _s = V _i (max)		70 (60)		dB

Note: Values in parenthesis for Vcc = +9V.

Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Terminal Voltage	V _{DD} , V _{GG} , V _{CP} , V _I	-18~+0.3	V
Output Voltage	V _O	-18~+0.3	V
Operating Temperature	T _{opr}	-20~+70	°C
Storage Temperature	T _{stg}	-55~+125	°C

Note: All voltages with respect to GND = 0V.

Operating Conditions (Ta = 25°C)

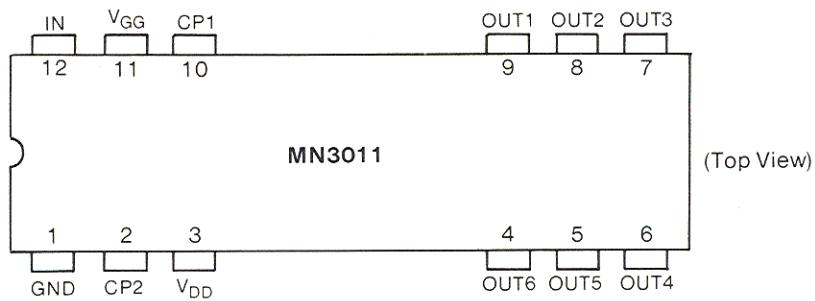
Item	Symbol	Min.	Typ.	Max.	Unit
Drain Supply Voltage	V _{DD}	-14	-15	-16	V
Gate Supply Voltage	V _{GG}		V _{DD} + 1		V
Clock Voltage "H" Level	V _{CPH}	0		-1.3	V
Clock Voltage "L" Level	V _{CPL}		V _{DD}		V
Clock Input Capacitance	C _{CP}			2300	pF
Clock Frequency	f _{cp}	10		100	kHz
Clock Pulse Width	t _{cpw}			0.5T*	
Clock Rise Time	t _{cpri}			500	nsec
Clock Fall Time	t _{cpf}			500	nsec

*T = 1/f_{cp}

Electrical Characteristics (Ta = 25°C, V_{DD} = V_{CPL} = -15V, V_{CPH} = 0V, V_{GG} = -14V, R_L = 56KΩ)

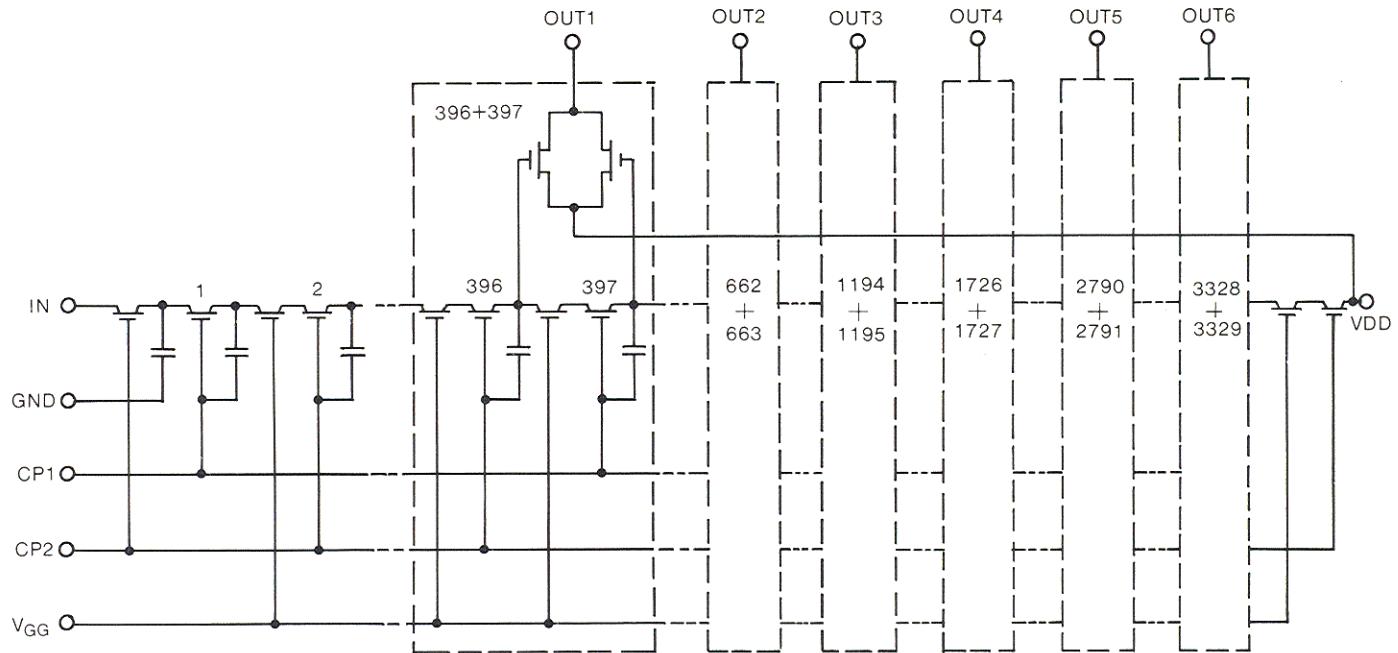
Item	Symbol	Condition	Min.	Typ.	Max.	Unit
Signal Delay Time						
Terminal OUT1	tD1	f _{cp} = 10kHz~100kHz	1.98		19.8	msec
Terminal OUT2	tD2		3.31		33.1	msec
Terminal OUT3	tD3		5.97		59.7	msec
Terminal OUT4	tD4		8.63		86.3	msec
Terminal OUT5	tD5		13.95		139.5	msec
Terminal OUT6	tD6		16.64		166.4	msec
Input Signal Frequency	f _i	f _{cp} = 40kHz ~ 3dB			11	kHz
Input Signal Swing	V _i	THD = 2.5%			1.1	Vrms
Insertion Loss	L _i	f _{cp} = 40kHz, f _i = 1kHz,		0		dB
Total Harmonic Distortion	THD	f _{cp} = 40kHz. f _i = 1kHz. V _i = 0.78Vrms		0.4		%
Noise Level						
OUT1, OUT2, OUT3	V _{no1}	f _{cp} = 100kHz Weighted by "A" curve			270	µVrms
OUT4, OUT5, OUT6	V _{no2}				400	µVrms
Signal to Noise Ratio						
OUT1, OUT2, OUT3	S/N1	f _{cp} = 100kHz Weighted by "A" curve		80		dB
OUT4, OUT5, OUT6	S/N2			76		dB

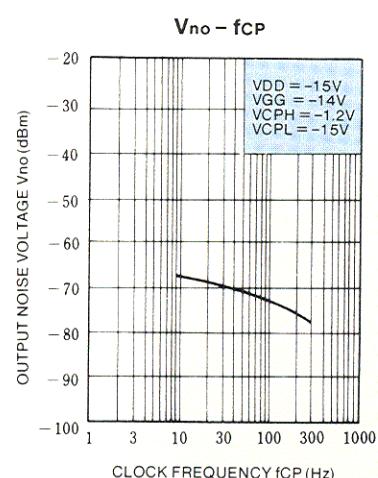
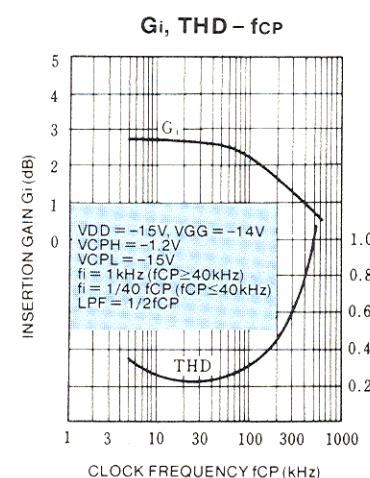
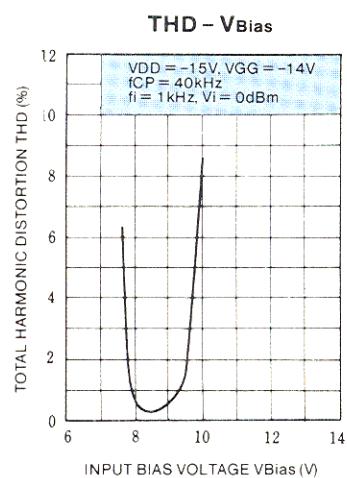
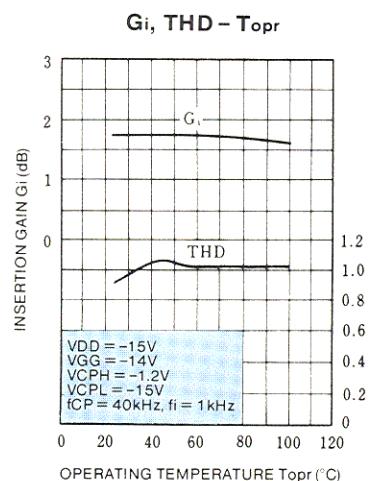
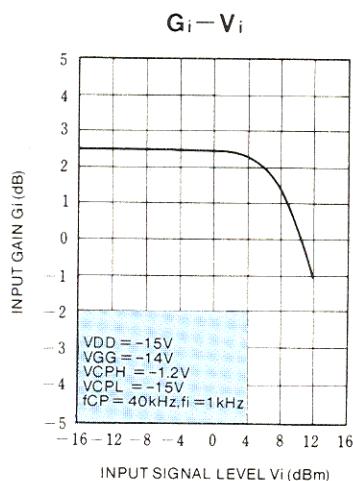
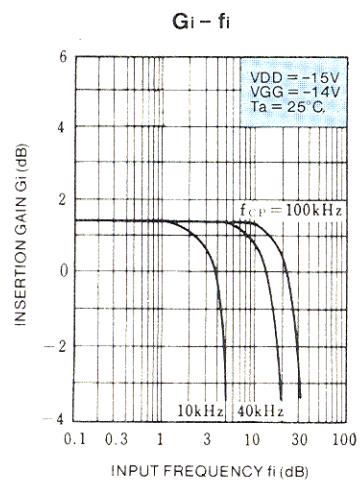
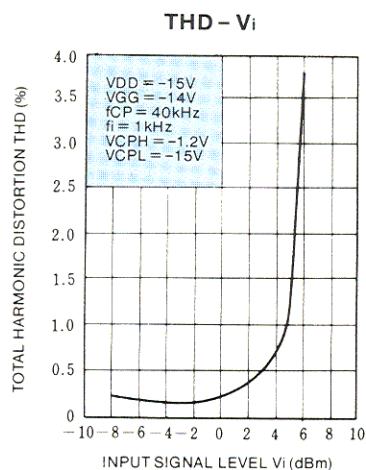
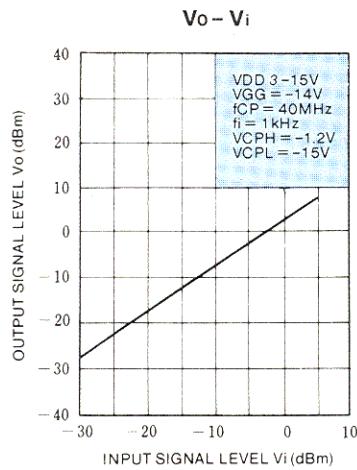
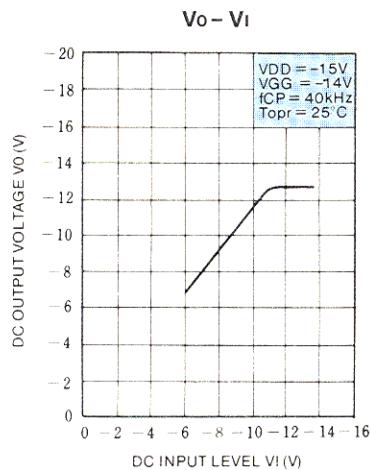
Terminal Assignments

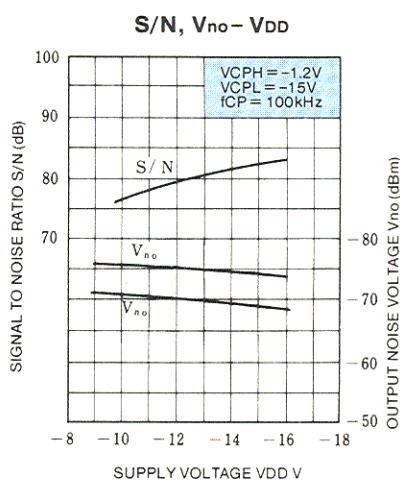
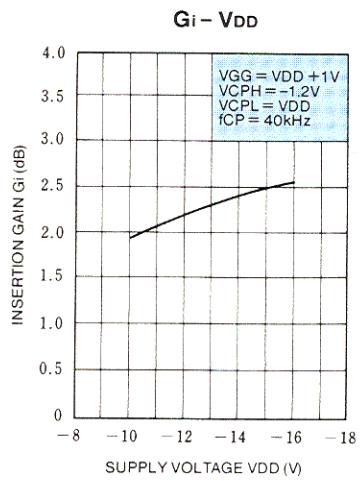
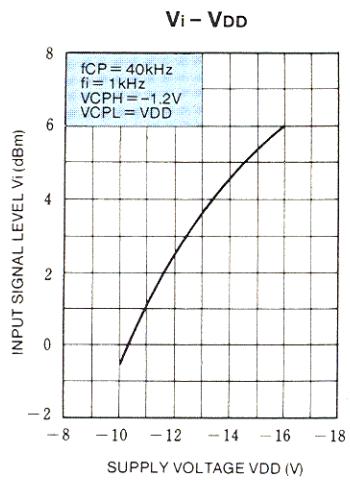
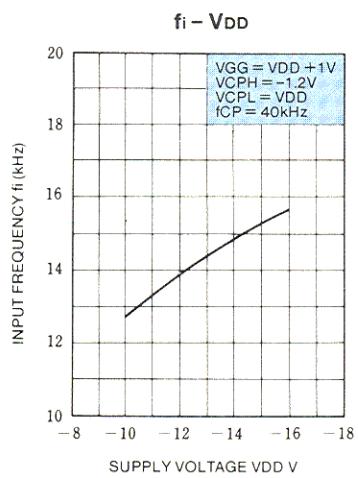
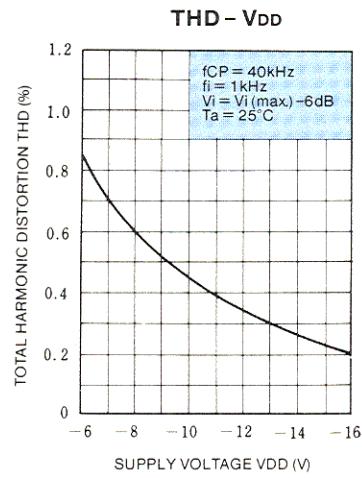
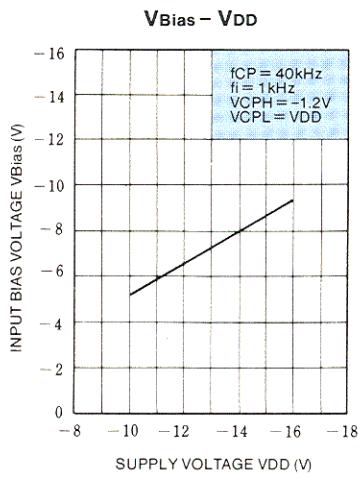


Pin No.	Symbol	Terminal	Functions
1	GND	Grounding	Ground connection
2	CP2	Clock Input 2	Fundamental clock pulse input for charge transfer
3	V _{DD}	V _{DD} Supply	-15V supply
4	OUT6	Output 6	3328th and 3329th stage synthetic output with clock component cancellation
5	OUT5	Output 5	2790th and 2791st stage synthetic output
6	OUT4	Output 4	1726th and 1727th stage synthetic output
7	OUT3	Output 3	1194th and 1195th stage synthetic output
8	OUT2	Output 2	662nd and 663rd stage synthetic output
9	OUT1	Output 1	396th and 397th stage synthetic output
10	CP1	Clock Input 1	Fundamental clock pulse input, inverted with respect to CP2
11	V _{GG}	V _{DD} Supply	V _{GG} bias supply input to each MOS transistor gate connected in series with BBD transfer gates V _{GG} = V _{DD} + 1
12	IN	Signal Input	Analog signal input The optimum DC bias must be applied to this terminal

Circuit Diagram







MN3012

BBD With 3 Parallel Signal Delay Lines Incorporating Clock Generator

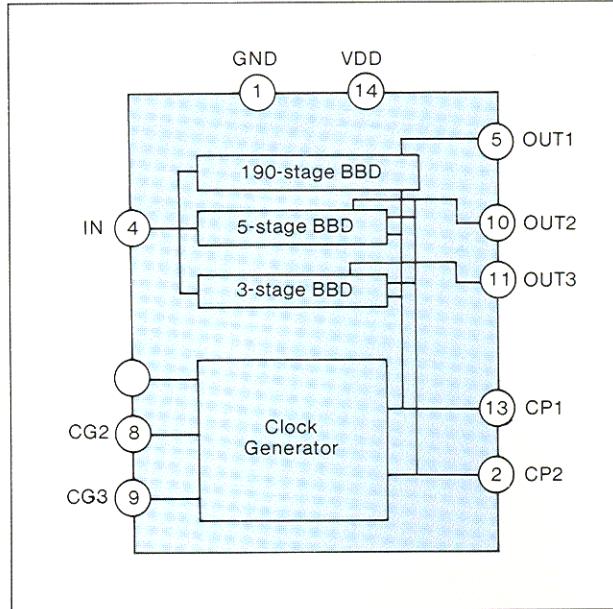
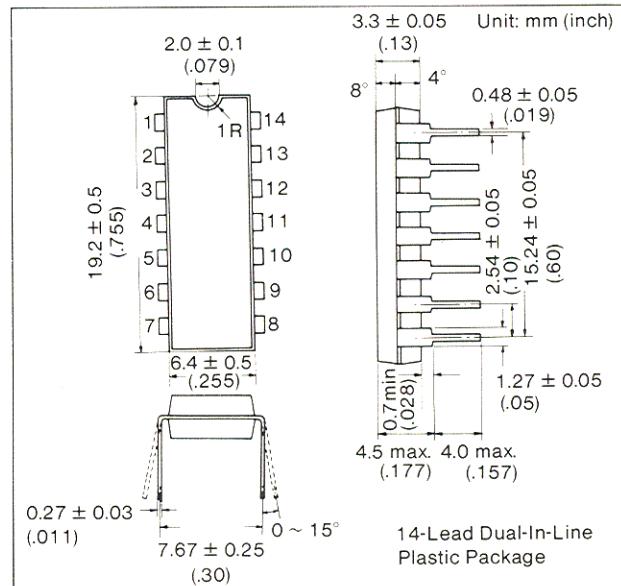
General Description

The MN3012 is BBD provided with 3, 5, 190 stages three parallel delay lines and a clock generator. The clock frequency which determines a delay time is controlled by the value of external resistor and capacitor connected to CG1, CG2 and CG3 terminals.

The MN3012 provides three differently delayed signals on OUT1, OUT2 and OUT3 terminals. The device is particularly suitable for producing chorus, vibrato and reverberation effects of audio equipment.

Features:

1. -8.5 ~15V single voltage supply (VDD)
2. Delay time 01 : 0.475 ~ 9.5ms (190-stage)
02 : 0.0125~0.25 (5-stage)
03 : 0.0075~0.15 (3-stage)
3. Dynamic range S/N = 98dB typ. (OUT3)
4. Insertion IL = 0 dB typ.
5. Distortion THD = 0.4% typ.
6. Incorporating clock generator
7. Clock frequency 10~200KHz
8. Clock component cancellation
9. P-channel silicon gate process.



Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Terminal Voltage	VDD, VI, VO, VCP	-18~+0.3	V
Operating Temperature	TOPR	-20~+70	°C
Storage Temperature	TSTG	-56~+125	°C

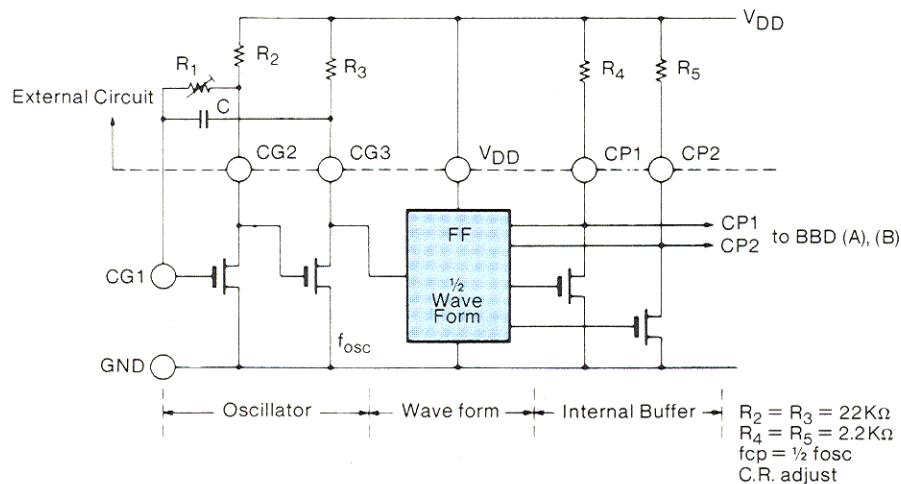
Operating Conditions (Ta = 25C)

Item	Symbol	Min.	Typ.	Max.	Unit
Supply Voltage	VDD	-6.5	-15	-16	V
Clock H Level	VCPH	0		-0.4	V
Clock L Level	VCPL		VDD		V
Clock Frequency	fcp	10		200	KHz
Clock Input Capacitance	Ccp			180	pF
Input DC Bias	Vbias				V

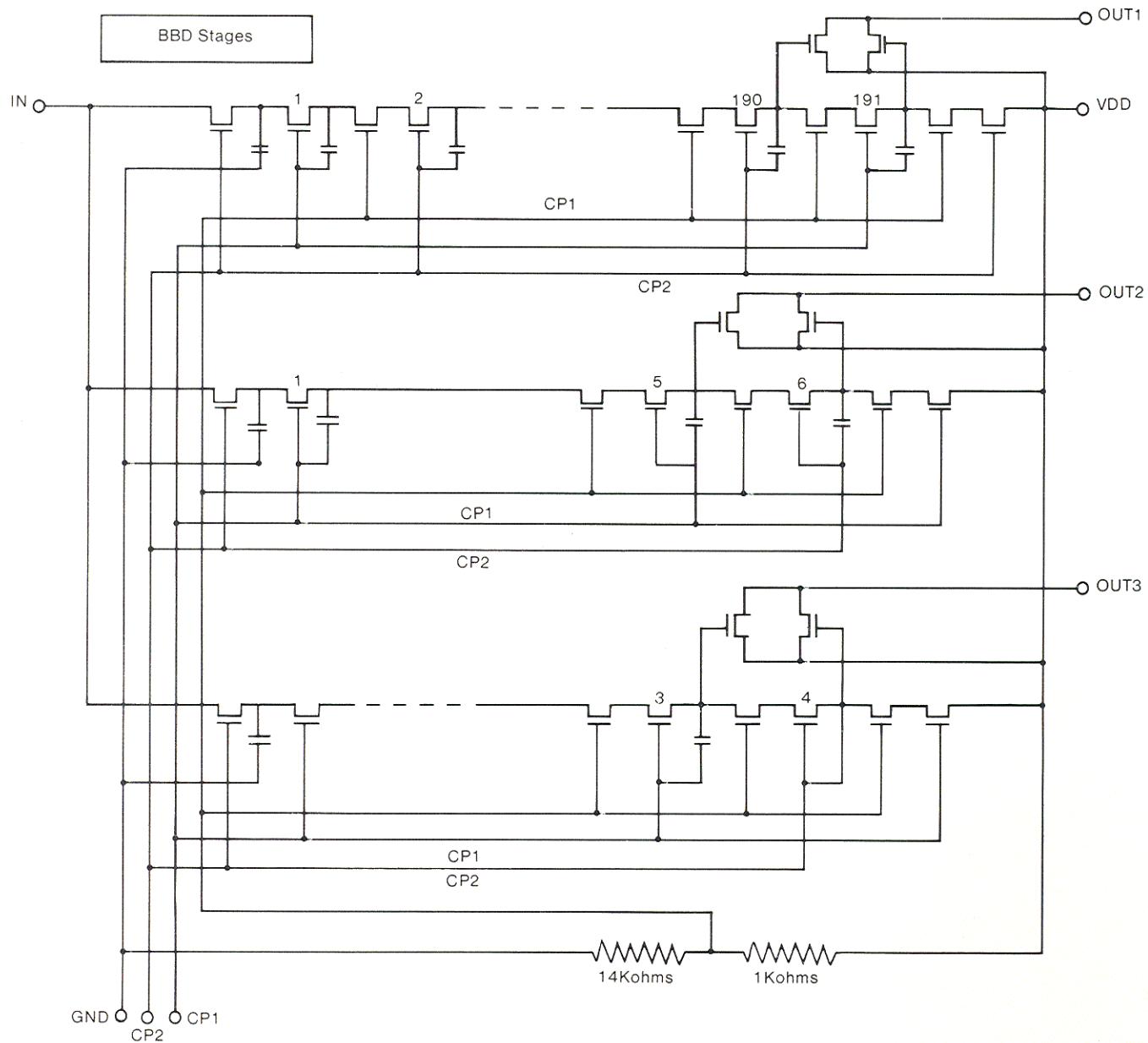
**Characteristics (Ta = 25°C, VDD = -15V, VCPL = -15V, VCPH = OV, RL = 56Kohms, C = 100pF
R1 = R3 = 22 Mohms, R4 = R5 = 2.2Kohms, fcp = 1/2 fosc (R1 adjust))**

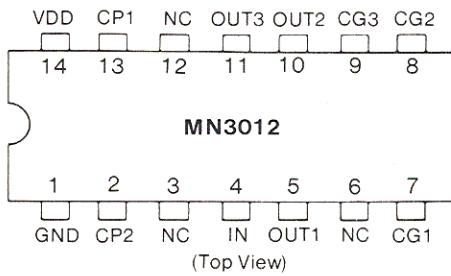
Item	Symbol	Condition	Min.	Typ.	Max.	Unit
Signal Delay Time OUT1 Terminal OUT2 Terminal OUT3 Terminal	tD1 tD2 tD3	fcp = 10KHz 200Khz	0.475 0.0125 0.0075		9.5 0.125 0.15	ms ms ms
Input Signal Frequency OUT Terminal 1 OUT Terminal 2 OUT Terminal 3	fin1 fin2 fin3	fcp = 40KHz Output -3dB			12 14 15	KHz KHz KHz
Input Signal Voltage	vin	THD = 2.5%			1.2	Vrms
Insertion Loss	IL	fcp = 40KHz fin = 1KHz vin = 0.775 Vrms		0		dB
Distortion	THD			0.4		%
Noise Voltage OUT Terminal 1 OUT Terminal 2 OUT Terminal 3	Vn1 Vn2 Vn3	fcp = 100KHz Weighted by A curve			0.14 0.05 0.04	mVrms mVrms mVrms
S/M Ratio OUT Terminal 1 OUT Terminal 2 OUT Terminal 3	S/N1 S/N2 S/N3	Vn/Vin fcp = 100KHz Weighted by A curve		90 97 98		dB dB dB

Circuit Diagram
Clock Generator



Note: When external clock is used, remove R1 and C, apply the clock input to CG1.

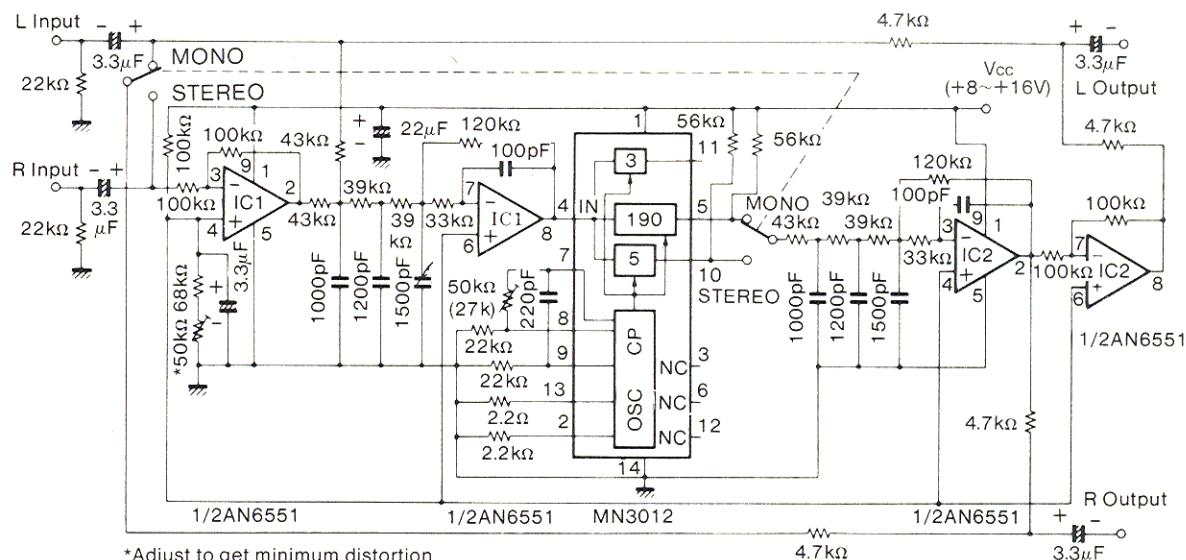


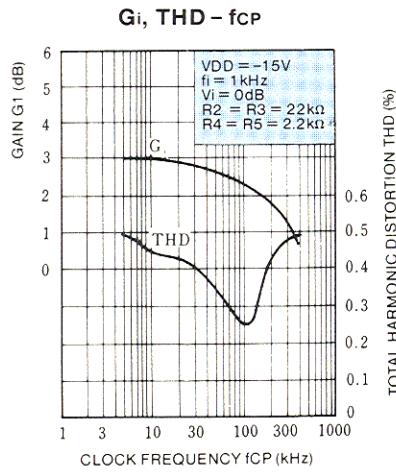
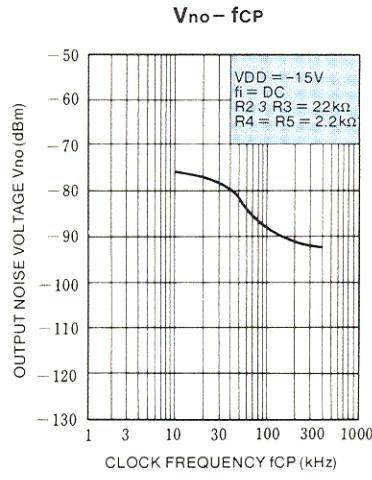
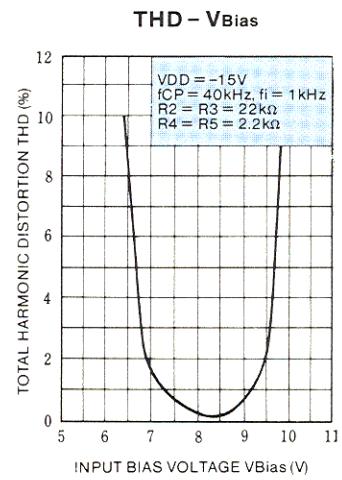
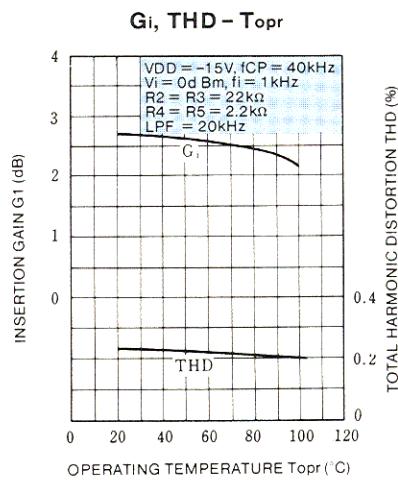
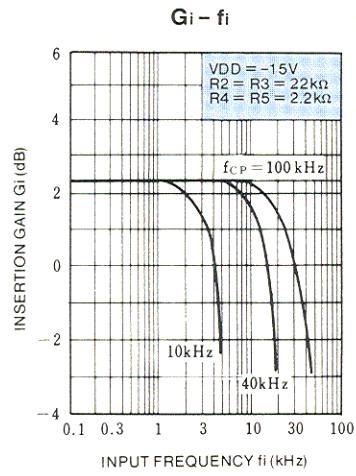
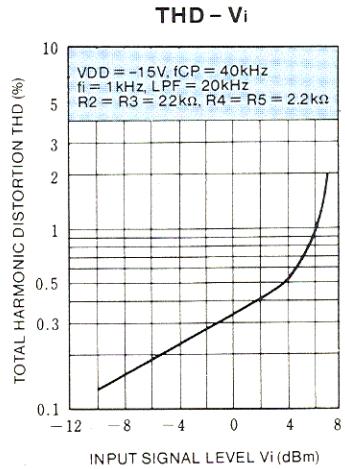
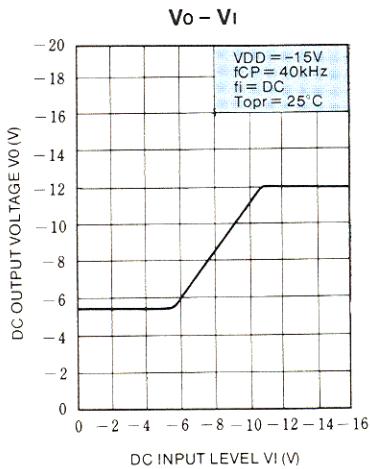


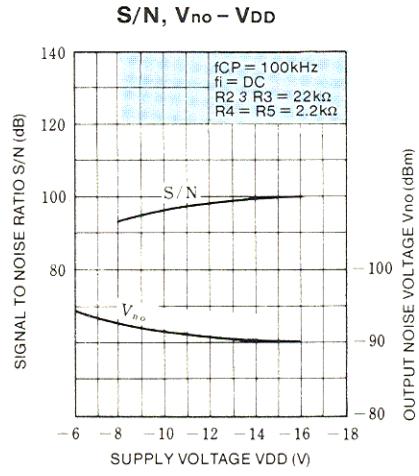
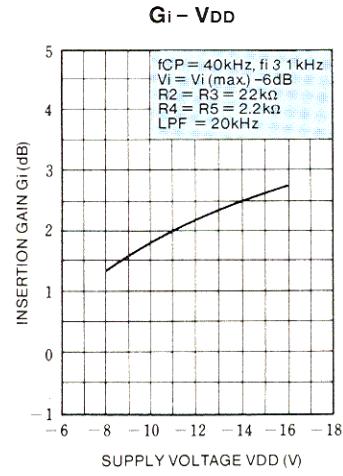
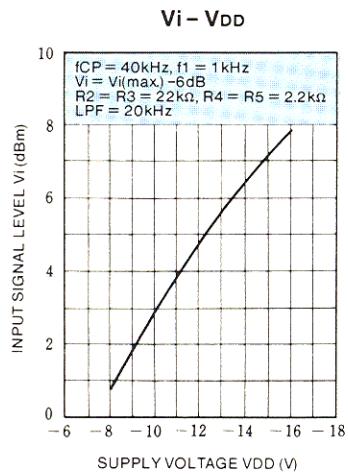
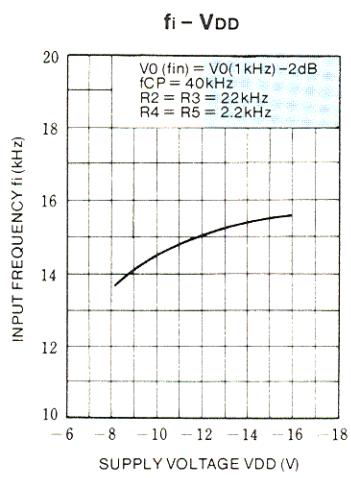
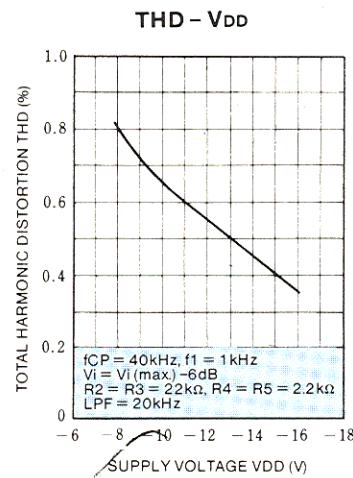
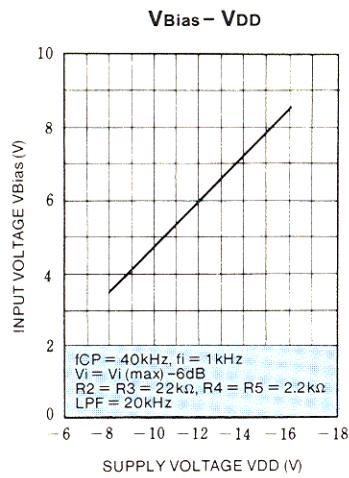
Terminal Assignments

Pin No.	Symbol	Terminal
1	GND	Grounding
2	CP2	Clock pulse input
4	IN	Analog signal input
5	OUT1	Output terminal at 190 and 191-stage
7	CG1	Clock oscillation input
8	CG2	Clock oscillation input
9	CG3	Clock oscillation input
10	OUT2	Output terminal at 5 and 6-stage
11	OUT3	Output terminal at 3 and 4-stage
13	CP1	Clock pulse input
14	VDD	VDD = -15V supply terminal

Note: Terminal No. 3, 6, and 12 are non connection







Clock Generator / Driver MN 3101 for BBD's

General Description

The MN3101 is a CMOS integrated circuit designed to generate low impedance two clock phases required for driving BBD's. In addition, the MN3101 provides the optimum V_{GG} for BBD's* when the MN3101 is used with BBD's on a common V_{DD} supply.

The self-contained oscillator can be controlled by an external RC circuit, but an external oscillator can also be used. The clock frequency is 1/2 of the oscillation frequency.

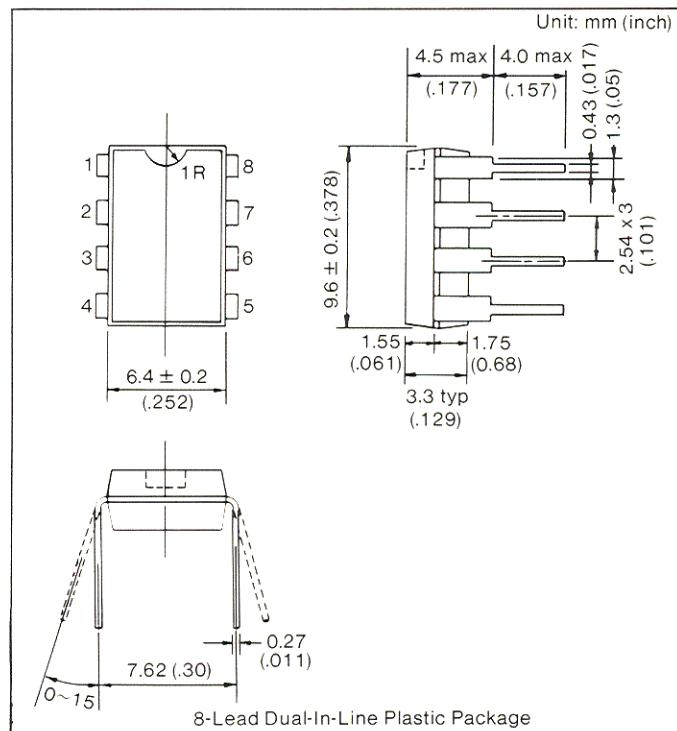
*PANASONIC's BBD product range: MN3001, MN3002, MN3003, MN3004, MN3005, MN3006, MN3007, MN3008, MN3009, MN3010, MN3011, MN3012. Note: The MN3003 is provided with an internal oscillator.

Features:

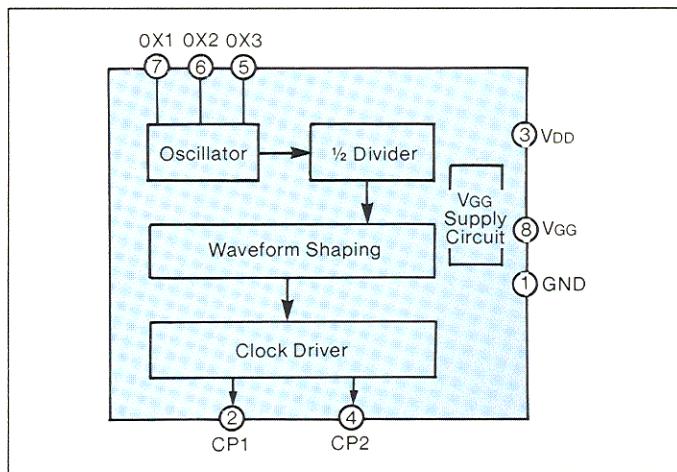
- BBD direct driving capability – up to two MN3005 types (equivalent to 8192 stages).
- Either internal or external oscillator can be used
- Two phases (1/2 duty) output
- Provided with V_{GG} supply circuit
- Operates on a single power supply: –8 ~ –16V
- 8-lead dual-in-line plastic package

Application

- BBD clock generator/driver



Block Diagram



Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Supply Voltage	VDD	-18~+0.3 *	V
Input Terminal Voltage	VI	VDD-0.3~+0.3 *	V
Output Terminal Voltage	VO	VDD - 0.3~+0.3 *	V
Power Dissipation	PD	200	mW
Operating Temperature	Topr	-10~+70	°C
Storage Temperature	Tstg	-30~+125	°C

*With respect to GND = OV.

Operating Conditions

Item	Symbol	Condition	Min.	Typ.	Max.	Unit
Supply Voltage	VDD	GND = OV	-8	-15	-16	V

Electrical Characteristics (Ta = 25°C, VDD = -15V, GND = OV)

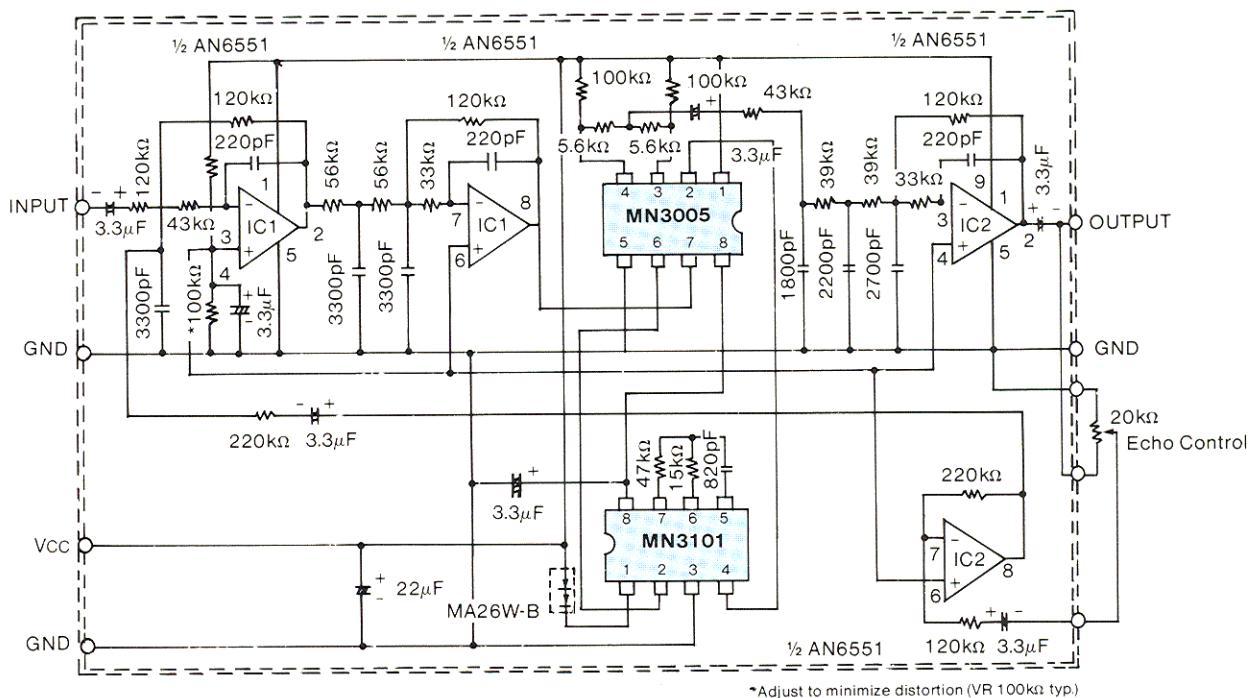
Item	Symbol	Condition	Min.	Typ.	Max.	Unit
Supply Current	I _{DD}	Without load Clock output 40kHz		3		mA
Power Consumption	P _{tot}			45		mW
OX1 Input Terminal						
Input Voltage "H" Level	V _{IH}		0		-1	V
Input Voltage "L" Level	V _{IL}		V _{DD} +1		V _{DD}	V
Input Leakage Current	I _{LK}	V _I = 0~-15V			30	μA
OX2 Output Terminal						
Output Current "H" Level	I _{OH1}	V _O = -1.0V	0.6			mA
Output Current "L" Level	I _{OL1}	V _O = -14V	0.5			mA
Output Leakage Current	I _{OL1}	V _O = V _{DD}			30	μA
Output Leakage Current	I _{LOH1}	V _O = GND			30	μA
OX3 Output Terminal						
Output Current "H" Level	I _{OH2}	V _O = -1.0V	1.5			mA
Output Current "L" Level	I _{OL2}	V _O = -14V	2.0			mA
Output Leakage Current	I _{OL2}	V _O = V _{DD}			30	μA
Output Leakage Current	I _{LOH2}	V _O = GND			30	μA
CP1, CP2 Output Terminal						
Output Current "H" Level	I _{OH3}	V _O = -1.0V	10			mA
Output Current "L" Level	I _{OL3}	V _O = -14V	10			mA
Output Leakage Current	I _{OL3}	V _O = V _{DD}			30	μA
Output Leakage Current	I _{LOH3}	V _O = GND			30	μA
VGG Output Terminal*						
Output Voltage	V _{GG OUT}			-14.0		V

*This terminal outputs VGG voltage particularly suitable for the BBD's manufactured by PANASONIC. The voltage is not necessarily suitable for the manufacturer's products.

The V_{GG OUT} changes depending on V_{DD}. The relationship between V_{GG OUT} and V_{DD} is as follows:

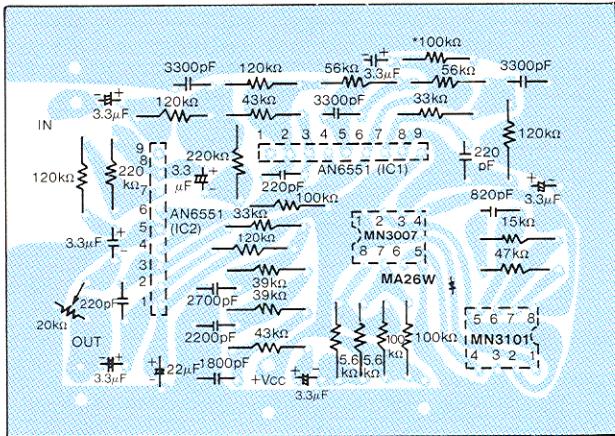
V_{GG OUT} = 14/15 V_{DD}

Application Circuit Example 1 – Echo Effect Generation Circuit With The MN3005



*Adjust to minimize distortion (VR 100kΩ typ.)

Printed Circuit Board Layout (Actual Size)



Quick Reference Data for The MN3005

Item	Symbol	Value	Unit
Supply Voltage	VDD, VGG	-15, VDD +1	V
Signal Delay Time	tD	20.48 ~ 204.8	msec.
Total Harmonic Distortion	THD	1	%
Signal to Noise Ratio	S/N	75	dB

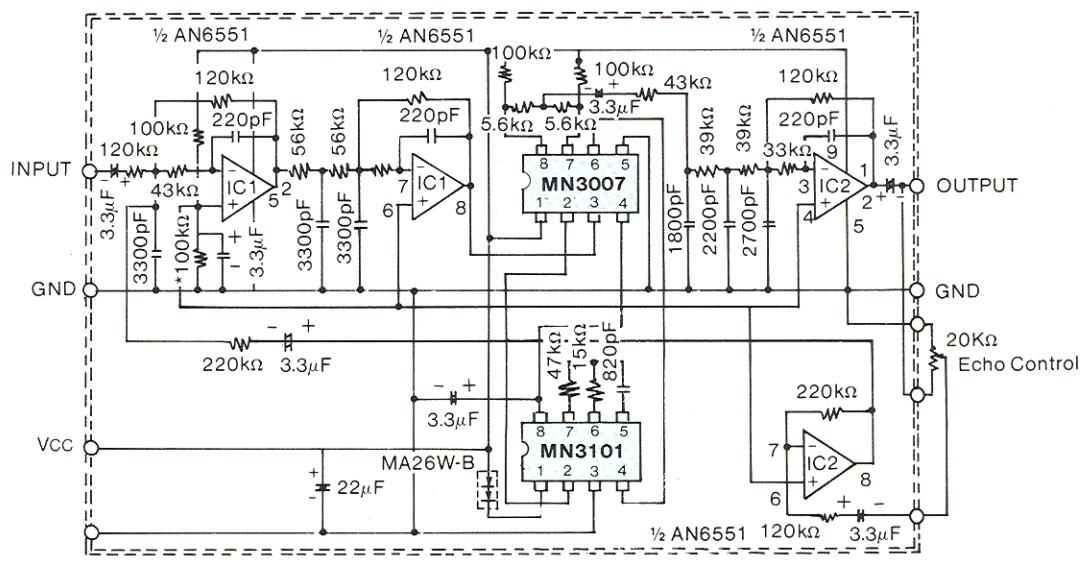
Quick Reference Data for the AN6551

Item	Symbol	Value	Unit
Supply Voltage	VCC	15	V
	VEE	-15	V
Input Bias Current	IB	500max.	nA
Voltage Gain	Gv	100typ.	dB
Noise Voltage Referred to Input	Vni	2.5typ.	µVrms
Maximum Output Voltage	Vo(max.)	±13typ.	V
Common-Mode Rejection Ratio	CMR	90typ.	dB
Supply Voltage Rejection	SVR	30typ.	µV/V

Electrical Characteristics of The Application Circuit Using The MN3005 (Vcc = 9V, Ta = 25°C)

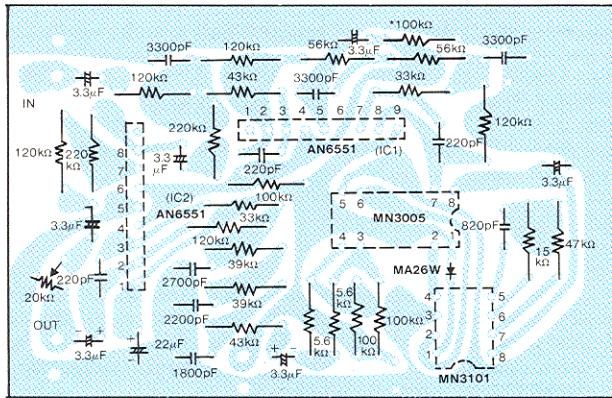
Item	Symbol	Condition	Min.	Typ.	Max.	Unit
Supply Current	ICC			8	10	mA
Total Power Consumption	Ptot			70		mW
Signal Delay Time	tD	fcp = 18±2kHz	100	113	128	msec
Cutoff Frequency	fco			2		kHz
Input Signal Swing	Vi	THD = 2.5%			500	mVrms
Insertion Loss	Li	fi = 1kHz, Vi = 300mV	-2	0	2	dB
Total Harmonic Distortion	THD	fi = 1kHz, Vi = Vi(max.) -6dB		0.5	1	%
Output Noise Voltage	Vno	Vi = OV			0.35	mVrms
Signal to Noise Ratio	S/N	Vs Vi(max.) = 500mVrms	60			dB

Application Circuit Example 2 – Echo Effect Generation Circuit With The MN31007



*Adjust to minimize distortion (VR 100kΩ typ.)

Printed Circuit Board Layout (Actual Size)



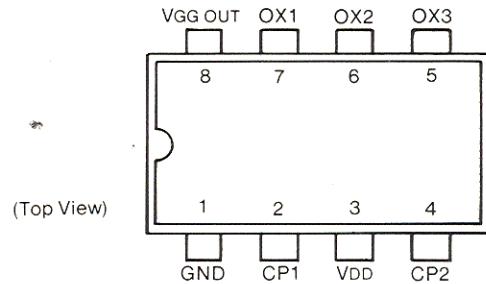
Quick Reference Data for The MN31007

Item	Symbol	Value	Unit
Supply Voltage	VDD, VGG	-15, V _{DD} + 1	V
Signal Delay Time	tD	5.12 ~ 51.2	msec
Total Harmonic Distortion	THD	0.3	%
Signal to Noise Ratio	S/N	88	dB

Electrical Characteristics of The Application Circuit Using The MN31007 (Vcc = 9V, Ta = 25°C)

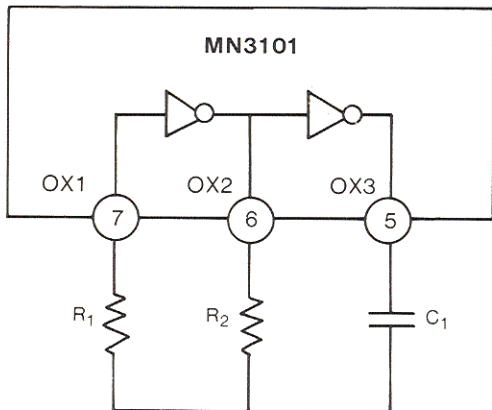
Item	Symbol	Condition	Min.	Typ.	Max.	Unit
Supply Current	I _{CC}			8	10	mA
Total Power Consumption	P _{tot}			70		mW
Signal Delay Time	tD	f _{cp} = 14±2kHz	32	37	43	msec
Cutoff Frequency	f _{c0}			2		kHz
Input Signal Swing	V _i	THD = 2.5%			500	mVrms
Insertion Loss	L _i	f _i = 1kHz, V _i = 300mV	-2	0	2	dB
Total Harmonic Distortion	THD	f _i = 1kHz, V _i = V _{i(max.)} - 6dB		0.5	1	%
Output Noise Voltage	V _{no}	V _i = OV			0.35	mVrms
Signal to Noise Ratio	S/N	V _s V _{i(max.)} = 500mVrms	60			dB

Terminal Assignments



Pin No.	Symbol	I/O	Functions	
1	GND	Supply	Grounding	
2	CP1	O	Outputs 1/2 duty cycle clock pulse at frequency 1/2 of an oscillation frequency, having an opposite phase relationship with respect to CP2.	
3	VDD	Supply	-15V supply voltage input.	
4	CP2	O	Outputs clock pulse having an opposite phase relationship with respect to CP1.	
5	OX3	O	Internal Oscillation:	External Oscillation:
6	OX2	O	C R network connection to the pins (See oscillator circuit example)	
7	OX1	I		
8	VGG OUT	O	-14V output (When VDD = 15V) The relationship between VDD and VGG OUT is: $V_{GG\ OUT} = 14/15\ V_{DD}$	

Oscillator Circuit Example

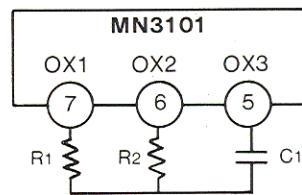
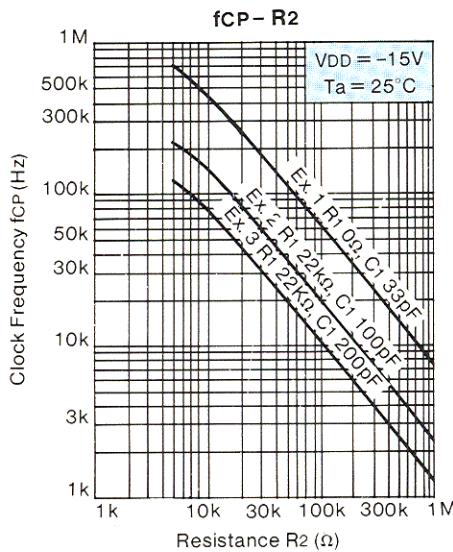


The internal oscillator circuit of the MN3101 consists of a 2-stage inverter. The oscillation frequency is established by the time constant of C_1 and R_2 . The following table shows examples of C_1 , R_1 and R_2 values. $f_{CP} - R_2$ characteristics example is shown in Figure 1.

Example \ Constant	R1 (Ω)	R2 (Ω)	C1 (pF)	f_{osc}^{**} (kHz)	F_{CP^*} (kHz)
Example 1	0	5k~1M	33	15~1500	7.5~750
Example 2	22k	5k~1M	100	5.2~440	2.6~220
Example 3	22k	5k~1M	200	1.4~280	0.7~140

*Clock output frequency for CP1 or CP2.

**Oscillation frequency for OX1, OX2, and OX3.



Maximum Clock Frequency

The maximum clock frequency is limited by device power dissipation and load capacitance. The power consumption of the devices increases as the clock frequency or load capacitance is increased (See Fig. 2). Therefore, a proper clock frequency and load capacitance value must be chosen so that the maximum allowable power dissipation of 200mW for the MN3101 is not exceeded.

Fig. 3 shows the relationship between the maximum frequency and load capacitance for 150mW power dissipation. The maximum clock frequency can be increased without increasing the power consumption when a resistor is connected to each clock output terminal (See Fig. 2 and 3). The series resistor consumes a part of the power required for driving the load capacitance and help reduce the power dissipated in the device.

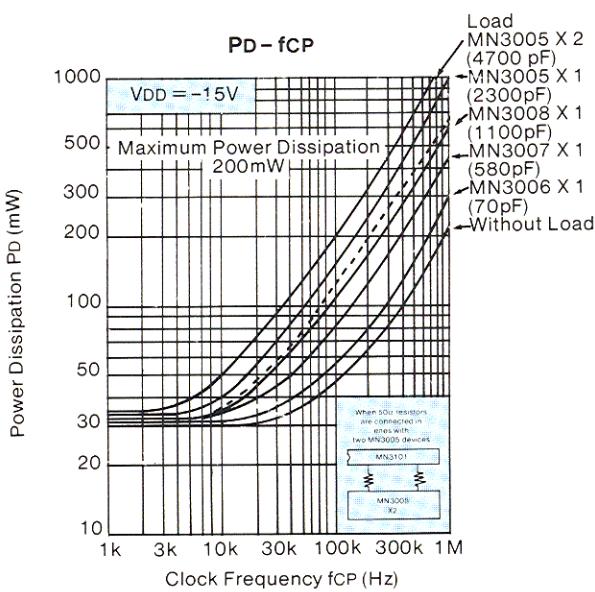


Fig. 2 Power Consumption vs Clock Frequency

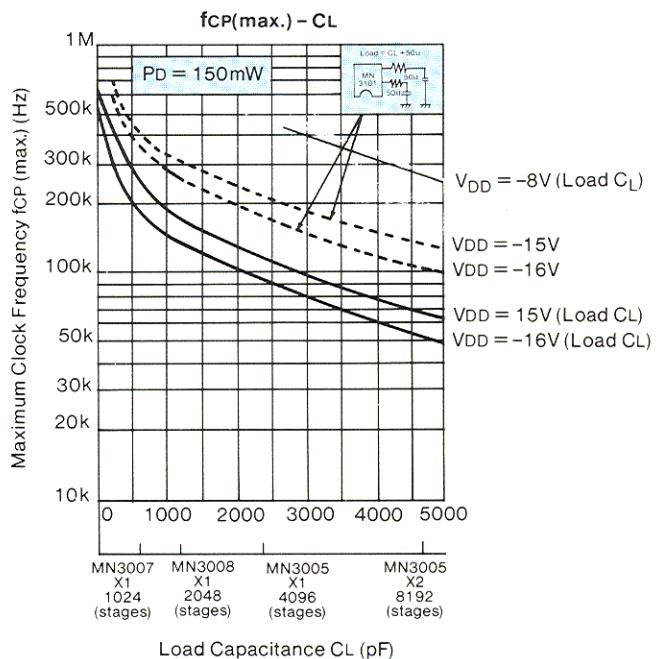
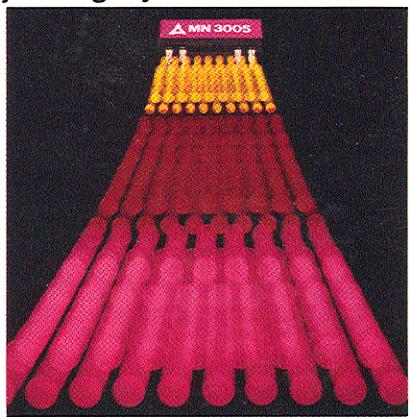


Fig. 3 Maximum Clock Frequency vs Load Capacitance at 150mW Power Consumption

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